ISSN 0169-4332

applied surface science

MASTER INDEX

A journal devoted to applied physics
and chemistry of surfaces and interfaces

Editors:
L.C. Feldman, Nashville, TN, USA
J. Nishizawa, Sendai, Japan
P. van der Weg, Utrecht, The Netherlands

Volumes 81–90

ADVISORY BOARD

North-Holland

APPLIED SURFACE SCIENCE

Editors: L.C. Feldman, J. Nishizawa, W.F. van der Weg

Founding Editor: R.L. Park

Advisory Editorial Board:

D.E. Aspnes, *Raleigh, NC*
M. Balkanski, *Paris, France*
J.C. Bean, *Murray Hill, NJ*
S.A. Chambers, *Richland, WA*
J. Chikawa, *Hyogo, Japan*
D.B. Frazer, *Santa Clara, CA*
M. Henzler, *Hannover, Germany*
M. Hirose, *Hiroshima, Japan*
P.S. Ho, *Austin, TX*
S. Hofmann, *Ibaraki, Japan*
H. Ishiwara, *Yokohama, Japan*
D.A. King, *Cambridge, UK*
K.M. Maex, *Leuven, Belgium*
J.W. Niemantsverdriet, *Eindhoven, The Netherlands*
P.R. Norton, *London, Canada*
C.J. Powell, *Gaithersburg, MD*
E. Rimini, *Catania, Italy*
G.A. Somorjai, *Berkeley, CA*
S. Ushioda, *Sendai, Japan*
W.H. Weinberg, *Santa Barbara, CA*
J.M. White, *Austin, TX*
Xie Xide, *Shanghai, China*
J.T. Yates, *Pittsburgh, PA*
M.L. Yu, *Yorktown Heights, NY*

Scope:
Applied Surface Science is concerned with applied physics and chemistry of surfaces and interfaces and with the atomistic description of processing, modification and characterization of surfaces, interfaces and thin films. These include growth and epitaxy, oxidation, reactivity as well as surface modification by directed energy deposition (lasers, ion or electron beams) or other techniques (i.e. plasma etching). Important areas in the field are electronic materials (i.e. semiconductors, organic films, ceramics) and chemical processes at surfaces (catalysis, corrosion, reactivity).

Information for Authors:
Contributions shall be written in English and should be submitted in triplicate directly to one of the editors listed below:

Professor L.C. Feldman
Dept. of Physics and Astronomy
Vanderbilt University
Nashville, TN 37235
USA

FAX: +1-615-343-1708
E-Mail: FELDMAN@ctrvax.Vanderbilt.Edu

Professor Jun-ichi Nishizawa
Tohoku University
2-1-1 Katahira
Aoba-ku, Sendai
Japan 980

FAX: +81-22-262 3180

Professor W.F. van der Weg
Debye Institute
University of Utrecht
P.O. Box 80.000, 3508 TA Utrecht
The Netherlands

FAX: +31-30-543 165
E-Mail: vdweg@fys.ruu.nl

Detailed information on the preparation of manuscripts may be found on the inside back cover.

All correspondence with the publisher regarding manuscripts accepted for publication should be addressed to:

Applied Surface Science Issue Management
P.O. Box 2759
1000 CT Amsterdam
The Netherlands

FAX: +31-20-485 2775

Applied Surface Science (ISSN 0169-4332). For 1996, volumes 93–104 are scheduled for publication. Subscription prices are available upon request from the publisher. A combined subscription to Applied Surface Science volumes 93–104, Surface Science Reports volumes 24–26, and Surface Science volumes 343–366 is available at a reduced rate.
Subscriptions are accepted on a prepaid basis only and are entered on a calendar year basis.
Issues are sent by surface mail except to the following countries where air delivery via SAL is ensured: Argentina, Australia, Brazil, Canada, China, Hong Kong, India, Israel, Japan, Malaysia, Mexico, New Zealand, Pakistan, Singapore, South Africa, South Korea, Taiwan, Thailand, USA. For all other countries airmail rates are available upon request.
Please address all your requests regarding orders and subscription queries to: Elsevier Science, Journal Department, P.O. Box 211, 1000 AE Amsterdam, The Netherlands. Telephone: +31-20-4853642, Telefax: +31-20-4853598. Claims for issues not received should be made within six months of our publication (mailing) date.

Elsevier Science B.V. All rights reserved. No part of this publication may be reproduced, stored in a retrieval system or transmitted in any form or by any means, electronic, mechanical, photocopying, recording or otherwise, without the written permission of the Publisher, Elsevier Science B.V., Copyright & Permissions Department, P.O. Box 521, 1000 AM Amsterdam, The Netherlands.
Special regulations for authors – Upon acceptance of an article by the journal, the author(s) will be asked to transfer copyright of the article to the Publisher. This transfer will ensure the widest possible dissemination of information.
Special regulations for readers in the USA – This journal has been registered with the Copyright Clearance Center, Inc. Consent is given for copying of articles for personal or internal use, or for the personal use of specific clients. This consent is given on the condition that the copier pays through the Center the per-copy fee stated in the code on the first page of each article for copying beyond that permitted by Sections 107 or 108 of the US Copyright Law. The appropriate fee should be forwarded with a copy of the first page of the article to the Copyright Clearance Center, Inc., 222 Rosewood Drive, Danvers, MA 01923, USA. If no code appears in an article, the author has not given broad consent to copy and permission to copy must be obtained directly from the author. The fee indicated on the first page of an article in this issue will apply retroactively to all articles published in the journal, regardless of the year of publication. This consent does not extend to other kinds of copying, such as for general distribution, resale, advertising and promotion purposes, or for creating new collective works. Special written permission must be obtained from the Publisher for such copying.

US mailing notice – Applied Surface Science (ISSN 0169-4332) is published semimonthly except monthly in January, November and December by Elsevier Science B.V., Molenwerf 1, P.O. Box 211, 1000 AE Amsterdam, The Netherlands. The annual subscription price in the USA is US$ 3147 (valid in North, Central and South America only), including air speed delivery. Second class postage paid at Jamaica, NY 11431.
USA POSTMASTERS: Send address changes to Applied Surface Science, Publications Expediting, Inc., 200 Meacham Avenue, Elmont, NY 11003. Airfreight and mailing in the USA by Publications Expediting.

No responsibility is assumed by the Publisher for any injury and/or damage to persons or property as a matter of products liability, negligence or otherwise, or from any use or operation of any methods, products, instructions or ideas contained in the material herein. Although all advertising material is expected to conform to ethical standards, inclusion in this publication does not constitute a guarantee or endorsement of the quality or value of such product or of the claims made of it by its manufacturer.

∞ The paper used in this publication meets the requirements of ANSI/NISO 239.48-1992 (Permanence of Paper).

Printed in The Netherlands

APPLIED SURFACE SCIENCE

Editorial Board

Professor L.C. Feldman
Dept. of Physics and Astronomy
Vanderbilt University
Nashville, TN 37235
USA

FAX: +1-615-343-1708
E-Mail: FELDMAN@ctrvax.
Vanderbilt.Edu

Professor Jun-ichi Nishizawa
Tohoku University
2-1-1 Katahira
Aoba-ku, Sendai
Japan 980

FAX: +81-22-262 3180

Professor W.F. van der Weg
Debye Institute
University of Utrecht
P.O. Box 80.000, 3508 TA Utrecht
The Netherlands

FAX: +31-30-543 165
E-Mail: vdweg@fys.ruu.nl

Advisory Editorial Board

D.E. Aspnes
Bell Communications Research
Red Bank, NJ 07701, USA

M. Balkanski
Université Pierre et Marie Curie
75230 Paris Cedex 05, France

J.C. Bean
AT&T Bell Laboratories
Murray Hill, NJ 07974, USA

S.A. Chambers
Pacific Northwest Laboratory
Richland, WA 99352, USA

J. Chikawa
Himeji Institute of Technology
Ako-gun, Hyogo 678-12, Japan

D.B. Frazer
Intel Corporation
Santa Clara, CA 95052, USA

M. Henzler
Universität Hannover
D-30167 Hannover, Germany

M. Hirose
Hiroshima University
Higashi-Hiroshima 724, Japan

P.S. Ho
University of Texas at Austin
Austin, TX 78712, USA

S. Hofmann
National Research Institute for Metals
Tsukuba, Ibaraki 305, Japan

H. Ishiwara
Tokyo Institute of Technology
Yokohama 227, Japan

D.A. King
University of Cambridge
Cambridge CB2 1EW, UK

K.M. Maex
IMEC vzw
B-3030 Leuven, Belgium

J.W. Niemantsverdriet
Eindhoven University of Technology
NL-5600 MB Eindhoven
The Netherlands

P.R. Norton
University of Western Ontario
London, Ontario N6A 5B7, Canada

C.J. Powell
National Institute of Standards
and Technology
Gaithersburg, MD 20899, USA

E. Rimini
Università di Catania
I-95129 Catania, Italy

G.A. Somorjai
University of California
Berkeley, CA 94720, USA

S. Ushioda
Tohoku University
Aoba-ku, Sendai 980, Japan

W.H. Weinberg
University of California
Santa Barbara, CA 93106, USA

J.M. White
University of Texas at Austin
Austin, TX 78712, USA

Xie Xide
Fudan University
Shanghai, China

J.T. Yates, Jr.
University of Pittsburgh
Pittsburgh, PA 15260, USA

M.L. Yu
IBM T.J. Watson Research Center
Yorktown Heights, NY 10598, USA

applied surface science

A JOURNAL DEVOTED TO APPLIED PHYSICS
AND CHEMISTRY OF SURFACES AND INTERFACES

Editors:
L.C. Feldman, Nashville, TN, USA
J. Nishizawa, Sendai, Japan
W.F. van der Weg, Utrecht, The Netherlands

Master Index to Volumes 81–90

ELSEVIER
Amsterdam – Lausanne – New York – Oxford – Shannon – Tokyo

© 1996 Elsevier Science B.V. All rights reserved

No part of this publication may be reproduced, stored in a retrieval system or transmitted in any form or by any means, electronic, mechanical, photocopying, recording or otherwise, without the written permission of the Publisher, Elsevier Science B.V., Copyright & Permissions Department, P.O. Box 521, 1000 AM Amsterdam, The Netherlands.
Special regulations for authors – Upon acceptance of an article by the journal, the author(s) will be asked to transfer copyright of the article to the Publisher. This transfer will ensure the widest possible dissemination of information.
Special regulations for readers in the USA – This journal has been registered with the Copyright Clearance Center, Inc. Consent is given for copying of articles for personal or internal use, or for the personal use of specific clients. This consent is given on the condition that the copier pays through the Center the per-copy fee stated in the code on the first page of each article for copying beyond that permitted by Sections 107 or 108 of the US Copyright Law. The appropriate fee should be forwarded with a copy of the first page of the article to the Copyright Clearance Center, Inc., 222 Rosewood Drive, Danvers, MA 01923, USA. If no code appears in an article, the author has not given broad consent to copy and permission to copy must be obtained directly from the author. The fee indicated on the first page of an article in this issue will apply retroactively to all articles published in the journal, regardless of the year of publication. This consent does not extend to other kinds of copying, such as for general distribution, resale, advertising and promotion purposes, or for creating new collective works. Special written permission must be obtained from the publisher for such copying.

No responsibility is assumed by the Publisher for any injury and/or damage to persons or property as a matter of products liability, negligence or otherwise, or from any use or operation of any methods, products, instructions or ideas contained in the material herein.
Although all advertising material is expected to conform to ethical standards, inclusion in this publication does not constitute a guarantee or endorsement of the quality or value of such product or of the claims made of it by its manufacturer.

♾ The paper used in this publication meets the requirements of ANSI/NISO 239.48-1992 (Permanence of Paper).

PRINTED IN THE NETHERLANDS

MASTER INDEX

Volumes 81–90

Author index	1
Subject index	33
List of terms used in the subject index	116

ELSEVIER

Applied Surface Science MI 81–90 (1995) 1–32

applied surface science

Author index to volumes 81–90

Aarik, J. and H. Siimon, Characterization of adsorption in flow type atomic layer epitaxy reactor 81 (1994) 281
Aarik, J. and H. Siimon, Erratum to "Characterization of adsorption in flow type atomic layer epitaxy reactor" [Appl. Surf. Sci. 81 (1994) 281] 90 (1995) 109
Ababou, A., see Le Normand, F. 81 (1994) 309
Abbas, N.M., see Mohamed, M.H. 90 (1995) 409
Abdillahi, M.M., see Mohamed, M.H. 90 (1995) 409
Abe, H., see Kanazawa, I. 85 (1995) 124
Abon, M., see Debauge, Y. 90 (1995) 15
Abukawa, T., see Sasaki, M. 82/83 (1994) 387
Adnot, A., see Lamontagne, B. 90 (1995) 447
Adsool, A.D., R. Pande, R.B. Sharma, M.A. More and D.S. Joag, Adsorption studies of iron on tungsten by probe-hole field emission microscopy 87 (1995) 37
Aers, G.C., P.A. Marshall, T.C. Leung and R.D. Goldberg, Defect profiling in multilayered systems using mean depth scaling 85 (1995) 196
Afonso, C.N., see Gonzalo, J. 86 (1995) 40
Aguiar, R., see Queralt, X. 86 (1995) 95
Aguiar Colom, R., see Reihs, K. 84 (1995) 107
Ahlgren, T., K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen, Range profiles of 6–10 MeV ^{15}N ions implanted in silicon 90 (1995) 419
Ahmed, M.F., see Ashour, A. 89 (1995) 159
Aisaka, T., see Ishii, A. 85 (1995) 33
Akamatsu, M., S. Narahara, T. Kobayashi and F. Hasegawa, Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$ and AsH_3 82/83 (1994) 228
Akazawa, H., Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane 82/83 (1994) 394
Akinaga, H. and K. Tanaka, Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy 82/83 (1994) 298
Al-Kassab, T., M.-P. Macht and H. Wollenberger, FIM/AP analysis of Cu–Pd multilayers 87/88 (1995) 329
Alavi, K., see Hozhabri, N. 85 (1995) 311
Aleskovski, V.B., see Drozd, V.E. 82/83 (1994) 587
Aleskovski, V.B., see Drozd, V.E. 82/83 (1994) 591
Alexandrescu, R., see D'Anna, E. 86 (1995) 170
Alexandrescu, R., see Peled, A. 86 (1995) 538
Alexandrou, I., see Logothetidis, S. 86 (1995) 185
Alford, T.L., see Russell, S.W. 90 (1995) 455
Aliev, V.S., M.R. Baklanov and V.I. Bukhtiyarov, Silicon surface cleaning using XeF_2 gas treatment 90 (1995) 191
Allan, G., see Lang, B. 81 (1994) 17
Allegrini, M., see Amoruso, S. 86 (1995) 35
Allinger, Th., see Engelhard, H. 90 (1995) 89
Alnot, M., see Lobstein, N. 89 (1995) 307
Amarendra, G., see Vasumathi, D. 85 (1995) 154
Amarendra, G., see Canter, K.F. 85 (1995) 339
Ambigapathy, R., see Manuel, A.A. 85 (1995) 301
Amirhaghi, S., see Craciun, V. 86 (1995) 99
Amoruso, S., V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo, Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation 86 (1995) 35
Anandan, C., X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface 89 (1995) 57
Andrei, A., see Peled, A. 86 (1995) 538
Andrén, H.-O., G. Cai and L.-E. Svensson, Microstructure of heat resistant chromium steel weld metals 87/88 (1995) 200
Andreu, J., see Puigdollers, J. 86 (1995) 600
Antoni, F., E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert, $Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique 86 (1995) 175
Aono, M., see Kawai, M. 82/83 (1994) 487
Aoyagi, Y., see Isshiki, H. 82/83 (1994) 57
Aoyagi, Y., see Meguro, T. 82/83 (1994) 193
Aoyagi, Y., see Ishii, M. 86 (1995) 554
Arai, M., Y. Nishiyama, T. Masuda and K. Hashimoto, The distribution of activation energy for hydrogen desorption over

silica-supported nickel catalysts determined from temperature-programmed desorption spectra 89 (1995) 11
Arenholz, E., see Heitz, J. 81 (1994) 103
Arimondo, E., see Amoruso, S. 86 (1995) 35
Armas, B., see Aspar, B. 81 (1994) 55
Armenante, M., see Amoruso, S. 86 (1995) 35
Armstrong, J.V., see Farrell, T. 86 (1995) 582
Arnaud, Y.P. and H. Bertrais, Identification of active species and theoretical classification of simple catalyst oxides using surface redox couples 81 (1994) 69
Arnold, J., U. Dasbach, W. Ehrfeld, K. Hesch and H. Löwe, Combination of excimer laser micromachining and replication processes suited for large scale production 86 (1995) 251
Arnold, N., P.B. Kargl and D. Bäuerle, Laser direct writing and instabilities: a one-dimensional approach 86 (1995) 457
Arpatzanis, N., see Thurzo, I. 90 (1995) 39
Aruga, T., see Taguchi, Y. 82/83 (1994) 434
Aruga, T., S. Takamura, K. Nakata and Y. Ito, Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation 85 (1995) 229
Arvia, A.J., see Hernández Creus, A. 81 (1994) 387
Asahi, H., see Kim, J.H. 82/83 (1994) 76
Asahi, H., S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda, Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy 82/83 (1994) 109
Asami, K., see Kim, J.H. 82/83 (1994) 76
Asami, K., see Asahi, H. 82/83 (1994) 109
Asami, S., N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt, Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6 82/83 (1994) 359
Ascherl, M., see Wang, P.W. 90 (1995) 413
Asensi, J.M., see Puigdollers, J. 86 (1995) 600
Ashino, M., M. Tomitori and O. Nishikawa, Atom probe and field emission electron spectroscopy studies of semiconductor films on metals 87/88 (1995) 12
Ashour, A., M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan, Thermal effects on structural characterization of evaporated CdTe films during and after deposition 89 (1995) 159
Asikainen, T., M. Ritala and M. Leskelä, Growth of In_2S_3 thin films by atomic layer epitaxy 82/83 (1994) 122
Asoka-Kumar, P., see Umlor, M.T. 85 (1995) 295
Aspar, B., R. Berjoan, C. Labatut and B. Armas, Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD 81 (1994) 55
Asskali, A., see Reniers, F. 81 (1994) 151
Atanassova, E., T. Dimitrova and J. Koprinarova, AES and XPS study of thin RF-sputtered Ta_2O_5 layers 84 (1995) 193
Athenstaedt, W. and M. Leisch, A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy 87/88 (1995) 318
Atkinson, A., see Leung, T.C. 85 (1995) 292
Aubert, P., G. Garry, R. Bisaro and J. Garcia Lopez, Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique 86 (1995) 144
Auger, P., see Schmuck, C. 87/88 (1995) 228
Augugliaro, V., see Navío, J.A. 81 (1994) 325
Autric, M., see Grangeon, F. 86 (1995) 160
Auvert, G., Laser chemical vapour deposition for microelectronics 86 (1995) 466
Ayame, A., see Tomizuka, H. 89 (1995) 281

Babu, S.S., S.A. David, J.M. Vitek and M.K. Miller, Atom probe field ion microscopy of type 308 CRE stainless steel welds 87/88 (1995) 207
Babu, S.V., see Kononenko, T.V. 86 (1995) 234
Bachmann, K.J., see Kelliher, J.T. 86 (1995) 453
Backes, G., see Kreutz, E.W. 86 (1995) 310
Badawi, K.F., see Durand, N. 81 (1994) 119
Badaye, M., see Wang, F. 90 (1995) 123
Baeri, P., R. Reitano and N. Marino, SiO_2 film deposition by XeCl laser ablation of fused silica 86 (1995) 128
Baev, A.A., see Tutov, E.A. 90 (1995) 303
Bai, C., see Fang, Y. 89 (1995) 331
Bajikar, S.S., T.F. Kelly, C.-M. Teng and P.P. Camus, Microfabrication of extraction electrodes for local-electrode atom probes 87/88 (1995) 438
Bakhtizin, R.Z., C. Park, T. Hashizume and T. Sakurai, Scanning tunneling microscopy study of the (3×1) reconstruction induced by Li adsorption on the Si(111) surface 87/88 (1995) 347
Baklanov, M.R., see Aliev, V.S. 90 (1995) 191
Balducci, L., see Garbassi, F. 84 (1995) 145
Bali, K., see Geretovszky, Zs. 86 (1995) 494
Bali, K., Zs. Geretovszky, A.L. Tóth and T. Szörényi, The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions 86 (1995) 500
Ballutaud, D., C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob,

Reactivity of III–V and II–VI semiconductors toward hydrogen: surface modification and evolution in air 84 (1995) 187
Bannerjee, S., see Asami, S. 82/83 (1994) 359
Bao, X., see Deng, J. 81 (1994) 341
Baraban, A.P., see Drozd, V.E. 82/83 (1994) 583
Baranauskas, V., G.P. Thim and A. Peled, Laser-induced formation of porous silicon 86 (1995) 398
Bargon, J., see Lätsch, S. 81 (1994) 183
Barkshire, I.R., M. Prutton and G.C. Smith, Multi-spectral scanning Auger microscopy of tribological surfaces 84 (1995) 331
Barth, M., see Karstens, H. 86 (1995) 521
Barthés-Labrousse, M.-G., see Fauquet, C. 81 (1994) 435
Bas, P., A. Bostel, B. Deconihout and D. Blavette, A general protocol for the reconstruction of 3D atom probe data 87/88 (1995) 298
Bas, P., see Deconihout, B. 87/88 (1995) 428
Basiuk, E.V., see Dmitruk, N.L. 90 (1995) 489
Bastl, Z., see Fajgar, R. 86 (1995) 530
Bater, S., see Wang, P.W. 90 (1995) 413
Batirev, I.G., see Leiro, J.A. 90 (1995) 515
Bäuerle, D., see Heitz, J. 81 (1994) 103
Bäuerle, D., see Arnold, N. 86 (1995) 457
Baumgärtner, H., see Jiang, W. 86 (1995) 564
Bayrachny, B.I., see Skatkov, L.I. 81 (1994) 427
Beauvois, S., see Viville, P. 86 (1995) 411
Bedair, S.M. and N.A. El-Masry, Recent advances in atomic layer epitaxy devices 82/83 (1994) 7
Bedair, S.M., see Hayafuji, N. 82/83 (1994) 18
Beling, C.D., see Panda, B.K. 85 (1995) 182
Beling, C.D., see Ling, C.C. 85 (1995) 305
Bellard, L., see Shafeev, G.A. 86 (1995) 387
Benítez, J.J., I. Carrizosa and J.A. Odriozola, In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the $CO + H_2$ reaction over lanthanide-modified Rh/Al_2O_3 catalysts 84 (1995) 391
Benninghoven, A., see Reihs, K. 84 (1995) 107
Berardi, V., see Amoruso, S. 86 (1995) 35
Berger, S., see Tamir, S. 86 (1995) 514
Bergmann, H.W., K. Schutte, E. Schubert and A. Emmel, Laser–surface processing of metals and ceramics for industrial applications 86 (1995) 259
Berjeza, N.A., S.P. Velikevitch, V.I. Mazhukin, I. Smurov and G. Flamant, Influence of temperature gradient to solidification velocity ratio on the structure transformation in pulsed- and CW-laser surface treatment 86 (1995) 303
Berjoan, R., see Aspar, B. 81 (1994) 55
Bermudez, V.M., Adsorption and co-adsorption of boron and oxygen on ordered α-SiC surfaces 84 (1995) 45
Bertolini, J.C., see Debauge, Y. 90 (1995) 15
Bertomeu, J., see Izquierdo, R. 86 (1995) 509
Bertomeu, J., see Puigdollers, J. 86 (1995) 600
Bertóti, I., M. Mohai, J.L. Sullivan and S.O. Saied, Surface characterisation of plasma-nitrided titanium: an XPS study 84 (1995) 357
Bertrais, H., see Arnaud, Y.P. 81 (1994) 69
Bertrand, P., see Weng, L.T. 84 (1995) 9
Bertrand, P., see Piyakis, K. 84 (1995) 227
Bevk, J., see Kosowsky, S.D. 84 (1995) 179
Bisaro, R., see Aubert, P. 86 (1995) 144
Blake, R.G., see Miller, M.K. 87/88 (1995) 216
Błaszczyszyn, R., see Bryl, R. 87/88 (1995) 69
Blavette, D., see Schmuck, C. 87/88 (1995) 228
Blavette, D., see Duval, S. 87/88 (1995) 284
Blavette, D., see Bas, P. 87/88 (1995) 298
Blavette, D., see Deconihout, B. 87/88 (1995) 428
Block, J.H., see Cocke, D.L. 84 (1995) 153
Block, J.H., see Gorodetskii, V. 87/88 (1995) 151
Block, J.H., see Medvedev, V.K. 87/88 (1995) 159
Bloss, E., see Coleman, P.G. 85 (1995) 276
Blum, O. and U. König, Electrochemical and photoelectrochemical modification and characterisation of thin passive films 86 (1995) 417
Bolmont, D., see Hong, S. 90 (1995) 65
Bolt, P.H., S.F. Lobner, J.W. Geus and F.H.P.M. Habraken, Interfacial reaction of NiO with $Al_2O_3(11\bar{2}0)$ and polycrystalline α-Al_2O_3 89 (1995) 339
Boman, M., see Stenberg, G. 86 (1995) 543
Bonnet, J., see Lévêque, G. 89 (1995) 211
Bonser, D.J., see Asami, S. 82/83 (1994) 359
Borochov, N. and A. Peled, Aggregation kinetics of photo-excited colloid solutions observed by dynamic photon correlation spectroscopy (PCS) 86 (1995) 533
Bostel, A., see Bas, P. 87/88 (1995) 298
Bostel, A., see Deconihout, B. 87/88 (1995) 428
Bouabid, K., see Maury, F. 86 (1995) 447
Bouet, M., see Deconihout, B. 87/88 (1995) 428
Bouillon, F., see Reniers, F. 81 (1994) 151
Bourbigot, S., M. Le Bras, L. Gengembre and R. Delobel, XPS study of an intumescent coating. Application to the ammonium polyphosphate/pentaerythritol fire-retardant system 81 (1994) 299
Bourée, J.E., R. Helbing, W. Kuhn and O. Gorochov, Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs 86 (1995) 437
Bourée, J.E., see Tonneau, D. 86 (1995) 488
Bouveresse, E., see Friedbacher, G. 84 (1995) 133
Boyd, I.W., see Tyrrell, G.C. 86 (1995) 50
Boyd, I.W., see Craciun, V. 86 (1995) 99
Boyd, I.W., see King, S. 86 (1995) 134
Bracconi, P., see Buisson, L. 84 (1995) 211
Bradley, R.H., Surface studies of Cu/Cr/Ag impregnated microporous carbons 90 (1995) 271
Bradshaw, A.M., see Keil, M. 90 (1995) 377
Bram, Ch., see Starke, U. 89 (1995) 175

Brauer, G., see Weiss, A.H. 85 (1995) 82
Braul, N., see Le Normand, F. 81 (1994) 309
Brédas, J.L., see Viville, P. 86 (1995) 411
Bréelle, E., S. Rigo, J.A. Kilner and J.-J. Ganem, SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient 81 (1994) 127
Bremert, O., see Krebs, H.-U. 86 (1995) 86
Bremert, O., see Krebs, H.-U. 86 (1995) 90
Brimaud, J.-H., see Durand, H.-A. 86 (1995) 122
Britton, D.T. and J. Störmer, Application of time-dependent diffusion models to the study of real solids 85 (1995) 1
Britton, D.T., K. Uhlmann and G. Kögel, Magnetic positron optics 85 (1995) 158
Brochereux, A., O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni, Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer 90 (1995) 47
Brown, N.M.D. and Z.-H. Liu, An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge 90 (1995) 155
Brübach, J., see Hopkins, J. 84 (1995) 299
Brunel, M., see Laude, L.D. 86 (1995) 368
Brunel, M., see Brochereux, A. 90 (1995) 47
Bruque, J.M., see Jańczuk, B. 81 (1994) 95
Brusatin, G., see Caccavale, F. 81 (1994) 443
Bryl, R., T. Wysocki and R. Błaszczyszyn, Field-induced redistribution and diffusion of water on a Pt field emitter 87/88 (1995) 69
Bubert, H. and R.P.H. Garten, Matrix factors affecting quantitative analysis of AES for binary alloys 81 (1994) 203
Buckley, A.N. and R. Woods, Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart 84 (1995) 223
Buisson, L., P. Bracconi and X. Claudon, Quantitative analysis of the thermal degassing of a beryllium powder 84 (1995) 211
Bukhtiyarov, V.I., see Aliev, V.S. 90 (1995) 191
Bull, S.J., see Rice-Evans, P.C. 85 (1995) 320
Bull, S.J., see Saleh, A.S. 85 (1995) 325
Büssenschütt, A., see Zielasek, V. 90 (1995) 117
Butman, M.F., J. Nakamura, S. Kamidoi and H. Kawano, Influence of surface charge on thermal positive ion emission from potassium bromide 89 (1995) 323

Caccavale, F., G. Brusatin and I. Kleps, A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films 81 (1994) 443
Cade, N.A., see King, R.A. 87/88 (1995) 279
Cade, N.A., see Huang, M. 87/88 (1995) 421
Cai, G., see Andrén, H.-O. 87/88 (1995) 200
Cai, S., see Ji, G. 81 (1994) 63
Calder, I., see Lawther, D.W. 85 (1995) 265
Callegaro, L., see Vavassori, P. 89 (1995) 93
Camus, P.P., D.J. Larson and T.F. Kelly, A method for reconstructing and locating atoms on the crystal lattice in three-dimensional atom probe data 87/88 (1995) 305
Camus, P.P., see Bajikar, S.S. 87/88 (1995) 438
Camus, P.P., see Larson, D.J. 87/88 (1995) 446
Cañón, M.G., see L'Argentière, P.C. 89 (1995) 63
Canter, K.F., see Vasumathi, D. 85 (1995) 154
Canter, K.F., G. Amarendra, D. Vasumathi, S.A. Wesley, R. Xie, A.P. Mills, Jr., R.L. Sabatini and Y. Zhu, Contrast in positron reemission microscopy due to positron trapping by dislocations 85 (1995) 339
Carley, A.F., P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas, The hydroxylation of Cu(111) and Zn(0001) surfaces 81 (1994) 265
Carline, R.T., C. Pickering, T.J.C. Hosea and D.J. Robbins, Photoreflectance of strained $Si_{1-x}Ge_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry 81 (1994) 475
Carlsson, J.-O., see Stenberg, G. 86 (1995) 543
Carrière, B., see Le Normand, F. 81 (1994) 309
Carrizosa, I., see Benítez, J.J. 84 (1995) 391
Castle, J.E., see Salvi, A.M. 90 (1995) 333
Caudano, R., see Grégoire, Ch. 84 (1995) 163
Caudano, R., see Lamontagne, B. 90 (1995) 481
Cerezo, A., see Hyde, J.M. 87/88 (1995) 311
Cerezo, A., see Miller, M.K. 87/88 (1995) 323
Cerezo, A., see Sijbrandij, S.J. 87/88 (1995) 414
Černý, R., V. Vydra, P. Přikryl, I. Ulrych, J. Kočka, K.M.A. El-Kader, Z. Chvoj and V. Cháb, Theoretical and experimental studies of a-Si:H recrystallization by XeCl excimer laser irradiation 86 (1995) 359
Cerofolini, G.F. and L. Meda, Chemistry at silicon crystalline surfaces 89 (1995) 351
Cerofolini, G.F., G. La Bruna and L. Meda, Enhanced silicon oxidation in O_2 and O_2:F_2 89 (1995) 361
Cháb, V., see Černý, R. 86 (1995) 359
Chabrerie, J.-P., see Néron de Surgy, G. 87/88 (1995) 91
Chambers, S.A., see Tran, T.T. 81 (1994) 161
Chambreland, S., see Duval, S. 87/88 (1995) 284
Chan, S.-H., S.M. Sze, C.-Y. Chang and W.-I. Lee, Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources 82/83 (1994) 85
Chang, C.-Y., see Chan, S.-H. 82/83 (1994) 85

Chang, K.-S., see Iwata, T. 87/88 (1995) 31
Chang, M.F., see Dam, B. 86 (1995) 13
Charlton, M., see Moxom, J. 85 (1995) 118
Chattopadhyay, P. and S. Sanyal, Capacitance–voltage characteristics of Schottky barrier diode in the presence of deep-level impurities and series resistance 89 (1995) 205
Chen, C.S., see Mar, S.Y. 90 (1995) 497
Chen, H., see Deng, J. 81 (1994) 341
Chen, X. and Y. Wang, A study of the composition distribution at the Ti/Al_2O_3 interface using the MCs^+-SIMS technique 89 (1995) 169
Chen, X.G., see Xiao, X.R. 90 (1995) 321
Chen, Y.-W., see Li, C. 81 (1994) 465
Chen, Y.L., see Kelliher, J.T. 86 (1995) 453
Chenakin, S.P., Initial oxidation kinetics of Fe–Ni single crystals before and after ion bombardment 84 (1995) 91
Cheng, P., see Xue, G. 89 (1995) 77
Cheremskoy, P.G., see Skatkov, L.I. 81 (1994) 427
Chergui, A., see Deiss, J.L. 86 (1995) 149
Chiurlo, P., see Garbassi, F. 84 (1995) 145
Chiwaki, M., see Suzuki, R. 85 (1995) 87
Cho, K., J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai, Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces 87/88 (1995) 380
Choi, J.-G., see Lee, H.J. 89 (1995) 121
Chopra, K.L., see Rao, M.V.H. 89 (1995) 417
Choyke, W.J., see Yates, Jr., J.T. 82/83 (1994) 180
Chuah, G.K., see Cocke, D.L. 84 (1995) 153
Chub, A.B., see Khramtsova, E.A. 82/83 (1994) 576
Chvoj, Z., see Černý, R. 86 (1995) 359
Cifre, J., see Puigdollers, J. 86 (1995) 600
Claudon, X., see Buisson, L. 84 (1995) 211
Clement, M., see Van Veen, A. 85 (1995) 216
Coble, H.D., see Loo, B.H. 81 (1994) 175
Coccia, L., see King, S. 86 (1995) 134
Cocke, D.L., G.K. Chuah, N. Kruse and J.H. Block, Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry 84 (1995) 153
Cole, D., see Jordan, R. 86 (1995) 24
Coleman, P.G., see Knights, A.P. 85 (1995) 43
Coleman, P.G., see Overton, N. 85 (1995) 54
Coleman, P.G., see Goodyear, A. 85 (1995) 98
Coleman, P.G., E. Bloss, S. Setzler, S. LaShell, G. Davies and W.D. Sawyer, Slow positron implantation spectroscopy of edge-defined film-fed growth silicon 85 (1995) 276
Collaud-Coen, M., see Gröning, P. 89 (1995) 83
Colling, C.W., see Lee, H.J. 89 (1995) 121
Colón, G., see Navío, J.A. 81 (1994) 325
Colter, P.C., see Hayafuji, N. 82/83 (1994) 18
Compaan, A., see Dubowski, J.J. 86 (1995) 548
Condorelli, G.G., see Gulino, A. 90 (1995) 289
Cooke, P.W., see Umlor, M.T. 85 (1995) 295
Corbel, C., see Manuel, A.A. 85 (1995) 301
Coston, R., see Wee, A.T.S. 81 (1994) 377
Craciun, D., see Craciun, V. 86 (1995) 99
Craciun, V., S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd, Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition 86 (1995) 99
Craig, Jr., J.H., see Wang, P.W. 90 (1995) 413
Creighton, J.R., Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy 82/83 (1994) 171
Cros, A., see Grégoire, Ch. 84 (1995) 163
Cros, A., see Shafeev, G.A. 86 (1995) 387
Culp, R.D., see Jackson, M.S. 81 (1994) 195

D'Alessio, L., see Teghil, R. 86 (1995) 190
Dam, B., J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen, The laser ablation threshold of $YBa_2Cu_3O_{6+x}$ as revealed by using projection optics 86 (1995) 13
Danev, G., see Ihlemann, J. 86 (1995) 245
D'Anna, E., G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek, Excimer laser reactive ablation deposition of silicon nitride films 86 (1995) 170
Danoix, F., see Schmuck, C. 87/88 (1995) 228
Danoix, F., see Souchet, R. 87/88 (1995) 271
Dasbach, U., see Arnold, J. 86 (1995) 251
Daté, M., see Taguchi, Y. 82/83 (1994) 434
Dauwe, C., see Segers, D. 85 (1995) 172
David, S.A., see Babu, S.S. 87/88 (1995) 207
Davies, G., see Coleman, P.G. 85 (1995) 276
Davies, P.R., see Carley, A.F. 81 (1994) 265
Davies, R.E., see Smith, G.C. 90 (1995) 357
De Groot, D.G., see Dam, B. 86 (1995) 13
De Marco, R. and J. Liesegang, Surface analysis of commercial lead/acid battery grids 84 (1995) 237
De Maria, G., see Teghil, R. 86 (1995) 190
De Mierry, P., see Ballutaud, D. 84 (1995) 187
De Nijs, J.M.M., see Van Veen, A. 85 (1995) 216
Debauche, C., see Flicstein, J. 86 (1995) 286
Debauge, Y., M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort, Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and co-adsorption of CO and NO 90 (1995) 15
Debiemme-Chouvy, C., see Ballutaud, D. 84 (1995) 187
Declemy, A., see Durand, N. 81 (1994) 119
Deconihout, B., see Bas, P. 87/88 (1995) 298
Deconihout, B., A. Bostel, M. Bouet, J.M. Sarrau, P. Bas and D. Blavette, Perfor-

mance of the multiple events position sensitive detector used in the tomographic atom probe 87/88 (1995) 428
Deiana, L., see Garbassi, F. 84 (1995) 145
Deimel, M., see Reihs, K. 84 (1995) 107
Deiss, J.L., A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun, Pulsed laser deposition of epitaxial layers of ZnSe 86 (1995) 149
Deldime, M., J.-L. Dewez, Y.-J. Schneider and J. Marchand-Brynaert, Reactivity assay of surface carboxyl chain-ends of poly(ethylene terephthalate) (PET) film and track-etched microporous membranes using fluorine labelled- and/or ^{3}H-labelled derivatization reagents: tandem analysis by X-ray photoelectron spectroscopy (XPS) and liquid scintillation counting (LSC) 90 (1995) 1
Deleter, P., see Laude, L.D. 86 (1995) 368
Delgado, A.V., see Durán, J.D.G. 81 (1994) 1
Delobel, R., see Bourbigot, S. 81 (1994) 299
Delplancke, M.P., see Reniers, F. 81 (1994) 151
Demanet, C.M., Atomic force microscopy determination of the topography of fly-ash particles 89 (1995) 97
Demchuk, A.V. and V.A. Labunov, Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation 86 (1995) 353
DenBaars, S.P., see Keller, B.P. 82/83 (1994) 126
Deng, C., see Slaoui, A. 86 (1995) 346
Deng, J., H. Chen, X. Bao and M. Muhler, The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study 81 (1994) 341
Desimoni, E., see Salvi, A.M. 90 (1995) 333
Desjardins, P., see Meunier, M. 86 (1995) 475
Desjonquères, M.C., D. Spanjaard, B. Piveteau and S. Papadia, A simple approach to the calculation of surface defect energies in transition metals 87/88 (1995) 337
Dessaux, O., see Brocherieux, A. 90 (1995) 47
Devel, M., C. Girard, C. Joachim and O.J.F. Martin, Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study 87/88 (1995) 390
Devillers, M., O. Dupuis, A. Janosi and J.P. Soumillion, Coordination compounds as precursors for laser deposition of nickel-based conducting films 81 (1994) 83
Devine, R.A.B., see Parada, E.G. 86 (1995) 294
Dewez, J.-L., see Deldime, M. 90 (1995) 1
Dey, S.D., see Ray, N. 84 (1995) 203
Dhese, K., see Wagner, F.X. 86 (1995) 364
D'Huysser, A., see Souchet, R. 87/88 (1995) 271
Di Palma, T.M., S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele, Composition and gas dynamics of laser ablated AlN plumes 86 (1995) 68
Dieckhoff, S., see Gesang, T. 84 (1995) 273
Dietler, G., see Gröning, P. 89 (1995) 83
Dietrich, D., see Schlottig, F. 90 (1995) 129
Dietz, N., see Kelliher, J.T. 86 (1995) 453
Dillon, A.C., see George, S.M. 82/83 (1994) 460
Dimitrakis, P., see Thurzo, I. 90 (1995) 39
Dimitrova, T., see Atanassova, E. 84 (1995) 193
Ding, J., see Xue, G. 89 (1995) 77
Dip, A., see Hayafuji, N. 82/83 (1994) 18
Dirac, H., see Müllenborn, M. 86 (1995) 568
Dmitruk, N.L., E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets, Morphology, atomic composition and photoelectric properties of the microrelief InP–electrolyte interface 90 (1995) 489
Dodelet, J.P., see Weng, L.T. 84 (1995) 9
Domingue, A., see Piyakis, K. 84 (1995) 227
Domínguez, P.S., see Tejedor, P. 89 (1995) 271
Donaton, R.A., K. Lokere, R. Verbeeck and K. Maex, Etching of $CoSi_2$ in HF-based solutions 89 (1995) 221
Dorikens-Vanpraet, L., see Segers, D. 85 (1995) 172
Drachsel, W., see Gorodetskii, V. 87/88 (1995) 151
Dragnea, B., see Peled, A. 86 (1995) 538
Dreyfus, R.W., Why are high-T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm^2? 86 (1995) 29
Drozd, V.E., A.P. Baraban and I.O. Nikiforova, Electrical properties of Si–Al_2O_3 structures grown by ML-ALE 82/83 (1994) 583
Drozd, V.E., A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov, Synthesis of oxide superalloys by ML-ALE method 82/83 (1994) 587
Drozd, V.E. and V.B. Aleskovski, Synthesis of conducting oxides by ML-ALE 82/83 (1994) 591
Dubot, P., see Fauquet, C. 81 (1994) 435
Dubowski, J.J., A. Compaan and M. Prasad, Laser-assisted dry etching ablation of InP 86 (1995) 548
Dulac, O., see Flicstein, J. 86 (1995) 286
Dumont, H., Sz. Fujita and Sg. Fujita, Photo-assisted growth and characterization of $Zn_xCd_{1-x}S$ by MOVPE 86 (1995) 442
Dupuis, O., see Devillers, M. 81 (1994) 83
Durán, J.D.G., L. Zurita, M.C. Guindo, A.V. Delgado and F. González-Caballero, Surface thermodynamic properties of cadmium sulfide 81 (1994) 1
Durand, H.-A., J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis, Excimer laser sputtering deposition of TiO_2 optical coating for solar cells 86 (1995) 122
Durand, N., K.F. Badawi, A. Declemy and Ph. Goudeau, Origin of residual stress in

a textured Au thin film on a LiF substrate 81 (1994) 119
Durbin, S.M., see Gog, Th. 81 (1994) 485
Durrer, W.G., M. Portillo, P. Wang and D.P. Russell, Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission 81 (1994) 215
Duś, R., E. Nowicka, W. Lisowski and Z. Wolfram, Atomic hydrogen adsorption on sintered thin copper films 90 (1995) 277
Duval, S., S. Chambreland, D. Blavette, A. Loiseau and L. Potez, 3D reconstruction of antiphase boundaries in Cu_3Au from field ion images 87/88 (1995) 284
Dwyer, D.J., X.J. Pang, M. Gao and R.P. Wei, Surface enrichment of niobium on Inconel 718 (100) single crystals 81 (1994) 229
Dyer, P.E., D.M. Karnakis and G.A. Oldershaw, Analysis and experimental study of one-photon incubated absorption in polymers 86 (1995) 1
Dyer, P.E., P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner, Blast-wave studies of excimer laser ablation of ZnS 86 (1995) 18
Dyer, P.E., see Jackson, S.R. 86 (1995) 223

Eaglesham, D.J., see Weir, B.E. 84 (1995) 413
Easwarakhanthan, T., S. Ravelet and P. Renard, An ellipsometric procedure for the characterization of very thin surface films on absorbing substrates 90 (1995) 251
Ebeid, M.R., see Ashour, A. 89 (1995) 159
Egdell, R.G., see Gulino, A. 90 (1995) 289
Egdell, R.G., see Taverner, A.E. 90 (1995) 383
Ehrfeld, W., see Arnold, J. 86 (1995) 251
Ehrhardt, J.J., see Lobstein, N. 89 (1995) 307
Eisele, I., see Jiang, W. 86 (1995) 564
Ekerdt, J.G., see Jackson, M.S. 81 (1994) 195
Ekerdt, J.G., see Asami, S. 82/83 (1994) 359
El-Kader, K.M.A., see Černý, R. 86 (1995) 359
El-Kadry, N., see Ashour, A. 89 (1995) 159
El-Masry, N.A., see Bedair, S.M. 82/83 (1994) 7
El-Masry, N.A., see Hayafuji, N. 82/83 (1994) 18
Eldallal, G.M., see Hayafuji, N. 82/83 (1994) 18
Elders, J., see Craciun, V. 86 (1995) 99
Elers, K.-E., M. Ritala, M. Leskelä and E. Rauhala, $NbCl_5$ as a precursor in atomic layer epitaxy 82/83 (1994) 468
Elyaagoubi, N., see Meunier, M. 86 (1995) 475
Emmel, A., see Bergmann, H.W. 86 (1995) 259
Engelhard, H., F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann, Interfacial reaction of Ag with the InP(100)4 × 2 surface – a photoemission study 90 (1995) 89
Enomoto, A., see Kurihara, T. 85 (1995) 178
Enta, Y., N. Miyamoto, Y. Takakuwa and H. Kato, Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth 82/83 (1994) 327
Ernst, N., see Unger, J. 87/88 (1995) 45
Ernst, N., see Gorodetskii, V. 87/88 (1995) 151
Esrom, H., J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza, New approach of a laser-induced forward transfer for deposition of patterned thin metal films 86 (1995) 202
Estève, D., see Maury, F. 86 (1995) 447
Esteve, J., see Palau, J. 86 (1995) 59
Etcheberry, A., see Ballutaud, D. 84 (1995) 187
Evans, J.F., see Schulze, R.K. 81 (1994) 449

Fähler, S., see Krebs, H.-U. 86 (1995) 86
Fahy, M.R., K. Sato and B.A. Joyce, Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A 82/83 (1994) 14
Fajgar, R., M. Jakoubková, Z. Bastl and J. Pola, Germanium-containing coatings by IR laser-induced decomposition of ethoxy(trimethyl)germane and tetramethylgermane 86 (1995) 530
Fang, J., see Ji, G. 81 (1994) 63
Fang, Y., C. Bai, T. Wang and Y.-Q. Tang, Characterization of triplex RNA poly [rU] · poly[rA] · poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy 89 (1995) 331
Fanter, D., see Gesang, T. 84 (1995) 273
Farrell, T. and J.V. Armstrong, In-situ laser reflectometry of the epitaxial growth of thin semiconductor films 86 (1995) 582
Fauquet, C., P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte, Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces 81 (1994) 435
Fayette, L., see Le Normand, F. 81 (1994) 309
Fazleev, N.G., J.L. Fry, K. Kuttler and A.H. Weiss, Theoretical study of the positron surface state at an alkali-metal surface 85 (1995) 22
Fazleev, N.G., J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss, Study of positron surface states on the alkali-metal-covered transition-metal surface 85 (1995) 26
Fazouan, N., see Maury, F. 86 (1995) 447
Fedotov, A.K., M.I. Tarasik and A.M. Yanchenko, Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam 84 (1995) 379
Fei, X., see Wang, J. 84 (1995) 383
Feldman, L.C., see Weir, B.E. 84 (1995) 413
Feng, Z.C., see Wee, A.T.S. 81 (1994) 377

Ferrater, C., see Queralt, X. 86 (1995) 95
Ferro, D., see Teghil, R. 86 (1995) 190
Fígoli, N.S., see L'Argentière, P.C. 89 (1995) 63
Fitzpatrick, J.J., see Hansen, D.C. 84 (1995) 85
Flamant, G., see Mazhukin, V.I. 86 (1995) 7
Flamant, G., see Berjeza, N.A. 86 (1995) 303
Fleischer, S., see Panda, B.K. 85 (1995) 182
Flicstein, J., Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe, Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics 86 (1995) 286
Flicstein, J., see Parada, E.G. 86 (1995) 294
Fogarassy, E., see Antoni, F. 86 (1995) 175
Fogarassy, E., see Mathé, E.L. 86 (1995) 338
Follis, G.C., see Gog, Th. 81 (1994) 485
Fontaine, M.-F., see Le Mercier, T. 86 (1995) 382
Forbes, R.G., Field evaporation theory: a review of basic ideas 87/88 (1995) 1
Forbes, R.G., G.L.R. Mair, N.N. Ljepojevic and W. Liu, New understandings in the theory of liquid-metal ion sources 87/88 (1995) 99
Forbes, R.G., see Liu, W. 87/88 (1995) 122
Fragalà, I., see Gulino, A. 90 (1995) 289
Freer, B.S., see Kosowsky, S.D. 84 (1995) 179
Frerichs, H., see Kreutz, E.W. 86 (1995) 266
Frerichs, H., J. Stricker, D.A. Wesner and E.W. Kreutz, Laser-induced surface modification and metallization of polymers 86 (1995) 405
Fretwell, J., see Asami, S. 82/83 (1994) 359
Friedbacher, G., E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux, Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy 84 (1995) 133
Froben, F.W., see Yu, H. 86 (1995) 74
Frommeyer, G., see Wesemann, J. 87/88 (1995) 179
Fry, J.L., see Fazleev, N.G. 85 (1995) 22
Fry, J.L., see Fazleev, N.G. 85 (1995) 26
Fuchs, C., see Antoni, F. 86 (1995) 175
Fuchs, G., see Friedbacher, G. 84 (1995) 133
Fujishima, A., see Loo, B.H. 81 (1994) 175
Fujita, K., see Hirai, M. 82/83 (1994) 23
Fujita, Sg., see Fujita, Sz. 86 (1995) 431
Fujita, Sg., see Dumont, H. 86 (1995) 442
Fujita, Sz. and Sg. Fujita, Photoassisted growth of II–VI semiconductor films 86 (1995) 431
Fujita, Sz., see Dumont, H. 86 (1995) 442
Fukutani, K., see Kanazawa, I. 85 (1995) 124
Fung, S., see Panda, B.K. 85 (1995) 182
Fung, S., see Ling, C.C. 85 (1995) 305
Furukawa, H., see Yoshida, I. 82/83 (1994) 501
Furukawa, S., see Hwang, S.M. 82/83 (1994) 523
Fuso, F., see Amoruso, S. 86 (1995) 35
Gambardella, U., A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels, Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time 86 (1995) 45
Gamo, K., see Meguro, T. 82/83 (1994) 193
Gamo, K., see Ishii, M. 86 (1995) 554
Ganem, J.-J., see Bréelle, E. 81 (1994) 127
Gao, M., see Dwyer, D.J. 81 (1994) 229
Garbassi, F., L. Balducci, P. Chiurlo and L. Deiana, A study of surface modification of silica using XPS, DRIFT and NMR 84 (1995) 145
Garcia Lopez, J., see Aubert, P. 86 (1995) 144
Gardella, Jr., J.A., see Li, J.-X. 90 (1995) 205
Gardeniers, J.G.E., see Craciun, V. 86 (1995) 99
Garofalini, S.H., see Hensley, D.A. 81 (1994) 331
Garry, G., see Aubert, P. 86 (1995) 144
Garten, R.P.H., see Bubert, H. 81 (1994) 203
Gasser, A., see Kreutz, E.W. 86 (1995) 310
Gates, S.M., see Koleske, D.D. 82/83 (1994) 344
Ge, Q. and P.J. Møller, CO adsorption on clean and atomic-layer-Cu-covered ZnO($10\bar{1}0$) surfaces 82/83 (1994) 305
Geber, G.P., An APFIM/TEM investigation of the discontinuous precipitation in a Ni–In alloy 87/88 (1995) 234
Gengembre, L., see Bourbigot, S. 81 (1994) 299
Gengembre, L., see Brocherieux, A. 90 (1995) 47
George, S.M., see Okada, L.A. 82/83 (1994) 410
George, S.M., O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way, Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry 82/83 (1994) 460
Geretovszky, Zs., L. Kelemen, K. Bali and T. Szörényi, Kinetic model for scanning laser-induced deposition from the liquid phase 86 (1995) 494
Geretovszky, Zs., see Bali, K. 86 (1995) 500
Gerola, D., W.B. Waeber and M. Shi, Design and simulation of the PSI electrostatic positron beam 85 (1995) 106
Gerola, D., see Shi, M. 85 (1995) 143
Gesang, T., R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann, AFM investigations of the initial stages of prepolymer film growth on aluminium 84 (1995) 273
Gesbert, D., see Durand, H.-A. 86 (1995) 122
Geus, J.W., see Bolt, P.H. 89 (1995) 339
Geus, J.W., see Van Kooten, W.E.J. 90 (1995) 137
Geus, J.W., see Van Wijk, R. 90 (1995) 261
Gewinner, G., see Hong, S. 90 (1995) 65
Ghosh, T.B., see Sreemany, M. 81 (1994) 365
Ghosh, T.B., see Sreemany, M. 90 (1995) 241
Ghosh, V.J., Positron implantation profiles in elemental and multilayer systems 85 (1995) 187

Ghosh, V.J., B. Nielsen, K.G. Lynn and D.O. Welch, Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles 85 (1995) 210
Giardini, A., see Gambardella, U. 86 (1995) 45
Giardini-Guidoni, A., see Di Palma, T.M. 86 (1995) 68
Giardini-Guidoni, A., see Teghil, R. 90 (1995) 505
Gijzeman, O.L.J., see Van Kooten, W.E.J. 90 (1995) 137
Gijzeman, O.L.J., see Van Wijk, R. 90 (1995) 261
Girard, C., see Devel, M. 87/88 (1995) 390
Givargizov, E.I., V.V. Zhirnov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov, Microstructure and field emission of diamond particles on silicon tips 87/88 (1995) 24
Givord, D., see Jordan, R. 86 (1995) 24
Gleditzsch, S., see Reihs, K. 84 (1995) 107
Gog, Th., G.C. Follis and S.M. Durbin, LiBr on Si(111): an X-ray standing wave measurement 81 (1994) 485
Gol'berg, S.M., see Sobol, E.N. 90 (1995) 235
Goldberg, R.D., see Aers, G.C. 85 (1995) 196
Goldberg, R.D., P.J. Schultz and P.J. Simpson, Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon 85 (1995) 287
Goldmann, A., see Kürpick, U. 89 (1995) 383
Goldmann, A., see Engelhard, H. 90 (1995) 89
Gomozov, V.P., see Skatkov, L.I. 81 (1994) 427
Gonda, S., see Kim, J.H. 82/83 (1994) 76
Gonda, S., see Asahi, H. 82/83 (1994) 109
González, H., see Néron de Surgy, G. 87/88 (1995) 91
González, P., see Parada, E.G. 86 (1995) 294
González, S., see Hernández Creus, A. 81 (1994) 387
González-Caballero, F., see Durán, J.D.G. 81 (1994) 1
González-Martín, M.L., see Jańczuk, B. 81 (1994) 95
Gonzalo, J., C.N. Afonso, F. Vega, D. Martínez García and J. Perrière, Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films 86 (1995) 40
Goodyear, A., see Overton, N. 85 (1995) 54
Goodyear, A. and P.G. Coleman, Development of a reflection geometry positron reemission microscope 85 (1995) 98
Gorenstein, A., see Julien, C. 90 (1995) 389
Gorochov, O., see Bourée, J.E. 86 (1995) 437
Gorodetskii, V., N. Ernst, W. Drachsel and J.H. Block, Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter 87/88 (1995) 151
Gorshkov, V.N., see Vladimirov, V.V. 87/88 (1995) 112
Görts, P.C., see Van Wijk, R. 90 (1995) 261
Goto, A., see Itoh, Y. 85 (1995) 165
Goto, H., see Suzuki, T. 82/83 (1994) 103
Goto, K., see Takemi, M. 82/83 (1994) 115
Goto, S., see Ohno, H. 82/83 (1994) 164
Gotoda, M., H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita, Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE 82/83 (1994) 80
Goudeau, Ph., see Durand, N. 81 (1994) 119
Goudmand, P., see Brocherieux, A. 90 (1995) 47
Grangeon, F., H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine, Pulsed laser deposition of $NbTe_x$ thin films 86 (1995) 160
Gråsjö, L., G. Hultquist, K.L. Tan and M. Seo, Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry 89 (1995) 21
Grasserbauer, M., see Friedbacher, G. 84 (1995) 133
Greer, A.L., Diffusion and reactions in thin films 86 (1995) 329
Grégoire, Ch., J.-J. Pireaux, A. Cros and R. Caudano, High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation 84 (1995) 163
Griessen, R., see Dam, B. 86 (1995) 13
Griffiths, K., see Kasza, R.V. 84 (1994) 97
Grimblot, J., see Brocherieux, A. 90 (1995) 47
Gröning, P., O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlapbach, Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment 89 (1995) 83
Grozdanov, I., Solution growth and characterization of silver sulfide films 84 (1995) 325
Grun, J.B., see Deiss, J.L. 86 (1995) 149
Gu, H.C., see Wang, X.K. 89 (1995) 297
Gu, S., R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng, Raman study of strained SiGe layers 81 (1994) 431
Guay, D., see Weng, L.T. 84 (1995) 9
Guay, D., see Lamontagne, B. 90 (1995) 481
Guczi, L., see Sundararajan, R. 90 (1995) 165
Gué, A.M., see Maury, F. 86 (1995) 447
Guesdon, J.P., see Julien, C. 90 (1995) 389
Guindo, M.C., see Durán, J.D.G. 81 (1994) 1
Gulino, A., G.G. Condorelli, I. Fragalà and R.G. Egdell, Surface segregation of Sb in doped TiO_2 rutile 90 (1995) 289
Gulino, A., see Taverner, A.E. 90 (1995) 383
Gunter, P.L.J., see Van Hardeveld, R.M. 84 (1995) 339
Gunter, P.L.J. and J.W. Niemantsverdriet, Thickness determination of uniform overlayers on rough substrates by angle-dependent XPS 89 (1995) 69
Güntherodt, H.-J., see Sum, R. 86 (1995) 140
Guo, S., G. Xue and Y. Qian, Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole 84 (1995) 351
Gurin, V.S. and A.B. Kovrikov, STM-stimulated modification of solids: a quantum chemical study 81 (1994) 43

Habermehl, S., see Kelliher, J.T. 86 (1995) 453
Habraken, F.H.P.M., see Bolt, P.H. 89 (1995) 339
Habraken, F.H.P.M., see Van Wijk, R. 90 (1995) 261
Hachimi, A., see Lobstein, N. 89 (1995) 307
Hadj Zoubir, N. and M. Vergnat, Thermal desorption spectroscopy study of chemically etched porous silicon 89 (1995) 35
Hagenhoff, B., see Reihs, K. 84 (1995) 107
Hagmann, M.J., Simulations of rectification in a laser-illuminated scanning tunneling microscope 87/88 (1995) 368
Hague, C.F., see Le Mercier, T. 86 (1995) 382
Hakvoort, R.A., A. van Veen, P.E. Mijnarends and H. Schut, Helium and hydrogen-decorated cavities in silicon 85 (1995) 271
Hamada, A., see Sueoka, O. 85 (1995) 59
Hamada, A. and O. Sueoka, Total cross-section measurements for positrons and electrons colliding with molecules: CCl_4 85 (1995) 64
Hammer, C.F., see Ye, X.R. 89 (1995) 151
Hammer, L., see Starke, U. 89 (1995) 175
Han, P., see Gu, S. 81 (1994) 431
Han, R., see Ling, C.C. 85 (1995) 305
Hanabusa, M. and A. Komatsu, UV light irradiation effects on nucleation during chemical vapor deposition of Al films 86 (1995) 428
Hanada, T., see Kawai, M. 82/83 (1994) 487
Hanebuchi, M., T. Katoh and K. Morita, Characterization of thin Ag films deposited onto InP(001)-p(2×4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques 89 (1995) 113
Haneman, D., see Wu, S. 89 (1995) 289
Hansen, D.C., E. McCafferty, C.W. Lins and J.J. Fitzpatrick, An FT-IR investigation of parabactin adsorbed onto aluminum 84 (1995) 85
Hara, K., see Suzuki, T. 82/83 (1994) 103
Hara, K., see Kano, N. 82/83 (1994) 132
Hariharan, K., see Van Bakel, G.P.E.M. 90 (1995) 95
Hartner, W., see Starke, U. 89 (1995) 175
Hartwig, A., see Gesang, T. 84 (1995) 273
Hasegawa, F., see Akamatsu, M. 82/83 (1994) 228
Hasegawa, M., see Kawasuso, A. 85 (1995) 280
Hashimoto, K., see Loo, B.H. 81 (1994) 175
Hashimoto, K., see Arai, M. 89 (1995) 11
Hashizume, T., see Bakhtizin, R.Z. 87/88 (1995) 347
Hashizume, T., see Xue, Q. 87/88 (1995) 364
Hashizume, T., Q.K. Xue, A. Ichimiya and T. Sakurai, Structure of the MBE-grown GaAs(001)-(2×4) phase 87/88 (1995) 373
Hashizume, T., see Cho, K. 87/88 (1995) 380
Hashizume, T., see Jeon, D. 87/88 (1995) 386
Hashizume, T., see Sakurai, T. 87/88 (1995) 405
Haslingerová, I., see Pingo, M. 90 (1995) 373
Hastie, J.W., see Di Palma, T.M. 86 (1995) 68
Hata, K., M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita, A FEM study of liquid lithium on a ⟨011⟩-oriented tungsten tip 87/88 (1995) 117
Hatab, Z.R., S.L. Prins, S.S.H. Naqvi and J.R. McNeil, 16 MB DRAM trench depth characterization using dome scatterometry 86 (1995) 597
Hatta, A., see Suzuki, Y. 84 (1995) 1
Hattori, T., see Kanazawa, I. 85 (1995) 124
Haubner, R., see Friedbacher, G. 84 (1995) 133
Haukka, S., E.-L. Lakomaa and T. Suntola, Surface coverage of ALE precursors on oxides 82/83 (1994) 548
Hautojärvi, P., see Vaari, J. 81 (1994) 289
Hautojärvi, P., see Manuel, A.A. 85 (1995) 301
Hautojärvi, P., see Vaara, T. 89 (1995) 103
Hayafuji, N., G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair, Atomic layer epitaxy of device quality AlGaAs and AlAs 82/83 (1994) 18
Headrick, R.L., see Weir, B.E. 84 (1995) 413
Heinonen, M.H., see Leiro, J.A. 90 (1995) 515
Heinz, K., see Starke, U. 89 (1995) 175
Heitz, J., E. Arenholz, D. Bäuerle and K. Schilcher, Growth of excimer-laser-induced dendritic surface structures on polyethylene-terephthalate 81 (1994) 103
Heitzinger, J.M., see Jackson, M.S. 81 (1994) 195
Helbing, R., see Bourée, J.E. 86 (1995) 437
Hellman, O., see Durand, H.-A. 86 (1995) 122
Hennemann, O.-D., see Gesang, T. 84 (1995) 273
Hensley, D.A. and S.H. Garofalini, XPS investigation of lithium borate glass and the $Li/LiBO_2$ interface 81 (1994) 331
Henzler, M., see Zielasek, V. 90 (1995) 117
Hernández Creus, A., R.M. Souto, S. González, M.M. Laz, R.C. Salvarezza and A.J. Arvia, The electrochemical faceting of copper in 85% aqueous o-phosphoric acid by using a potential reversal technique 81 (1994) 387
Hesch, K., see Arnold, J. 86 (1995) 251
Hess, P., see Karstens, H. 86 (1995) 521
Hess, P., see Kolomenskii, A.A. 86 (1995) 591
Hetherington III, W.M., see Wijekoon, W.M.K.P. 81 (1994) 347
Heun, S., M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima, Morphology of epitaxial SrF_2 films on atomically modified InP(100) 82/83 (1994) 507
Hibino, H. and T. Ogino, Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111) 82/83 (1994) 374
Himei, H., E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto, Theoretical estimation of ordered metal species in zeolite pores 82/83 (1994) 543
Hirabayashi, I., see Matsubara, M. 82/83 (1994) 494
Hirai, M., H. Ohnishi, K. Fujita and T. Watanabe, Substrate misorientation de-

pendence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A 82/83 (1994) 23
Hiraoka, H., see Lätsch, S. 81 (1994) 183
Hirosawa, T., see Yoshida, I. 82/83 (1994) 501
Hirose, M., M. Washio and K. Takahashi, Production of an intense slow positron beam using a compact cyclotron 85 (1995) 111
Hirose, M., see Kanazawa, I. 85 (1995) 124
Hirose, S., see Kano, N. 82/83 (1994) 132
Hng, H.H., see Wee, A.T.S. 81 (1994) 377
Hoekje, S.J., see Outlaw, R.A. 81 (1994) 143
Hofmann, A., see Schlottig, F. 90 (1995) 129
Hofmann, S. and M.G. Stepanova, Preferential sputtering of argon ion bombarded Ni_3Al and $TaSi_2$ 90 (1995) 227
Holmes Jr., A.L., see Keller, B.P. 82/83 (1994) 126
Holt, S.A., R. Zhao and S. Myhra, Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration 84 (1995) 125
Homma, Y., see Yamaguchi, H. 82/83 (1994) 223
Honda, Y., see Nunogaki, M. 85 (1995) 132
Hong, J.K., I.-H. Oh, S.-A. Hong and W.Y. Lee, The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte 89 (1995) 229
Hong, S., C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner, Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation 90 (1995) 65
Hong, S.-A., see Hong, J.K. 89 (1995) 229
Hongo, S., S. Taniguchi, K. Ojima, T. Urano and T. Kanaji, Adsorption and desorption of H_2O on potassium precovered Si(100)2 × 1 surface 82/83 (1994) 437
Hongo, S., K. Ojima, S. Taniguchi, T. Urano and T. Kanaji, Observation of the interface of Ba/Si(100) by MDS and TDS 82/83 (1994) 537
Hono, K. and T. Sakurai, Atom probe studies of nanostructured alloys 87/88 (1995) 166
Hono, K., see Ringer, S.P. 87/88 (1995) 223
Hono, K., R. Okano, T. Saeda and T. Sakurai, The performance of the IMR three-dimensional atom probe 87/88 (1995) 453
Hono, K., see Ringer, S.P. 90 (1995) 107
Hood, G.M., see Zou, H. 90 (1995) 59
Höper, R., see Gesang, T. 84 (1995) 273
Hopkins, J., M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter, A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE 84 (1995) 299
Horikoshi, Y., see Yamaguchi, H. 82/83 (1994) 223
Hosea, T.J.C., see Carline, R.T. 81 (1994) 475
Hou, H.W., see Ye, X.R. 89 (1995) 151
Hozhabri, N., A.R. Koymen, S.C. Sharma and K. Alavi, Defects and arsenic distribution in low-temperature-grown GaAs 85 (1995) 311
Hrovatin, R. and J. Možina, Optodynamic aspect of a pulsed laser ablation process 86 (1995) 213
Hsu, C.-H., see Kosowsky, S.D. 84 (1995) 179
Hu, R., see Wee, A.T.S. 81 (1994) 377
Hu, X. and Z. Lin, Hydrogen adsorption induced phase transitions on Si(100)-c(8 × 8): temperature dependence studied by LEED 90 (1995) 111
Huang, M., R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade, Development of a FEM, FIM-AP system for studying gridded vacuum microelectronic devices 87/88 (1995) 421
Huang, M., S. Kaliaguine and S. Suppiah, Surface interaction between H_2 and CO_2 over silicalite-supported platinum 90 (1995) 393
Huang, Y.S., see Mar, S.Y. 90 (1995) 497
Huber, M.G., see Yu, H. 86 (1995) 74
Hübner, A., see Yates, Jr., J.T. 82/83 (1994) 180
Hulett, Jr., L.D., see Xu, J. 85 (1995) 49
Hulett, Jr., L.D., S. Wallace, J. Xu, B. Nielsen, Cs. Szeles, K.G. Lynn, J. Pfau and A. Schaub, Assay of weathering effects on protective polymer coatings using positron annihilation spectroscopy 85 (1995) 334
Hultquist, G., see Gråsjö, L. 89 (1995) 21
Hwang, S.M., A. Izumi, K. Tsutsui and S. Furukawa, Surface modification of CaF_2 in atomic layer scale by electron beam exposure 82/83 (1994) 523
Hyde, J.M., M.K. Miller, A. Cerezo and G.D.W. Smith, A study of the effect of ageing temperature on phase separation in Fe–45%Cr alloys 87/88 (1995) 311
Hyde, J.M., see Miller, M.K. 87/88 (1995) 323

Ichimiya, A., see Kanazawa, I. 85 (1995) 124
Ichimiya, A., see Hashizume, T. 87/88 (1995) 373
Ichimura, S., see Sekine, S. 84 (1995) 401
Ide, Y. and M. Yamada, Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography 82/83 (1994) 310
Ignatiev, A., see Zomorrodian, A. 90 (1995) 343
Ihlemann, J. and B. Wolff-Rottke, Excimer laser ablation patterning of dielectric layers 86 (1995) 228
Ihlemann, J., B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova, Structuring of polyimide–metal carbide layer systems by excimer laser ablation 86 (1995) 245
IJpma, M.R., see Van Veen, A. 85 (1995) 216
Ikari, A., Defects in Czochralski-grown silicon crystals investigated by positron annihilation 85 (1995) 253

Ikeda, H., Y. Miura, N. Takahashi, A. Koukitu and H. Seki, Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy 82/83 (1994) 257
Ikeda, H., see Suda, Y. 82/83 (1994) 332
Il'chenko, L.G., Yu.V. Kryuchenko and V.G. Litovchenko, Electron field emission (FE) from quantum size systems 87/88 (1995) 53
Imai, S. and M. Matsumura, Hydrogen atom assisted ALE of silicon 82/83 (1994) 322
Imai, S., see Sugahara, S. 82/83 (1994) 380
Imai, S., see Sugahara, S. 90 (1995) 349
Inada, T., see Kiyota, Y. 82/83 (1994) 400
Inoue, N., see Yokoyama, H. 82/83 (1994) 158
Ionescu, R., C. Moise and A. Vancu, Are modulations of the Schottky surface barrier the only explanation for the gas-sensing effects in sintered SnO_2? 84 (1995) 291
Ishida, H., see Yoshida, S. 89 (1995) 39
Ishida, M., see Suda, Y. 82/83 (1994) 332
Ishii, A. and T. Aisaka, Surface barrier sensitivity of positronium formation at surfaces 85 (1995) 33
Ishii, A., see Kato, M. 85 (1995) 69
Ishii, M., see Meguro, T. 82/83 (1994) 193
Ishii, M., T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi, Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching 86 (1995) 554
Ishikawa, K., see Yago, H. 84 (1995) 119
Isshiki, H., Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro, Surface processes of selective growth by atomic layer epitaxy 82/83 (1994) 57
Isu, T., see Gotoda, M. 82/83 (1994) 80
Ito, H., see Suzuki, T. 82/83 (1994) 103
Ito, S., see Kameoka, S. 89 (1995) 411
Ito, T., K. Shiraishi and T. Ohno, A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $Al_xGa_{1-x}As$ on a GaAs(001) surface 82/83 (1994) 208
Ito, Y., see Kanazawa, I. 85 (1995) 124
Ito, Y., see Itoh, Y. 85 (1995) 165
Ito, Y., see Aruga, T. 85 (1995) 229
Ito, Y., see Oshima, N. 85 (1995) 329
Itoh, Y., K.H. Lee, T. Nakajyo, A. Goto, N. Nakanishi, M. Kase, I. Kanazawa, Y. Yamamoto, N. Oshima and Y. Ito, Slow positron production using the RIKEN AVF cyclotron 85 (1995) 165
Ivanov, I., see Julien, C. 90 (1995) 389
Ivanov, V.A., see Tumareva, T.A. 87/88 (1995) 18
Ivchenko, V.A. and N.N. Syutkin, Effect of low-energy (20–40 keV) ion implantation on phase transformations in the subsurface volume of alloys 87/88 (1995) 257
Iwai, S., see Isshiki, H. 82/83 (1994) 57
Iwasa, I., see Otake, S. 82/83 (1994) 263
Iwashita, T., see Oshima, N. 85 (1995) 329
Iwata, K., see Kim, J.H. 82/83 (1994) 76
Iwata, T. and K.-S. Chang, A quantitative estimation of the sensitivity of field-emission pressure-gauge 87/88 (1995) 31
Izquierdo, R., see Meunier, M. 86 (1995) 475
Izquierdo, R., J. Bertomeu, M. Suys, E. Sacher and M. Meunier, Excimer laser-induced deposition of copper from Cu(hfac)(TMVS) 86 (1995) 509
Izumi, A., see Hwang, S.M. 82/83 (1994) 523
Jackson, M.S., J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt, A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100) 81 (1994) 195
Jackson, S.R., W.J. Metheringham and P.E. Dyer, Excimer laser ablation of Nd:YAG and Nd:glass 86 (1995) 223
Jackson, S.R., see Wagner, F.X. 86 (1995) 364
Jackson, S.T. and R.G. Nuzzo, Determining hybridization differences for amorphous carbon from the XPS C 1s envelope 90 (1995) 195
Jain, A., A.K. Razdan, P.N. Kotru and B.M. Wanklyn, Chemical etching of (100) and (110) faces of flux-grown $LaBO_3$ crystals 84 (1995) 65
Jakoubková, M., see Fajgar, R. 86 (1995) 530
Jańczuk, B., M.L. González-Martín and J.M. Bruque, The adsorption of sodium dodecyl sulphate on fluorite and its surface free energy 81 (1994) 95
Janosi, A., see Devillers, M. 81 (1994) 83
Jansen, F., see Pflüger, S. 86 (1995) 504
Jardinier-Offergeld, M., see Reniers, F. 81 (1994) 151
Jeon, D., H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai, MnCu surface alloy studied by scanning tunneling microscopy 87/88 (1995) 386
Ji, G., J. Fang, S. Cai and G. Xue, Grafting onto the surface of plasma-modified fillers 81 (1994) 63
Jiang, S., D. Peng, X. Zhao, L. Xie and Q. Li, Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering 84 (1995) 373
Jiang, W., H. Baumgärtner and I. Eisele, Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm 86 (1995) 564
Jimbo, T., see Soga, T. 82/83 (1994) 64
Jin, B., see Sueoka, O. 85 (1995) 59
Jo, B.H. and R.W. Vook, Dependence of electromigration rate on applied electric potential 89 (1995) 237
Joachim, C., see Devel, M. 87/88 (1995) 390

Joag, D.S., see Adsool, A.D. 87/88 (1995) 37
Johansen, H., see Reisse, G. 86 (1995) 107
Johansen, H., see Reisse, G. 86 (1995) 114
Jordan, R., D. Cole, J.G. Lunney, K. Mackay and D. Givord, Pulsed laser ablation of copper 86 (1995) 24
Jostsons, A., see Miller, M.K. 87/88 (1995) 216
Joyce, B.A., see Fahy, M.R. 82/83 (1994) 14
Julien, C., J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov, The influence of the substrate material on the growth of V_2O_5 flash-evaporated films 90 (1995) 389
Jung, E., see Weiss, A.H. 85 (1995) 82

Kadoshima, M., see Sugahara, S. 90 (1995) 349
Kafader, U., H. Sirringhaus and H. von Känel, In situ DC-plasma cleaning of silicon surfaces 90 (1995) 297
Kajiyama, K., Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen) 85 (1995) 259
Kaliaguine, S., see Huang, M. 90 (1995) 393
Kalomiros, J.A., see Kennou, S. 90 (1995) 283
Kameoka, S., T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori, The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide 89 (1995) 411
Kamidoi, S., see Butman, M.F. 89 (1995) 323
Kanaji, T., see Hongo, S. 82/83 (1994) 437
Kanaji, T., see Hongo, S. 82/83 (1994) 537
Kanazawa, I., Y. Ito, M. Hirose, H. Abe, O. Sueoka, S. Takamura, A. Ichimiya, Y. Murata, F. Komori, K. Fukutani, S. Okada and T. Hattori, Production of an intense slow positron beam by using an electron LINAC and its applications 85 (1995) 124
Kanazawa, I., see Itoh, Y. 85 (1995) 165
Kanazawa, I., see Oshima, N. 85 (1995) 329
Kaneko, H., see Okada, S. 85 (1995) 149
Kano, N., S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto, AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source 82/83 (1994) 132
Kántor, Z., Z. Tóth and T. Szörényi, Metal pattern deposition by laser-induced forward transfer 86 (1995) 196
Kántor, Z., see Szörényi, T. 86 (1995) 219
Kantor, Z., see Piglmayer, K. 86 (1995) 484
Kargl, P.B., see Arnold, N. 86 (1995) 457
Karnakis, D.M., see Dyer, P.E. 86 (1995) 1
Kars, S., see Dam, B. 86 (1995) 13
Karstens, H., J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess, VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling 86 (1995) 521
Kartio, I., see Laajalehto, K. 81 (1994) 11
Kase, M., see Itoh, Y. 85 (1995) 165
Kasza, R.V., K. Griffiths, V.P. Zhdanov and P.R. Norton, Nucleation and island growth during water adsorption at submonolayer coverages 84 (1994) 97
Katayama, I., see Ohnishi, H. 82/83 (1994) 444
Katayama, I., see Tanaka, Y. 82/83 (1994) 528
Katayama, M., see Kawai, M. 82/83 (1994) 487
Katayama, Y., see Ohno, H. 82/83 (1994) 164
Kato, H., see Enta, Y. 82/83 (1994) 327
Kato, M. and A. Ishii, Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions 85 (1995) 69
Katoh, T., see Hanebuchi, M. 89 (1995) 113
Kawai, M., Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville, Layer controlled growth of oxide superconductors 82/83 (1994) 487
Kawanishi, H., see Takahashi, I. 82/83 (1994) 70
Kawano, H., see Butman, M.F. 89 (1995) 323
Kawasaki, M., see Song, Z. 82/83 (1994) 250
Kawasuso, A., M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino, An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique 85 (1995) 280
Keeble, D.J., see Umlor, M.T. 85 (1995) 295
Keil, M., J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw, The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces 90 (1995) 377
Keinonen, J., see Ahlgren, T. 90 (1995) 419
Keiper, B., see Reisse, G. 86 (1995) 107
Keiper, B., see Reisse, G. 86 (1995) 114
Kelber, J.A., see Nuesca, G. 81 (1994) 237
Kelemen, L., see Geretovszky, Zs. 86 (1995) 494
Keller, B.P., J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra, Flow modulation epitaxy of $Ga_xIn_{1-x}As$/AlAs heterostructures on InP for resonant tunneling diodes 82/83 (1994) 126
Kelliher, J.T., A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann, Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance 86 (1995) 453
Kellogg, G.L., Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces 87/88 (1995) 353
Kelly, T.F., see Camus, P.P. 87/88 (1995) 305
Kelly, T.F., see Bajikar, S.S. 87/88 (1995) 438

Kelly, T.F., see Larson, D.J. 87/88 (1995) 446
Kennou, S., S. Ladas, E.C. Paloura and J.A. Kalomiros, Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy 90 (1995) 283
Key, P.H., see Dyer, P.E. 86 (1995) 18
Key, P.H., see Wagner, F.X. 86 (1995) 364
Khatri, R., see Lawther, D.W. 85 (1995) 265
Khelfa, A., see Julien, C. 90 (1995) 389
Khramtsova, E.A., A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits, Growth of extra-thin ordered aluminum films on Si(111) surface 82/83 (1994) 576
Kilner, J.A., see Bréelle, E. 81 (1994) 127
Kim, C.O., see Kim, T.W. 90 (1995) 75
Kim, J.H., H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda, Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices 82/83 (1994) 76
Kim, J.H., see Yang, G. 85 (1995) 77
Kim, S.G., see Kim, J.H. 82/83 (1994) 76
Kim, S.G., see Asahi, H. 82/83 (1994) 109
Kim, T.W., Y.S. Yoon, S.S. Yom and C.O. Kim, Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition 90 (1995) 75
Kimura, S., see Murakami, E. 82/83 (1994) 338
Kimura, T., see Takemi, M. 82/83 (1994) 115
King, R.A., R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade, Atom probe field ion microscope studies of palladium silicide on silicon 87/88 (1995) 279
King, S., L. Coccia and I.W. Boyd, SEM observations of YBCO on as-received and heat-treated MgO substrates 86 (1995) 134
Kinser, D.L., see Wang, P.W. 84 (1995) 75
Kirbitson, R., see Wagner, F.X. 86 (1995) 364
Kirsanova, T.S., see Tumareva, T.A. 87/88 (1995) 18
Kiselev, A.N., see Givargizov, E.I. 87/88 (1995) 24
Kishimoto, J., see Cho, K. 87/88 (1995) 380
Kitai, M.S., see Sobol, E.N. 90 (1995) 235
Kitamura, T., see Sugahara, S. 82/83 (1994) 380
Kitamura, T., see Sugahara, S. 90 (1995) 349
Kiyota, Y., T. Nakamura and T. Inada, Boron δ-doping in Si using atmospheric pressure CVD 82/83 (1994) 400
Kleps, I., see Caccavale, F. 81 (1994) 443
Klotzbücher, T., W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz, Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD) 86 (1995) 165
Knights, A.P. and P.G. Coleman, Secondary electron emission from Ag(100) stimulated by positron and electron impact 85 (1995) 43
Knights, A.P., see Overton, N. 85 (1995) 54
Knobloch, J., see Karstens, H. 86 (1995) 521
Knoll, W., see Piscevic, D. 90 (1995) 425
Kobayashi, H., F. Mizuno and Y. Nakato, Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells 81 (1994) 399
Kobayashi, H., see Kurihara, T. 85 (1995) 178
Kobayashi, M., see Yoshikawa, A. 82/83 (1994) 316
Kobayashi, N. and T. Makimoto, Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs 82/83 (1994) 284
Kobayashi, N., see Uwai, K. 82/83 (1994) 290
Kobayashi, T., see Akamatsu, M. 82/83 (1994) 228
Koch, M., see Stoll, H. 85 (1995) 17
Kočka, J., see Černý, R. 86 (1995) 359
Koenig, E.W., see Wijekoon, W.M.K.P. 81 (1994) 347
Kögel, G., see Britton, D.T. 85 (1995) 158
Kogelschatz, U., see Esrom, H. 86 (1995) 202
Kolbasov, G.Ya., see Dmitruk, N.L. 90 (1995) 489
Koleske, D.D. and S.M. Gates, Si ALE using chlorine/hydrogen exchange. Fundamentals and films 82/83 (1994) 344
Kolev, K., see Laude, L.D. 86 (1995) 368
Kolev, K., see Viville, P. 86 (1995) 411
Kolomenskii, A.A., M. Szabadi and P. Hess, Laser diagnostics of C_{60} and C_{70} films by broadband surface acoustic wave spectroscopy 86 (1995) 591
Koltay, E., see Sundararajan, R. 90 (1995) 165
Komatsu, A., see Hanabusa, M. 86 (1995) 428
Komolov, S.A., see Møller, P.J. 82/83 (1994) 569
Komori, F., see Kanazawa, I. 85 (1995) 124
Komura, T., see Uesugi, K. 82/83 (1994) 367
König, U., see Blum, O. 86 (1995) 417
Kono, S., see Sasaki, M. 82/83 (1994) 387
Kononenko, T.V., V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin, Excimer laser etching of diamond-like carbon films: spalling effect 86 (1995) 234
Konotop, V.V., see Skatkov, L.I. 81 (1994) 427
Konov, V.I., see Pimenov, S.M. 86 (1995) 208
Konov, V.I., see Kononenko, T.V. 86 (1995) 234
Koprinarova, J., see Atanassova, E. 84 (1995) 193
Korol'kov, D.V., see Drozd, V.E. 82/83 (1994) 587
Kosowsky, S.D., C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer, An X-ray scattering study of SiO_x/Si/Ge(001) 84 (1995) 179
Kotru, P.N., see Sharma, K.K. 81 (1994) 251
Kotru, P.N., see Jain, A. 84 (1995) 65
Koukitu, A., see Ikeda, H. 82/83 (1994) 257
Koutti, L., see Deiss, J.L. 86 (1995) 149
Kovrikov, A.B., see Gurin, V.S. 81 (1994) 43
Koymen, A.R., see Fazleev, N.G. 85 (1995) 26
Koymen, A.R., see Weiss, A.H. 85 (1995) 82
Koymen, A.R., see Hozhabri, N. 85 (1995) 311
Kramer, K.J., see Slaoui, A. 86 (1995) 346
Krause, H.-P., see Li, B. 86 (1995) 577

Krebs, H.-U., S. Fähler and O. Bremert, Laser deposition of metallic alloys and multilayers 86 (1995) 86
Krebs, H.-U., O. Bremert, M. Störmer and Y. Luo, Comparison of the structure of laser deposited and sputtered metallic alloys 86 (1995) 90
Kreuss, M., see Wesemann, J. 87/88 (1995) 179
Kreutz, E.W., see Klotzbücher, T. 86 (1995) 165
Kreutz, E.W., H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging, Tailoring of surface properties by removal and deposition with laser radiation 86 (1995) 266
Kreutz, E.W., G. Backes, A. Gasser and K. Wissenbach, Rapid prototyping with CO_2 laser radiation 86 (1995) 310
Kreutz, E.W., see Frerichs, H. 86 (1995) 405
Kruck, Th., see Pflüger, S. 86 (1995) 504
Kruit, P., see Seijbel, L.J. 85 (1995) 92
Kruse, N., see Cocke, D.L. 84 (1995) 153
Kruse, N., see Voss, C. 87/88 (1995) 127
Kruse, N., see Voss, C. 87/88 (1995) 134
Kruseman, A., see Van Veen, A. 85 (1995) 216
Kryuchenko, Yu.V., see Il'chenko, L.G. 87/88 (1995) 53
Kubo, M., see Vetrivel, R. 82/83 (1994) 516
Kubo, M., see Himei, H. 82/83 (1994) 543
Kubo, M., R. Yamauchi, R. Vetrivel and A. Miyamoto, Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics 82/83 (1994) 559
Kubo, M., R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto, Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics 89 (1995) 131
Kubota, H., M. Nagata, R. Miyagawa and M.A. Nicolet, Oxidation of TiN thin films in an ion-beam-assisted deposition process 82/83 (1994) 565
Kuhn, W., see Bourée, J.E. 86 (1995) 437
Kuipers, E.W., see Van Hardeveld, R.M. 84 (1995) 339
Kujirai, H., see Murakami, E. 82/83 (1994) 338
Kuk, Y., see Jeon, D. 87/88 (1995) 386
Kukimoto, H., see Kano, N. 82/83 (1994) 132
Kulkarni, G.U., see Rao, C.N.R. 84 (1995) 285
Kumagai, H. and K. Toyoda, In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions 82/83 (1994) 481
Kumamura, M., see Hata, K. 87/88 (1995) 117
Kumeda, M., see Masuda, A. 81 (1994) 277
Kunimori, K., see Kameoka, S. 89 (1995) 411
Kurabayashi, T., see Płotka, P. 82/83 (1994) 91
Kurabayashi, T. and J. Nishizawa, Temperature synchronized molecular layer epitaxy 82/83 (1994) 97
Kurihara, T., A. Shirakawa, A. Enomoto, T. Shidara, H. Kobayashi and K. Nakahara, An overview of the slow-positron beam facility at the photon factory, KEK 85 (1995) 178
Kuriyama, T., see Kameoka, S. 89 (1995) 411
Kuroda, M., see Kameoka, S. 89 (1995) 411
Kürpick, U., G. Meister and A. Goldmann, Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission 89 (1995) 383
Kusiński, J., Microstructure, chemical composition and properties of the surface layer of M2 steel after laser melting under different conditions 86 (1995) 317
Küttel, O.M., see Gröning, P. 89 (1995) 83
Kuttler, K., see Fazleev, N.G. 85 (1995) 22
Kuttler, K., see Fazleev, N.G. 85 (1995) 26
Kuzmichov, A.V., Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption 86 (1995) 559

Laajalehto, K., I. Kartio and P. Nowak, XPS study of clean metal sulfide surfaces 81 (1994) 11
La Bruna, G., see Cerofolini, G.F. 89 (1995) 361
Labatut, C., see Aspar, B. 81 (1994) 55
Labunov, V.A., see Demchuk, A.V. 86 (1995) 353
Ladas, S., see Kennou, S. 90 (1995) 283
Lahtinen, J., see Vaari, J. 81 (1994) 289
Lahtinen, J., see Vaara, T. 89 (1995) 103
Lakomaa, E.-L., see Haukka, S. 82/83 (1994) 548
Lalande, G., see Weng, L.T. 84 (1995) 9
Lambin, G., see Viville, P. 86 (1995) 411
Lamontagne, B., F. Semond, A. Adnot and D. Roy, SIMS investigation of the Si(111) oxidation promoted by potassium overlayers 90 (1995) 447
Lamontagne, B., D. Guay, D. Roy, R. Sporken and R. Caudano, AFM and XPS characterization of the Si(111) surface after thermal treatment 90 (1995) 481
Lang, B., B. Sefsaf and G. Allan, An AES study of intrinsic and ion-induced structure in the SiO_2–Si system 81 (1994) 17
Lang, H.P., see Sum, R. 86 (1995) 140
LaPierre, R.R., B.J. Robinson and D.A. Thompson, Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (*h*11)-oriented InP substrates 90 (1995) 437
Larena, A., G. Pinto and F. Millán, Using the Lambert–Beer law for thickness evaluation of photoconductor coatings for recording holograms 84 (1995) 407
L'Argentière, P.C., M.G. Cañón and N.S. Fígoli, XPS studies of the effect of Mn on Pd/Al_2O_3 89 (1995) 63
Laricchia, G., see Moxom, J. 85 (1995) 118

Larson, D.J., see Camus, P.P. 87/88 (1995) 305
Larson, D.J., C.-M. Teng, P.P. Camus and T.F. Kelly, Fabrication of microtips on planar specimens 87/88 (1995) 446
LaShell, S., see Coleman, P.G. 85 (1995) 276
Lätsch, S., H. Hiraoka, W. Nieveen and J. Bargon, Interface study on laser-induced material transfer from polymer and quartz surfaces 81 (1994) 183
Laude, L., see Viville, P. 86 (1995) 411
Laude, L.D., see Szörényi, T. 86 (1995) 219
Laude, L.D., K. Kolev, M. Brunel and P. Deleter, Surface properties of excimer-laser-irradiated sintered alumina 86 (1995) 368
Lauff, U., see Stoll, H. 85 (1995) 17
Lawall, R., see Piscevic, D. 90 (1995) 425
Lawther, D.W., R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver, Variable-energy positron beam study of arsenic diffusion in poly-silicon 85 (1995) 265
Laz, M.M., see Hernández Creus, A. 81 (1994) 387
Lazneva, E.F., see Møller, P.J. 82/83 (1994) 569
Lazzaroni, R., see Viville, P. 86 (1995) 411
Lazzaroni, R., see Brocherieux, A. 90 (1995) 47
Le Bras, M., see Bourbigot, S. 81 (1994) 299
Le Mercier, T., J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton, Formation of Ti^{3+} ions at the surface of laser-irradiated rutile 86 (1995) 382
Le Normand, F., A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser, Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies 81 (1994) 309
Leclerc, G., see Piyakis, K. 84 (1995) 227
Lee, H.J., J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson, Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films 89 (1995) 121
Lee, K.H., see Itoh, Y. 85 (1995) 165
Lee, S.-P. and M.C. Lin, Laser-induced decomposition of dimethyl cadmium on a quartz substrate 84 (1995) 31
Lee, T.C., see Ling, C.C. 85 (1995) 305
Lee, W.-I., see Chan, S.-H. 82/83 (1994) 85
Lee, W.S., see Outlaw, R.A. 81 (1994) 143
Lee, W.Y., see Hong, J.K. 89 (1995) 229
Leggett, G.J. and J.C. Vickerman, Sample charging during static SIMS studies of polymers 84 (1995) 253
Leggieri, G., see D'Anna, E. 86 (1995) 170
Leiro, J.A., M.H. Heinonen and I.G. Batirev, Surface segregation and core-level shift of a Pd–Rh alloy studied by XPS 90 (1995) 515
Leisch, M., see Athenstaedt, W. 87/88 (1995) 318
LeMone, D.V., see Wang, P.W. 84 (1995) 75
Lenglet, M., see Souchet, R. 87/88 (1995) 271
Lennard, W.N., see Massoumi, G.R. 85 (1995) 39
León, B., see Parada, E.G. 86 (1995) 294
Leppävuori, S., see Levoska, J. 86 (1995) 180
Leskelä, M., see Asikainen, T. 82/83 (1994) 122
Leskelä, M., see Niinistö, L. 82/83 (1994) 454
Leskelä, M., see Elers, K.-E. 82/83 (1994) 468
Leskelä, M., see Rautanen, J. 82/83 (1994) 553
Leung, T.C., see Aers, G.C. 85 (1995) 196
Leung, T.C., P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz, Measurement of oxide thickness using a variable-energy positron beam 85 (1995) 292
Lévêque, G. and J. Bonnet, Quantitative correction of backscattering in Auger electron spectroscopy of thin films 89 (1995) 211
Levoska, J. and S. Leppävuori, Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films 86 (1995) 180
Lewis, T.A., see Xu, J. 85 (1995) 49
Leys, M.R., see Hopkins, J. 84 (1995) 299
Lhoest, J.B., see Piyakis, K. 84 (1995) 227
Li, B., U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii, Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm 86 (1995) 577
Li, C., see Wu, J. 81 (1994) 37
Li, C., Y.-W. Chen, S.-J. Yang and R.-B. Yen, In-situ FTIR investigation of coke formation on USY zeolite 81 (1994) 465
Li, F.M., see Wu, J.D. 90 (1995) 81
Li, G., see Wu, J. 81 (1994) 37
Li, J., see Russell, S.W. 90 (1995) 455
Li, J.-X., J.A. Gardella, Jr. and P.J. McKeown, A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid–base alternating Langmuir–Blodgett films 90 (1995) 205
Li, Q., see Jiang, S. 84 (1995) 373
Li, S., see Wu, J. 81 (1994) 37
Li, Y.S., see Wong, P.C. 84 (1995) 245
Li, Y.S., see Wong, P.C. 89 (1995) 255
Li, Y.S., P.C. Wong and K.A.R. Mitchell, XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma 89 (1995) 263
Licciardello, A., see Torrisi, A. 81 (1994) 259
Licoppe, C., see Flicstein, J. 86 (1995) 286
Liesegang, J., see De Marco, R. 84 (1995) 237
Lifshits, V.G., see Khramtsova, E.A. 82/83 (1994) 576
Liley, M., see Piscevic, D. 90 (1995) 425
Lin, M.C., see Lee, S.-P. 84 (1995) 31

Lin, Y., see Xiao, X.R. 90 (1995) 321
Lin, Z., see Hu, X. 90 (1995) 111
Linares-Solano, A., see Muñoz-Guillena, M.J. 81 (1994) 409
Linares-Solano, A., see Muñoz-Guillena, M.J. 81 (1994) 417
Linares-Solano, A., see Muñoz-Guillena, M.J. 89 (1995) 197
Ling, C.C., see Panda, B.K. 85 (1995) 182
Ling, C.C., T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han, Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam 85 (1995) 305
Lins, C.W., see Hansen, D.C. 84 (1995) 85
Lisovskii, I.P., V.G. Litovchenko and V.B. Lozinskii, Effect of UV annealing of radiation damage in SiO_2 films 86 (1995) 299
Lisowski, W., see Duś, R. 90 (1995) 277
Litovchenko, V.G., see Lisovskii, I.P. 86 (1995) 299
Litovchenko, V.G., see Il'chenko, L.G. 87/88 (1995) 53
Liu, W., see Forbes, R.G. 87/88 (1995) 99
Liu, W. and R.G. Forbes, Modelling the link between emission current and LMIS cusp length 87/88 (1995) 122
Liu, Z.-H., see Brown, N.M.D. 90 (1995) 155
Liu, Z.-Y., see Kawai, M. 82/83 (1994) 487
Liu Yunpeng and Luo Enze, Electron tunneling in double-barrier diode 87/88 (1995) 75
Ljepojevic, N.N., see Forbes, R.G. 87/88 (1995) 99
Lloret, A., see Puigdollers, J. 86 (1995) 600
Lobner, S.F., see Bolt, P.H. 89 (1995) 339
Lobstein, N., E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt, Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate 89 (1995) 307
Logothetidis, S., I. Alexandrou and J. Stoemenos, In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films 86 (1995) 185
Loh, T.E., see Lu, Y.F. 90 (1995) 217
Loiseau, A., see Duval, S. 87/88 (1995) 284
Loison, J.L., see Deiss, J.L. 86 (1995) 149
Lokere, K., see Donaton, R.A. 89 (1995) 221
Loo, B.H., J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima, A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide 81 (1994) 175
Loubnin, E.N., see Kononenko, T.V. 86 (1995) 234
Loubnin, E.N., see Shafeev, G.A. 86 (1995) 392
Low, T.S., see Lu, Y.F. 90 (1995) 217
Löwe, H., see Arnold, J. 86 (1995) 251
Lozinskii, V.B., see Lisovskii, I.P. 86 (1995) 299
Lu, L., see Wang, P.W. 84 (1995) 75
Lu, Y.-F., Square-shaped temperature distribution induced by a Gaussian-shaped laser beam 81 (1994) 357
Lu, Y.F., T.E. Loh, H.G. Soh and T.S. Low, Laser-induced temperature rise in Gaussian-shaped holes 90 (1995) 217
Lu, Z., see Kelliher, J.T. 86 (1995) 453
Lu, Z.-H., see Yang, X.-M. 90 (1995) 175
Lucas, S.R., see Yates, Jr., J.T. 82/83 (1994) 180
Luches, A., see D'Anna, E. 86 (1995) 170
Lucovsky, G., see Kelliher, J.T. 86 (1995) 453
Luftman, H.S., see Weir, B.E. 84 (1995) 413
Lujala, V., J. Skarp, M. Tammenmaa and T. Suntola, Atomic layer epitaxy growth of doped zinc oxide thin films from organometals 82/83 (1994) 34
Lundin, L. and B. Richarz, Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel 87/88 (1995) 194
Lunney, J.G., see Jordan, R. 86 (1995) 24
Lunney, J.G., Pulsed laser deposition of metal and metal multilayer films 86 (1995) 79
Lunney, J.G., see Masterson, H.J. 86 (1995) 154
Luo, Y., see Krebs, H.-U. 86 (1995) 90
Luo Enze, see Liu Yunpeng, 87/88 (1995) 75
Lupp, F., see Pflüger, S. 86 (1995) 504
Lux, B., see Friedbacher, G. 84 (1995) 133
Lynn, K.G., see Ghosh, V.J. 85 (1995) 210
Lynn, K.G., see Umlor, M.T. 85 (1995) 295
Lynn, K.G., see Hulett, Jr., L.D. 85 (1995) 334

Macht, M.-P., see Al-Kassab, T. 87/88 (1995) 329
Macías, M., see Navío, J.A. 81 (1994) 325
Mackay, K., see Jordan, R. 86 (1995) 24
Mackenzie, R.A.D., see King, R.A. 87/88 (1995) 279
Mackenzie, R.A.D., see Huang, M. 87/88 (1995) 421
Maeda, F., see Watanabe, Y. 82/83 (1994) 136
Maeda, F., Y. Watanabe and M. Oshima, Surface reactions of Ga and As on Sb-terminated GaAs(001) 82/83 (1994) 276
Maeda, H., see Nakayama, H. 82/83 (1994) 214
Maeda, Y., see Watamori, M. 82/83 (1994) 417
Maex, K., see Donaton, R.A. 89 (1995) 221
Maeyama, S., see Heun, S. 82/83 (1994) 507
Magni, E. and G.A. Somorjai, Preparation of a model Ziegler–Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride 89 (1995) 187
Mahajan, A., see Asami, S. 82/83 (1994) 359
Maier, K., see Stoll, H. 85 (1995) 17
Mair, G.L.R., see Forbes, R.G. 87/88 (1995) 99
Majni, G., see D'Anna, E. 86 (1995) 170
Major, J., see Stoll, H. 85 (1995) 17
Makimoto, T., see Kobayashi, N. 82/83 (1994) 284
Makita, Y., see Durand, H.-A. 86 (1995) 122
Makropoulou, M., see Skordoulis, C.D. 86 (1995) 239
Manuel, A.A., R. Ambigapathy, K. Saarinen, P. Hautojärvi and C. Corbel, Defect analysis using 2D-ACAR: GaAs as a test case 85 (1995) 301

Mar, S.Y., C.S. Chen, Y.S. Huang and K.K. Tiong, Characterization of RuO_2 thin films by Raman spectroscopy 90 (1995) 497
Marchand-Brynaert, J., see Deldime, M. 90 (1995) 1
Marcus, B., see Le Normand, F. 81 (1994) 309
Marine, W., see Grangeon, F. 86 (1995) 160
Marine, W., see Shafeev, G.A. 86 (1995) 387
Marino, N., see Baeri, P. 86 (1995) 128
Mariot, J.-M., see Le Mercier, T. 86 (1995) 382
Marotta, V., see Gambardella, U. 86 (1995) 45
Marotta, V., see Teghil, R. 90 (1995) 505
Marshall, P.A., see Aers, G.C. 85 (1995) 196
Martin, O.J.F., see Devel, M. 87/88 (1995) 390
Martínez García, D., see Gonzalo, J. 86 (1995) 40
Martini, T., see Reisse, G. 86 (1995) 107
Martini, T., see Reisse, G. 86 (1995) 114
Martino, M., see D'Anna, E. 86 (1995) 170
Maruno, S., see Gotoda, M. 82/83 (1994) 80
Maruya, E., see Himei, H. 82/83 (1994) 543
Marx, G., see Schlottig, F. 90 (1995) 129
Massardier, J., see Debauge, Y. 90 (1995) 15
Massoumi, G.R., W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson, Energy loss measurements for 20 keV positrons in Al thin films 85 (1995) 39
Masterson, H.J. and J.G. Lunney, Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition 86 (1995) 154
Masuda, A., Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu, Ultrathin SiO_2 films on Si formed by N_2O-plasma oxidation technique 81 (1994) 277
Masuda, T., see Arai, M. 89 (1995) 11
Mathé, E.L., A. Naudon, F. Repplinger and E. Fogarassy, Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si 86 (1995) 338
Mathey, Y., see Grangeon, F. 86 (1995) 160
Mathur, B.K., see Rao, M.V.H. 89 (1995) 417
Matsubara, M. and I. Hirabayashi, Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition 82/83 (1994) 494
Matsumiya, Y., see Sakuma, Y. 82/83 (1994) 46
Matsumura, M., see Imai, S. 82/83 (1994) 322
Matsumura, M., see Sugahara, S. 82/83 (1994) 380
Matsumura, M., see Sugahara, S. 90 (1995) 349
Matsuura, T., see Suzue, K. 82/83 (1994) 422
Maury, F., K. Bouabid, N. Fazouan, A.M. Gué and D. Estève, GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic 86 (1995) 447
Mazhukin, V.I., I. Smurov, C. Surry and G. Flamant, Overheated metastable states in polymer sublimation by laser radiation 86 (1995) 7
Mazhukin, V.I., see Berjeza, N.A. 86 (1995) 303
McCafferty, E., see Hansen, D.C. 84 (1995) 85
McConville, C.F., see Kawai, M. 82/83 (1994) 487
McKeown, P.J., see Li, J.-X. 90 (1995) 205
McNeil, J.R., see Hatab, Z.R. 86 (1995) 597
Meda, L., see Cerofolini, G.F. 89 (1995) 351
Meda, L., see Cerofolini, G.F. 89 (1995) 361
Medvedev, A.S., see Shklyaev, A.A. 89 (1995) 49
Medvedev, V.K., Yu. Suchorski and J.H. Block, Investigation of adsorption and coadsorption of O_2 and CO on Rh by O_2^+ field ion and Li^+ field desorption microscopies 87/88 (1995) 159
Meguro, T., see Isshiki, H. 82/83 (1994) 57
Meguro, T., M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi, Control of the etching reaction of digital etching using tunable UV laser irradiation 82/83 (1994) 193
Meguro, T., see Ishii, M. 86 (1995) 554
Meister, G., see Kürpick, U. 89 (1995) 383
Mele, A., see Di Palma, T.M. 86 (1995) 68
Mele, A., see Teghil, R. 90 (1995) 505
Mengucci, P., see D'Anna, E. 86 (1995) 170
Mens, A.J.M., see Van Wijk, R. 90 (1995) 261
Mermoux, M., see Le Normand, F. 81 (1994) 309
Mertin, M., see Klotzbücher, T. 86 (1995) 165
Mertin, M., see Kreutz, E.W. 86 (1995) 266
Mesarwi, A., see Zomorrodian, A. 90 (1995) 343
Metheringham, W.J., see Jackson, S.R. 86 (1995) 223
Meunier, M., P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon, Laser processing of tungsten from WF_6 and SiH_4 86 (1995) 475
Meunier, M., see Izquierdo, R. 86 (1995) 509
Meyrueis, P., see Durand, H.-A. 86 (1995) 122
Michaelsen, C., see Pundt, A. 87/88 (1995) 264
Miehé, J.A., see Palau, J. 86 (1995) 59
Mihailescu, I.N., see D'Anna, E. 86 (1995) 170
Mihashi, Y., see Takemi, M. 82/83 (1994) 115
Mijnarends, P.E., see Hakvoort, R.A. 85 (1995) 271
Mikado, T., see Suzuki, R. 85 (1995) 87
Mikhailov, V.A., F.N. Putilin and D.N. Trubnikov, Study of PbTe(Ga) evaporation using a nanosecond pulsed laser 86 (1995) 64
Millán, F., see Larena, A. 84 (1995) 407
Miller, A.E., see Kelliher, J.T. 86 (1995) 453
Miller, M.K., see Thomson, R.C. 87/88 (1995) 185
Miller, M.K., see Babu, S.S. 87/88 (1995) 207
Miller, M.K., K.F. Russell, A. Jostsons and R.G. Blake, Characterization of neutron-irradiated Fe–Au alloys 87/88 (1995) 216
Miller, M.K. and G.D.W. Smith, Atom probe analysis of interfacial segregation 87/88 (1995) 243
Miller, M.K., see Hyde, J.M. 87/88 (1995) 311
Miller, M.K., J.M. Hyde, A. Cerezo and G.D.W. Smith, Comparison of low temperature decomposition in Fe–Cr and duplex stainless steels

87/88 (1995) 323
Millon, E., see Lobstein, N. 89 (1995) 307
Mills, Jr., A.P., see Vasumathi, D. 85 (1995) 154
Mills, Jr., A.P., see Canter, K.F. 85 (1995) 339
Milun, M., see Valla, T. 89 (1995) 375
Minel, L., see Fauquet, C. 81 (1994) 435
Minoura, S., see Sato, S. 90 (1995) 29
Mishra, U.K., see Keller, B.P. 82/83 (1994) 126
Mitchell, I.V., see Leung, T.C. 85 (1995) 292
Mitchell, K.A.R., see Wong, P.C. 84 (1995) 245
Mitchell, K.A.R., see Wong, P.C. 89 (1995) 255
Mitchell, K.A.R., see Li, Y.S. 89 (1995) 263
Mitteraner, J., Microstructured liquid metal ion and electron sources (MILMIS/MILMES) 87/88 (1995) 79
Mityukhlyaev, V.B., Electron-beam-induced oxidation of CdS 81 (1994) 137
Miura, H., see Shirai, Y. 85 (1995) 138
Miura, R., see Kubo, M. 89 (1995) 131
Miura, Y., see Ikeda, H. 82/83 (1994) 257
Miyagawa, R., see Kubota, H. 82/83 (1994) 565
Miyamoto, A., see Vetrivel, R. 82/83 (1994) 516
Miyamoto, A., see Himei, H. 82/83 (1994) 543
Miyamoto, A., see Kubo, M. 82/83 (1994) 559
Miyamoto, A., see Kubo, M. 89 (1995) 131
Miyamoto, N., see Enta, Y. 82/83 (1994) 327
Miyamoto, N., see Suemitsu, M. 82/83 (1994) 449
Mizuno, F., see Kobayashi, H. 81 (1994) 399
Mizutani, W., A. Ohi, M. Motomatsu and H. Tokumoto, Field evaporation of gold by scanning tunneling microscopy 87/88 (1995) 398
Mochizuki, Y., T. Takada and A. Usui, Theoretical studies on the chloride ALE process 82/83 (1994) 200
Mohai, M., see Bertóti, I. 84 (1995) 357
Mohamed, M.H., M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui, An XPS study of the optimum loading of barium on high-silica MFI zeolite 90 (1995) 409
Moise, C., see Ionescu, R. 84 (1995) 291
Molchanovskii, I.A., see Dmitruk, N.L. 90 (1995) 489
Møller, P.J., see Ge, Q. 82/83 (1994) 305
Møller, P.J., S.A. Komolov and E.F. Lazneva, Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001) 82/83 (1994) 569
More, M.A., see Adsool, A.D. 87/88 (1995) 37
Morenza, J.L., see Palau, J. 86 (1995) 59
Mori, K., see Takemi, M. 82/83 (1994) 115
Morimoto, A., see Masuda, A. 81 (1994) 277
Morioka, H., see Watamori, M. 82/83 (1994) 417
Morishita, H., see Tanaka, Y. 82/83 (1994) 528
Morishita, T., see Wang, F. 90 (1995) 123
Morishita, Y., see Ohno, H. 82/83 (1994) 164
Morita, K., see Hanebuchi, M. 89 (1995) 113
Morone, A., see Gambardella, U. 86 (1995) 45
Morris, R.E., see Schreifels, J.A. 84 (1995) 23
Motomatsu, M., see Mizutani, W. 87/88 (1995) 398
Moxom, J., G. Laricchia and M. Charlton, A gated positron beam incorporating a scattering cell and novel ion extractor 85 (1995) 118
Možina, J., see Hrovatin, R. 86 (1995) 213
Mozyrsky, D.V., see Vladimirov, V.V. 87/88 (1995) 112
Mudholkar, M.S., see Lee, H.J. 89 (1995) 121
Muhler, M., see Deng, J. 81 (1994) 341
Müllenborn, M., H. Dirac and J.W. Petersen, Three-dimensional nanostructures by direct laser etching of Si 86 (1995) 568
Muller, J.F., see Lobstein, N. 89 (1995) 307
Müller, K., see Starke, U. 89 (1995) 175
Munekata, H., see Kano, N. 82/83 (1994) 132
Muñoz-Guillena, M.J., A. Linares-Solano and C. Salinas-Martínez de Lecea, A study of $CaO–SO_2$ interaction 81 (1994) 409
Muñoz-Guillena, M.J., A. Linares-Solano and C. Salinas-Martínez de Lecea, A study of $CaO–SO_2$ interaction in the presence of O_2 81 (1994) 417
Muñoz-Guillena, M.J., A. Linares-Solano and C. Salinas-Martínez de Lecea, A new parameter to characterize limestones as SO_2 sorbents 89 (1995) 197
Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces 82/83 (1994) 338
Murata, Y., see Kanazawa, I. 85 (1995) 124
Murota, J., see Sakuraba, M. 82/83 (1994) 354
Murota, J., see Suzue, K. 82/83 (1994) 422
Muto, S., see Sakuma, Y. 82/83 (1994) 46
Muto, S., see Sakuma, Y. 82/83 (1994) 239
Myhra, S., see Holt, S.A. 84 (1995) 125

Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2 82/83 (1994) 405
Nagata, M., see Kubota, H. 82/83 (1994) 565
Naidu, S., see Weiss, A.H. 85 (1995) 82
Nail, J.W., see Jackson, M.S. 81 (1994) 195
Naitoh, M., see Watamori, M. 82/83 (1994) 417
Nakahara, K., see Kurihara, T. 85 (1995) 178
Nakaji, M., see Takahashi, I. 82/83 (1994) 70
Nakajima, K., see Sakuma, Y. 82/83 (1994) 46
Nakajima, K., see Sakuma, Y. 82/83 (1994) 239
Nakajyo, T., see Itoh, Y. 85 (1995) 165
Nakajyo, T., see Oshima, N. 85 (1995) 329
Nakamura, J., see Butman, M.F. 89 (1995) 323
Nakamura, T., see Kiyota, Y. 82/83 (1994) 400
Nakanishi, N., see Itoh, Y. 85 (1995) 165
Nakao, M., see Yoshida, I. 82/83 (1994) 501
Nakata, K., see Aruga, T. 85 (1995) 229
Nakato, Y., see Kobayashi, H. 81 (1994) 399
Nakayama, H., M. Tochigi, H. Maeda and T. Nishino, Configurational atomic ordering caused by stochastic adsorption

processes in MBE-grown alloy semiconductors 82/83 (1994) 214
Nakazawa, H., see Suemitsu, M. 82/83 (1994) 449
Nakazawa, M. and G.A. Somorjai, Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide 84 (1995) 309
Naqvi, S.S.H., see Hatab, Z.R. 86 (1995) 597
Narahara, S., see Akamatsu, M. 82/83 (1994) 228
Naudon, A., see Mathé, E.L. 86 (1995) 338
Navío, J.A., M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano, Combined use of XPS, IR and EDAX techniques for the characterization of ZrO_2–SiO_2 powders prepared by a sol–gel process 81 (1994) 325
Neelissen, R.F.J., see Seijbel, L.J. 85 (1995) 92
Néron de Surgy, G., H. González and J.-P. Chabrerie, Influence of bounded geometry on the initial growth of electrocapillary instability for a liquid metal under electric field 87/88 (1995) 91
Nicholls, J.E., see Wagner, F.X. 86 (1995) 364
Nicolaescu, D., Modeling of the field emitter triode (FET) as a displacement/pressure sensor 87/88 (1995) 61
Nicolet, M.A., see Kubota, H. 82/83 (1994) 565
Nielsen, B., see Ghosh, V.J. 85 (1995) 210
Nielsen, B., see Hulett, Jr., L.D. 85 (1995) 334
Niemantsverdriet, J.W., see Van Hardeveld, R.M. 84 (1995) 339
Niemantsverdriet, J.W., see Gunter, P.L.J. 89 (1995) 69
Nieveen, W., see Lätsch, S. 81 (1994) 183
Niinistö, L. and M. Leskelä, Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications 82/83 (1994) 454
Niinistö, L., see Rautanen, J. 82/83 (1994) 553
Nikiforova, I.O., see Drozd, V.E. 82/83 (1994) 583
Nishijima, M., see Taguchi, Y. 82/83 (1994) 434
Nishikawa, K., see Yamamoto, M. 87/88 (1995) 291
Nishikawa, O., see Ashino, M. 87/88 (1995) 12
Nishimura, Y., H. Ujita and M. Tsuji, Tantalum oxide film formation by excimer laser ablation 89 (1995) 393
Nishinaga, T. and X.Q. Shen, Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE 82/83 (1994) 141
Nishino, T., see Nakayama, H. 82/83 (1994) 214
Nishiuchi, T., see Yamamoto, M. 87/88 (1995) 291
Nishiyama, Y., see Arai, M. 89 (1995) 11
Nishizawa, J., Molecular layer epitaxy of GaAs 82/83 (1994) 1
Nishizawa, J., see Oyama, Y. 82/83 (1994) 41
Nishizawa, J., see Płotka, P. 82/83 (1994) 91
Nishizawa, J., see Kurabayashi, T. 82/83 (1994) 97
Nissim, Y.I., see Flicstein, J. 86 (1995) 286
Noh, H.P., see Jeon, D. 87/88 (1995) 386
Nomura, T., see Yago, H. 84 (1995) 119
Nomura, Y., see Ohno, H. 82/83 (1994) 164
Norton, P.R., see Zhdanov, V.P. 81 (1994) 109
Norton, P.R., see Kasza, R.V. 84 (1994) 97
Nowak, P., see Laajalehto, K. 81 (1994) 11
Nowicka, E., see Duś, R. 90 (1995) 277
Nuesca, G., J. Prasad and J.A. Kelber, Effects of atomic hydrogen on Cu(II)bishexafluoroacetylacetonate interactions with a TiN surface 81 (1994) 237
Nunogaki, M., T. Yamamoto, Y. Honda and T. Okada, A several tens-keV monoenergetic positron surface analyzer with ^{22}Na and electrostatic fields 85 (1995) 132
Nunoshita, M., see Gotoda, M. 82/83 (1994) 80
Nuzzo, R.G., see Jackson, S.T. 90 (1995) 195
Nykänen, E., see Rautanen, J. 82/83 (1994) 553

Oakey, P.R., see Russell, S.W. 90 (1995) 455
Obraztsova, E.D., see Kononenko, T.V. 86 (1995) 234
Odriozola, J.A., see Benítez, J.J. 84 (1995) 391
Ogawa, K., see Wang, F. 90 (1995) 123
Ogino, T., see Hibino, H. 82/83 (1994) 374
Ogura, T., see Asahi, H. 82/83 (1994) 109
Oh, I.-H., see Hong, J.K. 89 (1995) 229
Ohba, Y., see Ohnishi, H. 82/83 (1994) 444
Ohgaki, H., see Suzuki, R. 85 (1995) 87
Ohi, A., see Mizutani, W. 87/88 (1995) 398
Ohmi, T., see Suzue, K. 82/83 (1994) 422
Ohnishi, H., see Hirai, M. 82/83 (1994) 23
Ohnishi, H., Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura, Scanning tunneling microscope observations of Si(111)3 × 1-Ag and 6 × 1-Ag structures 82/83 (1994) 444
Ohno, H., S. Goto, Y. Nomura, Y. Morishita and Y. Katayama, Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium 82/83 (1994) 164
Ohno, T., see Ito, T. 82/83 (1994) 208
Ohshita, A., see Hata, K. 87/88 (1995) 117
Ohta, T., see Vetrivel, R. 82/83 (1994) 516
Ohtsuka, N., see Sakuma, Y. 82/83 (1994) 46
Ohtsuka, N., see Ozeki, M. 82/83 (1994) 233
Ojima, K., see Hongo, S. 82/83 (1994) 437
Ojima, K., see Hongo, S. 82/83 (1994) 537
Okada, L.A., M.L. Wise and S.M. George, Isothermal H_2 desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors 82/83 (1994) 410
Okada, L.A., see George, S.M. 82/83 (1994) 460
Okada, S., see Kanazawa, I. 85 (1995) 124
Okada, S. and H. Kaneko, Development of a new Monte Carlo simulation system on positron behavior in matter 85 (1995) 149
Okada, T., see Nunogaki, M. 85 (1995) 132
Okahata, Y., see Piscevic, D. 90 (1995) 425

Okano, R., see Hono, K. 87/88 (1995) 453
Okuyama, F., see Theiss, A. 87/88 (1995) 146
Oldershaw, G.A., see Dyer, P.E. 86 (1995) 1
Ono, S., see Sakuraba, M. 82/83 (1994) 354
Orlando, S., see Gambardella, U. 86 (1995) 45
Orlando, S., see Di Palma, T.M. 86 (1995) 68
Orlando, S., see Teghil, R. 90 (1995) 505
Oshima, M., see Watanabe, Y. 82/83 (1994) 136
Oshima, M., see Maeda, F. 82/83 (1994) 276
Oshima, M., see Heun, S. 82/83 (1994) 507
Oshima, N., see Itoh, Y. 85 (1995) 165
Oshima, N., T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto, Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique 85 (1995) 329
Oshiyama, A., M. Saito and O. Sugino, Covalency, elasticity and electron correlation in Si vacancies 85 (1995) 239
Otake, S., A. Sakamoto, M. Yamamoto and I. Iwasa, In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages 82/83 (1994) 263
Ott, A.W., see George, S.M. 82/83 (1994) 460
Ottosson, M., see Stenberg, G. 86 (1995) 543
Oura, K., see Watamori, M. 82/83 (1994) 417
Oura, K., see Ohnishi, H. 82/83 (1994) 444
Oura, K., see Tanaka, Y. 82/83 (1994) 528
Outlaw, R.A., W.S. Lee, S.J. Hoekje and S.N. Sankaran, Sulfur segregation in titanium and selected titanium alloys 81 (1994) 143
Overton, N., A.P. Knights, A. Goodyear and P.G. Coleman, Work function and epithermal positron emission from copper 85 (1995) 54
Oyama, Y., P. Plotka and J. Nishizawa, Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application 82/83 (1994) 41
Oyama, Y., see Płotka, P. 82/83 (1994) 91
Ozeki, M., see Sakuma, Y. 82/83 (1994) 46
Ozeki, M. and N. Ohtsuka, Atomic layer epitaxy of AlAs: growth mechanism 82/83 (1994) 233

Paggel, J.J., see Keil, M. 90 (1995) 377
Pailharey, D., see Grangeon, F. 86 (1995) 160
Palau, J., M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehé, Laser wavelength dependence of $YBa_2Cu_3O_y$ laser ablation plumes 86 (1995) 59
Palau, J., see Queralt, X. 86 (1995) 95
Palmisano, L., see Navío, J.A. 81 (1994) 325
Paloura, E.C., see Kennou, S. 90 (1995) 283
Pancíř, J., see Pingo, M. 90 (1995) 373
Panda, B.K., S. Fleischer, C.C. Ling, C.D. Beling, S. Fung and S. Panda, Deconvolution of Doppler-broadened positron annihilation lineshapes by the generalised least-squares method 85 (1995) 182
Panda, S., see Panda, B.K. 85 (1995) 182
Pande, R., see Adsool, A.D. 87/88 (1995) 37
Pang, X.J., see Dwyer, D.J. 81 (1994) 229
Papadia, S., see Desjonquères, M.C. 87/88 (1995) 337
Papaioannou, G., see Thurzo, I. 90 (1995) 39
Parada, E.G., P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine, Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing 86 (1995) 294
Parent, P., see Le Mercier, T. 86 (1995) 382
Paridaens, J., see Segers, D. 85 (1995) 172
Park, C., see Bakhtizin, R.Z. 87/88 (1995) 347
Park, D., see Smith, G.C. 90 (1995) 357
Partlow, W.D., see Yates, Jr., J.T. 82/83 (1994) 180
Paul, A.J., see Di Palma, T.M. 86 (1995) 68
Pauleau, Y., see Tonneau, D. 86 (1995) 488
Pavlyak, F., Modified relative sensitivity factors for Auger spectra 81 (1994) 351
Pedraza, A.J., see Esrom, H. 86 (1995) 202
Peled, A., see Baranauskas, V. 86 (1995) 398
Peled, A., see Borochov, N. 86 (1995) 533
Peled, A., B. Dragnea, R. Alexandrescu and A. Andrei, Laser-induced photodeposition from ZnS colloid solutions 86 (1995) 538
Peng, D., see Jiang, S. 84 (1995) 373
Pérez-Amor, M., see Parada, E.G. 86 (1995) 294
Perrière, J., see Gonzalo, J. 86 (1995) 40
Perrone, A., see D'Anna, E. 86 (1995) 170
Persch, V., see Engelhard, H. 90 (1995) 89
Pershan, P.S., see Kosowsky, S.D. 84 (1995) 179
Pervan, P., see Valla, T. 89 (1995) 375
Petersen, J.W., see Müllenborn, M. 86 (1995) 568
Petkov, K., see Ihlemann, J. 86 (1995) 245
Pető, G., see Sundararajan, R. 90 (1995) 165
Pfau, J., see Hulett, Jr., L.D. 85 (1995) 334
Pfleging, W., see Klotzbücher, T. 86 (1995) 165
Pfleging, W., see Kreutz, E.W. 86 (1995) 266
Pflüger, S., M. Wehner, F. Jansen, Th. Kruck and F. Lupp, Deposition of gold on polyimide from solutions 86 (1995) 504
Pickering, C., see Carline, R.T. 81 (1994) 475
Pickering, H.W., see Cho, K. 87/88 (1995) 380
Pickering, H.W., see Sakurai, T. 87/88 (1995) 405
Piglmayer, K., Z. Tóth and Z. Kantor, Laser-induced etching and deposition of tungsten in WF_6–H_2 atmosphere 86 (1995) 484
Pimenov, S.M., G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga, Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films 86 (1995) 208
Pimenov, S.M., see Shafeev, G.A. 86 (1995) 392

Pincik, E., see Thurzo, I. 90 (1995) 39
Pingo, M., J. Vošta, J. Pancíř and I. Haslingerová, Topological study of crack growth on iron crystal 90 (1995) 373
Pinto, G., see Larena, A. 84 (1995) 407
Pireaux, J.-J., see Grégoire, Ch. 84 (1995) 163
Pireaux, J.-J., see Piyakis, K. 84 (1995) 227
Pirri, C., see Hong, S. 90 (1995) 65
Piscevic, D., R. Lawall, M. Veith, M. Liley, Y. Okahata and W. Knoll, Oligonucleotide hybridization observed by surface plasmon optical techniques 90 (1995) 425
Piveteau, B., see Desjonquères, M.C. 87/88 (1995) 337
Piyakis, K., E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest, A multitechnique analysis of the outermost layers of the Teflon PFA surface 84 (1995) 227
Pizzella, G., see Teghil, R. 90 (1995) 505
Plekhanov, P.S., see Givargizov, E.I. 87/88 (1995) 24
Plotka, P., see Oyama, Y. 82/83 (1994) 41
Plotka, P., T. Kurabayashi, Y. Oyama and J. Nishizawa, Ideal static induction transistor implemented with molecular layer epitaxy 82/83 (1994) 91
Pola, J., see Fajgar, R. 86 (1995) 530
Polo, M.C., see Puigdollers, J. 86 (1995) 600
Poltoratskii, Yu., see Li, B. 86 (1995) 577
Porcelli, T.A., see Massoumi, G.R. 85 (1995) 39
Poritsky, P.V., see Vladimirov, V.V. 87/88 (1995) 106
Portillo, M., see Durrer, W.G. 81 (1994) 215
Porto, A., see Scandurra, A. 89 (1995) 1
Possart, W., see Gesang, T. 84 (1995) 273
Potez, L., see Duval, S. 87/88 (1995) 284
Powell, C.J., Elemental binding energies for X-ray photoelectron spectroscopy 89 (1995) 141
Prasad, J., see Nuesca, G. 81 (1994) 237
Prasad, M., see Dubowski, J.J. 86 (1995) 548
Prévot, B., see Antoni, F. 86 (1995) 175
Prevot, B., see Slaoui, A. 86 (1995) 346
Přikryl, P., see Černý, R. 86 (1995) 359
Prins, S.L., see Hatab, Z.R. 86 (1995) 597
Prutton, M., see Barkshire, I.R. 84 (1995) 331
Puglisi, O., see Scandurra, A. 89 (1995) 1
Puigdollers, J., J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret, P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition 86 (1995) 600
Pundt, A. and C. Michaelsen, APFIM study of the compositional inhomogeneity of sputtered Co–Cr magnetic thin film 87/88 (1995) 264
Puppin, E., see Vavassori, P. 89 (1995) 93
Pusel, A., see Karstens, H. 86 (1995) 521
Puska, M.J., see Weiss, A.H. 85 (1995) 82
Putilin, F.N., see Mikhailov, V.A. 86 (1995) 64

Qian, Y., see Guo, S. 84 (1995) 351
Qiu, S.-L., see Ruckman, M.W. 89 (1995) 401
Quaeyhaegens, C., see Segers, D. 85 (1995) 172
Quarton, M., see Le Mercier, T. 86 (1995) 382
Queralt, X., C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela, Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation 86 (1995) 95

Räisänen, J., see Ahlgren, T. 90 (1995) 419
Rajasekar, P., see Ray, N. 84 (1995) 203
Rajumon, M.K., see Rao, C.N.R. 84 (1995) 285
Rakova, E.V., see Givargizov, E.I. 87/88 (1995) 24
Ralchenko, V.G., see Kononenko, T.V. 86 (1995) 234
Ralston, J., Reply to the "Comment of A.N. Buckley and R. Woods on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart" 84 (1995) 225
Ramadan, A.A., see Ashour, A. 89 (1995) 159
Rao, C.N.R., V. Vijayakrishnan, G.U. Kulkarni and M.K. Rajumon, A comparative study of the interaction of oxygen with clusters and single-crystal surfaces of nickel 84 (1995) 285
Rao, C.N.R., see Santra, A.K. 84 (1995) 347
Rao, M.V.H., V. Srinivas, V.V. Rao, B.K. Mathur and K.L. Chopra, Observation of field-induced fragmentation of nickel clusters using Scanning Tunneling Microscopy 89 (1995) 417
Rao, V.V., see Rao, M.V.H. 89 (1995) 417
Rauhala, E., see Elers, K.-E. 82/83 (1994) 468
Rauhala, E., see Ahlgren, T. 90 (1995) 419
Rautanen, J., M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen, The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy 82/83 (1994) 553
Ravelet, S., see Easwarakhanthan, T. 90 (1995) 251
Ray, N., P. Rajasekar and S.D. Dey, A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment 84 (1995) 203
Razdan, A.K., see Jain, A. 84 (1995) 65
Rector, J., see Dam, B. 86 (1995) 13
Rei Vilar, M., see Fauquet, C. 81 (1994) 435
Reihs, K., R. Aguiar Colom, S. Gleditzsch, M. Deimel, B. Hagenhoff and A. Benninghoven, Chemisorption of poly (methylhydrogensiloxane) on oxide surfaces: a quantitative investigation using static SIMS 84 (1995) 107
Reisse, G., S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz, Influence of ion bombardment on the refractive index of laser pulse deposited oxide films 86 (1995) 107

Reisse, G., S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz, Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films 86 (1995) 114
Reitano, R., see Baeri, P. 86 (1995) 128
Reitano, R., Thermodynamics and kinetics of solidification of Si–As solutions 86 (1995) 323
Renard, P., see Easwarakhanthan, T. 90 (1995) 251
Reniers, F., M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon, Surface segregation study of Ib–VIII single-crystal alloys 81 (1994) 151
Repplinger, F., see Mathé, E.L. 86 (1995) 338
Rice-Evans, P.C., see Towner, A. 85 (1995) 315
Rice-Evans, P.C., A.S. Saleh and S.J. Bull, Positron beam spectroscopy for the assessment of the structure and defect density of titanium nitride 85 (1995) 320
Rice-Evans, P.C., see Saleh, A.S. 85 (1995) 325
Richarz, B., see Lundin, L. 87/88 (1995) 194
Rigo, S., see Bréelle, E. 81 (1994) 127
Ringer, S.P., K. Hono and T. Sakurai, Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations 87/88 (1995) 223
Ringer, S.P., K. Hono and T. Sakurai, Erratum to "Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223] 90 (1995) 107
Ritala, M., see Asikainen, T. 82/83 (1994) 122
Ritala, M., see Elers, K.-E. 82/83 (1994) 468
Robbins, D.J., see Carline, R.T. 81 (1994) 475
Roberts, M.W., see Carley, A.F. 81 (1994) 265
Robino, M., see Deiss, J.L. 86 (1995) 149
Robinson, B.J., see LaPierre, R.R. 90 (1995) 437
Rochefort, A., see Debauge, Y. 90 (1995) 15
Röllgen, F.W., see Schulze, B. 87/88 (1995) 140
Röllgen, F.W., see Theiss, A. 87/88 (1995) 146
Romeo, M., see Le Normand, F. 81 (1994) 309
Roy, D., see Lamontagne, B. 90 (1995) 447
Roy, D., see Lamontagne, B. 90 (1995) 481
Roy, J.A., see Zou, H. 90 (1995) 59
Ruckman, M.W., S.-L. Qiu and M. Strongin, A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110) 89 (1995) 401
Russell, D.P., see Durrer, W.G. 81 (1994) 215
Russell, K.F., see Miller, M.K. 87/88 (1995) 216
Russell, N.M., see Asami, S. 82/83 (1994) 359
Russell, S.W., J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas, Rapid thermal nitridation of thin chromium films 90 (1995) 455
Ryzhkov, S.V., see Khramtsova, E.A. 82/83 (1994) 576

Saarinen, K., see Manuel, A.A. 85 (1995) 301
Sabatini, R.L., see Canter, K.F. 85 (1995) 339
Sacher, E., see Piyakis, K. 84 (1995) 227
Sacher, E., see Izquierdo, R. 86 (1995) 509
Saeda, T., see Hono, K. 87/88 (1995) 453
Sagisaka, K., see Suzuki, Y. 84 (1995) 1
Saied, S.O., see Bertóti, I. 84 (1995) 357
Saied, S.O., see Sullivan, J.L. 90 (1995) 309
Saito, M., see Oshiyama, A. 85 (1995) 239
Saito, Y., Atomic-hydrogen-induced desorption of fluorine from silicon surfaces 81 (1994) 223
Saito, Y., see Hata, K. 87/88 (1995) 117
Sakamoto, A., see Otake, S. 82/83 (1994) 263
Sakata, T., see Xue, Q. 87/88 (1995) 364
Sakuma, Y., M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama, Pulsed-jet epitaxy: application to device processes 82/83 (1994) 46
Sakuma, Y., S. Muto, K. Nakajima and N. Yokoyama, A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer expitaxy 82/83 (1994) 239
Sakuraba, M., J. Murota, T. Watanabe, Y. Sawada and S. Ono, Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases 82/83 (1994) 354
Sakuragi, S., see Durand, H.-A. 86 (1995) 122
Sakurai, T., see Hono, K. 87/88 (1995) 166
Sakurai, T., see Ringer, S.P. 87/88 (1995) 223
Sakurai, T., see Bakhtizin, R.Z. 87/88 (1995) 347
Sakurai, T., see Xue, Q. 87/88 (1995) 364
Sakurai, T., see Hashizume, T. 87/88 (1995) 373
Sakurai, T., see Cho, K. 87/88 (1995) 380
Sakurai, T., see Jeon, D. 87/88 (1995) 386
Sakurai, T., X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering, Adsorption of fullerenes on Cu(111) and Ag(111) surfaces 87/88 (1995) 405
Sakurai, T., see Hono, K. 87/88 (1995) 453
Sakurai, T., see Ringer, S.P. 90 (1995) 107
Salaita, G.N., Determination of the spatial distribution of trace elements in stainless steel by imaging microprobe secondary ion mass spectrometry 90 (1995) 465
Saleh, A.S., see Rice-Evans, P.C. 85 (1995) 320
Saleh, A.S., P.C. Rice-Evans and S.J. Bull, Aluminium nitride layers investigated by slow positrons 85 (1995) 325
Salinas-Martínez de Lecea, C., see Muñoz-Guillena, M.J. 81 (1994) 409
Salinas-Martínez de Lecea, C., see Muñoz-Guillena, M.J. 81 (1994) 417
Salinas-Martínez de Lecea, C., see Muñoz-Guillena, M.J. 89 (1995) 197
Salvarezza, R.C., see Hernández Creus, A. 81 (1994) 387
Salvi, A.M., J.E. Castle, J.F. Watts and E. Desimoni, Peak fitting of the chromium 2p XPS spectrum 90 (1995) 333
Salzman, W.R., see Wijekoon, W.M.K.P. 81 (1994) 347

Sánchez, F., see Queralt, X. 86 (1995) 95
Sánchez-Soto, P.J., see Navío, J.A. 81 (1994) 325
Sands, D., see Dyer, P.E. 86 (1995) 18
Sands, D., see Wagner, F.X. 86 (1995) 364
Sankaran, S.N., see Outlaw, R.A. 81 (1994) 143
Santagata, A., see Teghil, R. 90 (1995) 505
Santra, A.K. and C.N.R. Rao, Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers 84 (1995) 347
Sanyal, S., see Chattopadhyay, P. 89 (1995) 205
Saranin, A.A., see Khramtsova, E.A. 82/83 (1994) 576
Sarrau, J.M., see Deconihout, B. 87/88 (1995) 428
Sasaki, M., see Yoshida, S. 82/83 (1994) 28
Sasaki, M. and S. Yoshida, Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces 82/83 (1994) 269
Sasaki, M., T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono, Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001) 82/83 (1994) 387
Sasaoka, C. and A. Usui, Self-limiting adsorption of thermally cracked $SiCl_2H_2$ on Si surfaces 82/83 (1994) 348
Sassoli, H., see Grangeon, F. 86 (1995) 160
Sato, K., see Fahy, M.R. 82/83 (1994) 14
Sato, M., Surface structure dependence of O_2–W adsorption system 82/83 (1994) 532
Sato, S., see Sasaki, M. 82/83 (1994) 387
Sato, S., S. Minoura, T. Urisu and Y. Takasu, IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO_2 film with a buried metal layer 90 (1995) 29
Sawada, Y., see Sakuraba, M. 82/83 (1994) 354
Sawada, Y., see Suzue, K. 82/83 (1994) 422
Sawaki, N., see Suzuki, T. 82/83 (1994) 103
Sawyer, W.D., see Coleman, P.G. 85 (1995) 276
Scandurra, A., see Torrisi, A. 81 (1994) 259
Scandurra, A., A. Porto and O. Puglisi, SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests 89 (1995) 1
Schaefer, J., see Yates, Jr., J.T. 82/83 (1994) 180
Schaefer, J.A., see Engelhard, H. 90 (1995) 89
Schaub, A., see Hulett, Jr., L.D. 85 (1995) 334
Schedel-Niedrig, Th., see Keil, M. 90 (1995) 377
Schilcher, K., see Heitz, J. 81 (1994) 103
Schlapbach, L., see Gröning, P. 89 (1995) 83
Schlottig, F., J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx, Conversion film formation on titanium anodes in acetonitrile at high voltages 90 (1995) 129
Schmidt, U., see Schulze, B. 87/88 (1995) 140
Schmuck, C., P. Auger, F. Danoix and D. Blavette, Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy 87/88 (1995) 228
Schneider, H., see Stoll, H. 85 (1995) 17
Schneider, Y.-J., see Deldime, M. 90 (1995) 1
Scholz, R., see Reisse, G. 86 (1995) 107
Scholz, R., see Reisse, G. 86 (1995) 114
Schreckenbach, J., see Schlottig, F. 90 (1995) 129
Schreifels, J.A., N.H. Turner and R.E. Morris, A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants 84 (1995) 23
Schubert, E., see Bergmann, H.W. 86 (1995) 259
Schultz, P.J., see Massoumi, G.R. 85 (1995) 39
Schultz, P.J., see Lawther, D.W. 85 (1995) 265
Schultz, P.J., see Goldberg, R.D. 85 (1995) 287
Schultz, P.J., see Leung, T.C. 85 (1995) 292
Schultz, R.J., see Zou, H. 90 (1995) 59
Schulze, B., A. Theiss, U. Schmidt and F.W. Röllgen, FIM phenomena observed with benzene as image gas 87/88 (1995) 140
Schulze, R.K. and J.F. Evans, Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS 81 (1994) 449
Schut, H., see Seijbel, L.J. 85 (1995) 92
Schut, H., see Van Veen, A. 85 (1995) 216
Schut, H. and A. van Veen, Extension of the PC version of VEPFIT with input and output routines running under Windows 85 (1995) 225
Schut, H., see Hakvoort, R.A. 85 (1995) 271
Schutte, K., see Bergmann, H.W. 86 (1995) 259
Schwarzbach, D., see Friedbacher, G. 84 (1995) 133
Schwentner, N., see Li, B. 86 (1995) 577
Seeger, A., Positron diffusion in solids and in liquid metals 85 (1995) 8
Seeger, A., see Stoll, H. 85 (1995) 17
Sefsaf, B., see Lang, B. 81 (1994) 17
Segers, D., J. Paridaens, T. Van Hoecke, C. Dauwe, L. Dorikens-Vanpraet, C. Quaeyhaegens and L.M. Stals, Positron Doppler broadening measurements with a LINAC-based slow positron beam 85 (1995) 172
Seidman, D.N., see Van Bakel, G.P.E.M. 90 (1995) 95
Seijbel, L.J., R.F.J. Neelissen, P. Kruit, A. van Veen and H. Schut, Coupling optics for a combined electron positron scanning microscope 85 (1995) 92
Seki, H., see Ikeda, H. 82/83 (1994) 257
Sekine, S., H. Shimizu and S. Ichimura, Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures 84 (1995) 401
Semond, F., see Lamontagne, B. 90 (1995) 447
Seo, A. and H. Shindo, Atomic force microscopic study of directional $SrSO_4(001)$ surface and its etching property 82/83 (1994) 475
Seo, M., see Gråsjö, L. 89 (1995) 21
Serafetinides, A.A., see Skordoulis, C.D. 86 (1995) 239

Serra, J., see Parada, E.G. 86 (1995) 294
Serra, P., see Palau, J. 86 (1995) 59
Seta, M., see Asahi, H. 82/83 (1994) 109
Seth, J., see Kononenko, T.V. 86 (1995) 234
Setzler, S., see Coleman, P.G. 85 (1995) 276
Shafeev, G.A., see Pimenov, S.M. 86 (1995) 208
Shafeev, G.A., L. Bellard, J.-M. Themlin, W. Marine and A. Cros, Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer 86 (1995) 387
Shafeev, G.A., S.M. Pimenov and E.N. Loubnin, Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating 86 (1995) 392
Shafeev, G.A., see Simakin, A.V. 86 (1995) 422
Sharma, K.K., P.N. Kotru and B.M. Wanklyn, Microindentation studies of flux-grown $ErFeO_3$ single crystals 81 (1994) 251
Sharma, R.B., see Adsool, A.D. 87/88 (1995) 37
Sharma, S.C., see Hozhabri, N. 85 (1995) 311
Shatas, S.C., see Russell, S.W. 90 (1995) 455
Shaw, N., see Towner, A. 85 (1995) 315
Shen, N.F., see Wang, X.K. 89 (1995) 297
Shen, X.Q., see Nishinaga, T. 82/83 (1994) 141
Shi, M., see Gerola, D. 85 (1995) 106
Shi, M., D. Gerola, W.B. Waeber and U. Zimmermann, Slow positron beam extraction from high magnetic fields 85 (1995) 143
Shibata, H., see Durand, H.-A. 86 (1995) 122
Shidara, T., see Kurihara, T. 85 (1995) 178
Shigematsu, H., see Sakuma, Y. 82/83 (1994) 46
Shimizu, H., see Sekine, S. 84 (1995) 401
Shimizu, T., see Masuda, A. 81 (1994) 277
Shindo, H., see Seo, A. 82/83 (1994) 475
Shinohara, H., see Sakurai, T. 87/88 (1995) 405
Shinohara, M., see Yokoyama, H. 82/83 (1994) 158
Shirai, Y., H. Miura and M. Yamaguchi, Construction and performance of a slow positron beam guided by an increasing magnetic field 85 (1995) 138
Shiraishi, K., see Ito, T. 82/83 (1994) 208
Shirakawa, A., see Kurihara, T. 85 (1995) 178
Shklyaev, A.A. and A.S. Medvedev, Plasma-enhanced reactively evaporated deposition of SiO_2 films 89 (1995) 49
Shogen, S., see Song, Z. 82/83 (1994) 250
Shukla, N., see Carley, A.F. 81 (1994) 265
Siddiqui, A.B., see Mohamed, M.H. 90 (1995) 409
Siegle, A., see Stoll, H. 85 (1995) 17
Sigmon, T.W., see Slaoui, A. 86 (1995) 346
Siimon, H., see Aarik, J. 81 (1994) 281
Siimon, H., see Aarik, J. 90 (1995) 109
Sijbrandij, S.J., A. Cerezo and G.D.W. Smith, Improvements in the transmission of voltage evaporation pulses in the atom probe 87/88 (1995) 414
Sil, A. and D.S. Venkateswarlu, Modelling of barium transport in dispenser cathodes 81 (1994) 469
Simakin, A.V. and G.A. Shafeev, Laser-assisted etching-like damage of Si 86 (1995) 422
Simpson, P.J., see Massoumi, G.R. 85 (1995) 39
Simpson, P.J., see Lawther, D.W. 85 (1995) 265
Simpson, P.J., see Goldberg, R.D. 85 (1995) 287
Simpson, P.J., see Leung, T.C. 85 (1995) 292
Sirringhaus, H., see Kafader, U. 90 (1995) 297
Siuda, R., The smoothing properties of some new shapes for transmission functions in Fourier space. A real case study on exemplary noisy Auger spectra 81 (1994) 27
Skarp, J., see Lujala, V. 82/83 (1994) 34
Skatkov, L.I., V.V. Konotop, P.G. Cheremskoy, V.P. Gomozov and B.I. Bayrachny, Surface fractal dimension of sintered porous solid niobium 81 (1994) 427
Skordoulis, C.D., M. Makropoulou and A.A. Serafetinides, Ablation of nylon-6,6 with UV and IR lasers 86 (1995) 239
Slaoui, A., C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot, Formation of poly-$Si_{1-x}Ge_x$ using excimer-laser processing 86 (1995) 346
Sloboshanin, S., see Engelhard, H. 90 (1995) 89
Smith, G.C., see Barkshire, I.R. 84 (1995) 331
Smith, G.C., D. Park, K.J. Titchener, R.E. Davies and R.H. West, Surface studies of oil-seal degradation 90 (1995) 357
Smith, G.D.W., see Miller, M.K. 87/88 (1995) 243
Smith, G.D.W., see King, R.A. 87/88 (1995) 279
Smith, G.D.W., see Hyde, J.M. 87/88 (1995) 311
Smith, G.D.W., see Miller, M.K. 87/88 (1995) 323
Smith, G.D.W., see Sijbrandij, S.J. 87/88 (1995) 414
Smith, G.D.W., see Huang, M. 87/88 (1995) 421
Smolin, A.A., see Pimenov, S.M. 86 (1995) 208
Smurov, I., see Mazhukin, V.I. 86 (1995) 7
Smurov, I., see Berjeza, N.A. 86 (1995) 303
Sneh, O., see George, S.M. 82/83 (1994) 460
Snelling, H.V., see Dyer, P.E. 86 (1995) 18
Snels, M., see Gambardella, U. 86 (1995) 45
Sobol, E.N., M.S. Kitai, S.M. Gol'berg and A.N. Zherikhin, Macro-particle ejection by laser ablation of high-temperature superconductors 90 (1995) 235
Soe, W.-H., see Oshima, N. 85 (1995) 329
Soga, T., T. Jimbo and M. Umeno, Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition 82/83 (1994) 64
Soh, H.G., see Lu, Y.F. 90 (1995) 217
Soininen, P., see Rautanen, J. 82/83 (1994) 553
Somorjai, G.A., see Nakazawa, M. 84 (1995) 309
Somorjai, G.A., see Magni, E. 89 (1995) 187
Song, Y., see Carley, A.F. 81 (1994) 265

Song, Z., S. Shogen, M. Kawasaki and I. Suemune, X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution 82/83 (1994) 250
Song, Z.M., see Wu, J.D. 90 (1995) 81
Sotobayashi, H., see Keil, M. 90 (1995) 377
Souchet, R., F. Danoix, A. D'Huysser and M. Lenglet, APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys 87/88 (1995) 271
Soumillion, J.P., see Devillers, M. 81 (1994) 83
Souto, R.M., see Hernández Creus, A. 81 (1994) 387
Sowinska, M., see Palau, J. 86 (1995) 59
Spanjaard, D., see Desjonquères, M.C. 87/88 (1995) 337
Spassova, E., see Ihlemann, J. 86 (1995) 245
Speisser, C., see Le Normand, F. 81 (1994) 309
Spinelli, N., see Amoruso, S. 86 (1995) 35
Sporken, R., see Lamontagne, B. 90 (1995) 481
Sreemany, M. and T.B. Ghosh, On the XPS peak shape analysis 81 (1994) 365
Sreemany, M. and T.B. Ghosh, Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers 90 (1995) 241
Srinivas, V., see Rao, M.V.H. 89 (1995) 417
Stals, L.M., see Segers, D. 85 (1995) 172
Starke, U., Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller, The (0001)-surface of 6H-SiC: morphology, composition and structure 89 (1995) 175
Steiger, B., see Reisse, G. 86 (1995) 107
Steiger, B., see Reisse, G. 86 (1995) 114
Steiner, P.-R., see Starke, U. 89 (1995) 175
Steiner IV, P.A., see Asami, S. 82/83 (1994) 359
Stenberg, G., M. Boman, M. Ottosson and J.-O. Carlsson, Laser chemical etching of Cu_2O 86 (1995) 543
Stepanenko, V., see Li, B. 86 (1995) 577
Stepanova, A.N., see Givargizov, E.I. 87/88 (1995) 24
Stepanova, M.G., see Hofmann, S. 90 (1995) 227
Stietz, F., see Engelhard, H. 90 (1995) 89
Stiller, K., see Thuvander, M. 87/88 (1995) 251
Stoemenos, J., see Logothetidis, S. 86 (1995) 185
Stoll, H., M. Koch, U. Lauff, K. Maier, J. Major, H. Schneider, A. Seeger and A. Siegle, Annihilation of incompletely thermalized positronium studied by age–momentum correlation 85 (1995) 17
Stoquert, J.P., see Antoni, F. 86 (1995) 175
Stoquert, J.P., see Slaoui, A. 86 (1995) 346
Störmer, J., see Britton, D.T. 85 (1995) 1
Störmer, M., see Krebs, H.-U. 86 (1995) 90
Streller, U., see Li, B. 86 (1995) 577
Stricker, J., see Frerichs, H. 86 (1995) 405
Strohmeier, B.R., Comment on 'Influence of surface composition on initial hydration of aluminium in boiling water' by A. Strålin and T. Hjertberg 81 (1994) 273
Strongin, M., see Ruckman, M.W. 89 (1995) 401
Suchorski, Yu., see Medvedev, V.K. 87/88 (1995) 159
Suda, Y., M. Ishida, M. Yamashita and H. Ikeda, Sub-atomic-layer epitaxy of Si using Si_2H_6 82/83 (1994) 332
Suemitsu, M., H. Nakazawa and N. Miyamoto, Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1 82/83 (1994) 449
Suemune, I., Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs 82/83 (1994) 149
Suemune, I., see Song, Z. 82/83 (1994) 250
Sueoka, O., B. Jin and A. Hamada, Threshold behavior of ionization and excitation cross sections of He and Ar by positron impact 85 (1995) 59
Sueoka, O., see Hamada, A. 85 (1995) 64
Sueoka, O., see Kanazawa, I. 85 (1995) 124
Suezawa, M., see Kawasuso, A. 85 (1995) 280
Sugahara, S., T. Kitamura, S. Imai and M. Matsumura, Atomic layer epitaxy of germanium 82/83 (1994) 380
Sugahara, S., M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura, Atomic hydrogen-assisted ALE of germanium 90 (1995) 349
Sugano, T., see Isshiki, H. 82/83 (1994) 57
Sugano, T., see Meguro, T. 82/83 (1994) 193
Sugano, T., see Ishii, M. 86 (1995) 554
Sugimoto, H., see Gotoda, M. 82/83 (1994) 80
Sugino, O., see Oshiyama, A. 85 (1995) 239
Sugiyama, M., see Heun, S. 82/83 (1994) 507
Sullivan, J.L., see Bertóti, I. 84 (1995) 357
Sullivan, J.L., W. Yu and S.O. Saied, A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS 90 (1995) 309
Sum, R., H.P. Lang and H.-J. Güntherodt, Pulsed laser deposition and nanometer scale characterization of $YBa_2Cu_3O_{7-\delta}$ thin films by scanning probe methods 86 (1995) 140
Sumino, K., see Kawasuso, A. 85 (1995) 280
Summ, P., see Palau, J. 86 (1995) 59
Sun, S., see Ling, C.C. 85 (1995) 305
Sundararajan, R., G. Pető, E. Koltay and L. Guczi, Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon 90 (1995) 165
Suntola, T., see Lujala, V. 82/83 (1994) 34
Suntola, T., see Haukka, S. 82/83 (1994) 548
Suppiah, S., see Huang, M. 90 (1995) 393
Surry, C., see Mazhukin, V.I. 86 (1995) 7
Susaki, W., see Gotoda, M. 82/83 (1994) 80

Suys, M., see Izquierdo, R. 86 (1995) 509
Suzue, K., T. Matsuura, J. Murota, Y. Sawada and T. Ohmi, Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation 82/83 (1994) 422
Suzuki, R., T. Mikado, M. Chiwaki, H. Ohgaki and T. Yamazaki, Generation of an intense pulsed positron beam for positron lifetime and TOF experiments 85 (1995) 87
Suzuki, S., see Sasaki, M. 82/83 (1994) 387
Suzuki, T., H. Goto, N. Sawaki, H. Ito and K. Hara, Autocompensation in Si planar doped GaAs 82/83 (1994) 103
Suzuki, Y., K. Sagisaka and A. Hatta, Evidence for infrared absorption enhancement of species at the lithium metal/electrolytic solution interface 84 (1995) 1
Svensson, L.-E., see Andrén, H.-O. 87/88 (1995) 200
Svob, L., see Ballutaud, D. 84 (1995) 187
Syutkin, N.N., see Ivchenko, V.A. 87/88 (1995) 257
Szabadi, M., see Kolomenskii, A.A. 86 (1995) 591
Sze, S.M., see Chan, S.-H. 82/83 (1994) 85
Szeles, Cs., see Hulett, Jr., L.D. 85 (1995) 334
Szörényi, T., see Kántor, Z. 86 (1995) 196
Szörényi, T., Z. Kántor and L.D. Laude, Atypical characteristics of KrF excimer laser ablation of indium–tin oxide films 86 (1995) 219
Szörényi, T., see Geretovszky, Zs. 86 (1995) 494
Szörényi, T., see Bali, K. 86 (1995) 500
Szyszko, W., Melting and diffusion under nanosecond laser pulse 90 (1995) 325

Tabbal, M., see Meunier, M. 86 (1995) 475
Taguchi, Y., M. Daté, N. Takagi, T. Aruga and M. Nishijima, Chemical reactivity of the Si(111)$(\sqrt{3} \times \sqrt{3})$R30°-B surface: an electron-energy-loss spectroscopy study 82/83 (1994) 434
Takada, T., see Mochizuki, Y. 82/83 (1994) 200
Takagi, N., see Taguchi, Y. 82/83 (1994) 434
Takahashi, I., M. Nakaji and H. Kawanishi, Migration and related buried epitaxy using digital epitaxial growth conditions 82/83 (1994) 70
Takahashi, K., see Hirose, M. 85 (1995) 111
Takahashi, N., see Ikeda, H. 82/83 (1994) 257
Takakuwa, Y., see Enta, Y. 82/83 (1994) 327
Takamiya, S., see Takemi, M. 82/83 (1994) 115
Takamura, S., see Kanazawa, I. 85 (1995) 124
Takamura, S., see Aruga, T. 85 (1995) 229
Takasu, Y., see Sato, S. 90 (1995) 29
Takemi, M., T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya, Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction 82/83 (1994) 115
Takiguchi, T., K. Uesugi, M. Yoshimura and T. Yao, Atomic-scale modification of the $AlCl_3$-adsorbed Si(111)-7 × 7 surface 82/83 (1994) 428
Talwar, S., see Slaoui, A. 86 (1995) 346
Tamir, S. and S. Berger, Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation 86 (1995) 514
Tammenmaa, M., see Lujala, V. 82/83 (1994) 34
Tan, K.L., see Wee, A.T.S. 81 (1994) 377
Tan, K.L., see Gråsjö, L. 89 (1995) 21
Tanaka, K., see Akinaga, H. 82/83 (1994) 298
Tanaka, Y., H. Morishita, M. Watamori, K. Oura and I. Katayama, Structural study of $SrTiO_3$(100) surfaces by low energy ion scattering 82/83 (1994) 528
Tang, Y.-Q., see Fang, Y. 89 (1995) 331
Taniguchi, S., see Hongo, S. 82/83 (1994) 437
Taniguchi, S., see Hongo, S. 82/83 (1994) 537
Tanimoto, M., see Yokoyama, H. 82/83 (1994) 158
Taranets, T.A., see Dmitruk, N.L. 90 (1995) 489
Tarasik, M.I., see Fedotov, A.K. 84 (1995) 379
Tasch, A., see Asami, S. 82/83 (1994) 359
Tate, T.J., see Taverner, A.E. 90 (1995) 383
Taverner, A.E., A. Gulino, R.G. Egdell and T.J. Tate, A photoemission study of electron states in Sb-ion implanted TiO_2(110) 90 (1995) 383
Teghil, R., L. D'Alessio, G. De Maria and D. Ferro, Pulsed-laser deposition and characterization of TaC films 86 (1995) 190
Teghil, R., A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele, Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe 90 (1995) 505
Tejedor, P. and P.S. Domínguez, Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl_2 environment 89 (1995) 271
Teng, C.-M., see Bajikar, S.S. 87/88 (1995) 438
Teng, C.-M., see Larson, D.J. 87/88 (1995) 446
Theiss, A., see Schulze, B. 87/88 (1995) 140
Theiss, A., F. Okuyama and F.W. Röllgen, Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases 87/88 (1995) 146
Themlin, J.-M., see Shafeev, G.A. 86 (1995) 387
Thim, G.P., see Baranauskas, V. 86 (1995) 398
Thoelen, O., see Viville, P. 86 (1995) 411
Thomas, K.K., see Carley, A.F. 81 (1994) 265
Thompson, D.A., see LaPierre, R.R. 90 (1995) 437
Thompson, L.T., see Lee, H.J. 89 (1995) 121
Thomson, R.C. and M.K. Miller, The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels 87/88 (1995) 185

Thurzo, I., E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis, Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water 90 (1995) 39
Thuvander, M. and K. Stiller, Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials 87/88 (1995) 251
Tin, C.C., see Wee, A.T.S. 81 (1994) 377
Tiong, K.K., see Mar, S.Y. 90 (1995) 497
Titchener, K.J., see Smith, G.C. 90 (1995) 357
Tochigi, M., see Nakayama, H. 82/83 (1994) 214
Tokita, S., see Yoshikawa, A. 82/83 (1994) 316
Tokumoto, H., see Mizutani, W. 87/88 (1995) 398
Tolk, N.H., see Xu, J. 85 (1995) 49
Tomitori, M., see Ashino, M. 87/88 (1995) 12
Tomizuka, H. and A. Ayame, A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}Cs^+$ beam 89 (1995) 281
Tonneau, D., J.E. Bourée and Y. Pauleau, Kinetics of laser thermal decomposition of trimethylamine alane 86 (1995) 488
Tontegode, A.Ya. and F.K. Yusifov, Super-efficient diffusion of cesium atoms into rhenium covered by a 2D graphite film 90 (1995) 185
Torrisi, A., A. Scandurra and A. Licciardello, Evaluation of matrix effects in SIMS quantification of $Al_xGa_{1-x}As$/GaAs heterostructures: a SNMS approach 81 (1994) 259
Tóth, A.L., see Bali, K. 86 (1995) 500
Tóth, Z., see Kántor, Z. 86 (1995) 196
Tóth, Z., see Piglmayer, K. 86 (1995) 484
Towner, A., P.C. Rice-Evans and N. Shaw, A positron annihilation study of the formation of defect layers in cadmium mercury telluride 85 (1995) 315
Toyoda, K., see Kumagai, H. 82/83 (1994) 481
Tran, T.T. and S.A. Chambers, Auger and X-ray photoelectron diffraction in MgO(001) 81 (1994) 161
Trubnikov, D.N., see Mikhailov, V.A. 86 (1995) 64
Tsuji, M., see Nishimura, Y. 89 (1995) 393
Tsutsui, K., see Hwang, S.M. 82/83 (1994) 523
Tulub, A.A., see Drozd, V.E. 82/83 (1994) 587
Tumareva, T.A., V.A. Ivanov and T.S. Kirsanova, The investigation of the electron energy distribution and the structure of the thin films and microcrystals by field emission methods 87/88 (1995) 18
Turner, N.H., see Schreifels, J.A. 84 (1995) 23
Tutov, E.A. and A.A. Baev, Charge transfer processes in a-WO_3/Si heterostructure during electro- and photochromism 90 (1995) 303
Twesten, I., see Li, B. 86 (1995) 577
Tyrrell, G.C., T.H. York and I.W. Boyd, Characterisation of ionic species generated during ablation of $Bi_2Sr_2Ca_2Cu_3O_{10}$ by frequency-doubled Nd:YAG laser irradiation 86 (1995) 50

Ueda, O., see Sakuma, Y. 82/83 (1994) 46
Uesugi, K., T. Komura, M. Yoshimura and T. Yao, Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates 82/83 (1994) 367
Uesugi, K., see Takiguchi, T. 82/83 (1994) 428
Uhlmann, K., see Britton, D.T. 85 (1995) 158
Ujita, H., see Nishimura, Y. 89 (1995) 393
Ulrych, I., see Černý, R. 86 (1995) 359
Umeno, M., see Soga, T. 82/83 (1994) 64
Umlor, M.T., P. Asoka-Kumar, D.J. Keeble, P.W. Cooke and K.G. Lynn, Positron annihilation studies of defects in molecular beam epitaxy grown III–V layers 85 (1995) 295
Unger, J., Yu.A. Vlasov and N. Ernst, Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips 87/88 (1995) 45
Urano, T., see Hongo, S. 82/83 (1994) 437
Urano, T., see Hongo, S. 82/83 (1994) 537
Urisu, T., see Sato, S. 90 (1995) 29
Usui, A., see Mochizuki, Y. 82/83 (1994) 200
Usui, A., see Sasaoka, C. 82/83 (1994) 348
Utriainen, M., see Rautanen, J. 82/83 (1994) 553
Uwai, K. and N. Kobayashi, Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption 82/83 (1994) 290

Vaara, T., see Vaari, J. 81 (1994) 289
Vaara, T., J. Lahtinen and P. Hautojärvi, Reactions of CO and NO on Mg promoted cobalt 89 (1995) 103
Vaari, J., T. Vaara, J. Lahtinen and P. Hautojärvi, Adsorption of CO on Mg-promoted Co(poly) 81 (1994) 289
Väkeväinen, K., see Ahlgren, T. 90 (1995) 419
Valla, T., P. Pervan and M. Milun, Interaction of oxygen and silver on the V(100) surface 89 (1995) 375
Van Bakel, G.P.E.M., K. Hariharan and D.N. Seidman, On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy 90 (1995) 95
Van de Leest, R.E., UV photo-annealing of thin sol–gel films 86 (1995) 278
Van der Vleuten, W.C., see Hopkins, J. 84 (1995) 299
Van Hardeveld, R.M., P.L.J. Gunter, L.J. van IJzendoorn, W. Wieldraaijer, E.W. Kuipers and J.W. Niemantsverdriet, De-

position of inorganic salts from solution on flat substrates by spin-coating: theory, quantification and application to model catalysts 84 (1995) 339
Van Hoecke, T., see Segers, D. 85 (1995) 172
Van IJzendoorn, L.J., see Van Hardeveld, R.M. 84 (1995) 339
Van Kooten, W.E.J., J.P.C. van Nispen, O.L.J. Gijzeman and J.W. Geus, The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111) 90 (1995) 137
Van Nispen, J.P.C., see Van Kooten, W.E.J. 90 (1995) 137
Van Veen, A., see Seijbel, L.J. 85 (1995) 92
Van Veen, A., H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. IJpma, VEPFIT applied to depth profiling problems 85 (1995) 216
Van Veen, A., see Schut, H. 85 (1995) 225
Van Veen, A., see Hakvoort, R.A. 85 (1995) 271
Van Wijk, R., P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus, XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100) 90 (1995) 261
Vancu, A., see Ionescu, R. 84 (1995) 291
Varela, M., see Palau, J. 86 (1995) 59
Varela, M., see Queralt, X. 86 (1995) 95
Vasumathi, D., G. Amarendra, K.F. Canter and A.P. Mills, Jr., Installation of a Kr moderator in the high-brightness beam at Brandeis 85 (1995) 154
Vasumathi, D., see Canter, K.F. 85 (1995) 339
Vavassori, P., L. Callegaro and E. Puppin, Ultraviolet inverse photoemission study of the oxidation of YFe_2 89 (1995) 93
Vega, F., see Gonzalo, J. 86 (1995) 40
Veith, M., see Piscevic, D. 90 (1995) 425
Velikevitch, S.P., see Berjeza, N.A. 86 (1995) 303
Velotta, R., see Amoruso, S. 86 (1995) 35
Venkateswarlu, D.S., see Sil, A. 81 (1994) 469
Verbeeck, R., see Donaton, R.A. 89 (1995) 221
Vergnat, M., see Hadj Zoubir, N. 89 (1995) 35
Vetrivel, R., R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta, Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations 82/83 (1994) 516
Vetrivel, R., see Himei, H. 82/83 (1994) 543
Vetrivel, R., see Kubo, M. 82/83 (1994) 559
Vetrivel, R., see Kubo, M. 89 (1995) 131
Vickerman, J.C., see Leggett, G.J. 84 (1995) 253
Vijayakrishnan, V., see Rao, C.N.R. 84 (1995) 285
Villatte, M., see Fauquet, C. 81 (1994) 435
Vitek, J.M., see Babu, S.S. 87/88 (1995) 207
Vitel, Y., see Flicstein, J. 86 (1995) 286
Viville, P., O. Thoelen, S. Beauvois, R. Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude, Thin films of polymer blends: surface treatment and theoretical modeling 86 (1995) 411
Vladimirov, V.V. and P.V. Poritsky, On the theory of ion current onset delay in liquid metal ion sources 87/88 (1995) 106
Vladimirov, V.V., V.N. Gorshkov and D.V. Mozyrsky, The dynamical effects in liquid-metal ion sources 87/88 (1995) 112
Vlasov, Yu.A., see Unger, J. 87/88 (1995) 45
Vodolaga, B.K., see Pimenov, S.M. 86 (1995) 208
Von Känel, H., see Kafader, U. 90 (1995) 297
Vook, R.W., see Jo, B.H. 89 (1995) 237
Voss, C. and N. Kruse, Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt 87/88 (1995) 127
Voss, C. and N. Kruse, Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt 87/88 (1995) 134
Vošta, J., see Pingo, M. 90 (1995) 373
Vydra, V., see Černý, R. 86 (1995) 359

Wada, K., Defects and material processing in compound semiconductors 85 (1995) 246
Waeber, W.B., see Gerola, D. 85 (1995) 106
Waeber, W.B., see Shi, M. 85 (1995) 143
Wagner, F.X., see Dyer, P.E. 86 (1995) 18
Wagner, F.X., K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls, Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe 86 (1995) 364
Wallace, S., see Hulett, Jr., L.D. 85 (1995) 334
Wang, F., M. Badaye, K. Ogawa and T. Morishita, Recovery and recrystallization of $SrTiO_3(100)$ surface characterized by ion channeling 90 (1995) 123
Wang, J., X. Fei, Z. Yu and G. Zhao, Laser-induced selective deposition of Ni–P alloy on silicon 84 (1995) 383
Wang, P., see Durrer, W.G. 81 (1994) 215
Wang, P.W., L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser, Surface modification of lead silicate glass under X-ray irradiation 84 (1995) 75
Wang, P.W., S. Bater, L.P. Zhang, M. Ascherl and J.H. Craig, Jr., XPS investigation of electron beam effects on a trimethylsilane dosed Si(100) surface 90 (1995) 413
Wang, R., see Gu, S. 81 (1994) 431
Wang, T., see Fang, Y. 89 (1995) 331
Wang, X.D., see Sakurai, T. 87/88 (1995) 405
Wang, X.K., N.F. Shen, Z.S. Yang and H.C. Gu, Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2Al_{0.2}$ catalysts 89 (1995) 297

Wang, Y., see Chen, X. 89 (1995) 169
Wanklyn, B.M., see Sharma, K.K. 81 (1994) 251
Wanklyn, B.M., see Jain, A. 84 (1995) 65
Washio, M., see Hirose, M. 85 (1995) 111
Watamori, M., M. Naitoh, H. Morioka, Y. Maeda and K. Oura, Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis 82/83 (1994) 417
Watamori, M., see Tanaka, Y. 82/83 (1994) 528
Watanabe, H., see Asahi, H. 82/83 (1994) 109
Watanabe, T., see Hirai, M. 82/83 (1994) 23
Watanabe, T., see Sakuraba, M. 82/83 (1994) 354
Watanabe, Y., F. Maeda and M. Oshima, Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001) 82/83 (1994) 136
Watanabe, Y., see Maeda, F. 82/83 (1994) 276
Watanabe, Y., see Heun, S. 82/83 (1994) 507
Watts, J.F., see Salvi, A.M. 90 (1995) 333
Way, J.D., see George, S.M. 82/83 (1994) 460
Weaver, L., see Lawther, D.W. 85 (1995) 265
Wee, A.T.S., Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston, Surface chemical states on 3C-SiC/Si epilayers 81 (1994) 377
Wehner, M., see Pflüger, S. 86 (1995) 504
Wei, R.P., see Dwyer, D.J. 81 (1994) 229
Wei, Y., see Zhang, X.Q. 84 (1995) 267
Wei, Y., see Yang, X.-M. 90 (1995) 175
Weir, B.E., D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick, Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon 84 (1995) 413
Weiss, A.H., see Fazleev, N.G. 85 (1995) 22
Weiss, A.H., see Fazleev, N.G. 85 (1995) 26
Weiss, A.H., see Yang, G. 85 (1995) 77
Weiss, A.H., S. Yang, H.Q. Zhou, E. Jung, A.R. Koymen, S. Naidu, G. Brauer and M.J. Puska, Method for the measurement of positron affinities and positron work functions suitable for both positive and negative work function materials 85 (1995) 82
Weissmantel, S., see Reisse, G. 86 (1995) 107
Weissmantel, S., see Reisse, G. 86 (1995) 114
Welch, D.O., see Ghosh, V.J. 85 (1995) 210
Weng, H., see Ling, C.C. 85 (1995) 305
Weng, L.T., P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet, Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black 84 (1995) 9
Wesemann, J., G. Frommeyer and M. Kreuss, APFIM investigations on ordered γ-TiAl using single-layer detection method 87/88 (1995) 179
Wesley, S.A., see Canter, K.F. 85 (1995) 339
Wesner, D.A., see Klotzbücher, T. 86 (1995) 165
Wesner, D.A., see Kreutz, E.W. 86 (1995) 266
Wesner, D.A., see Frerichs, H. 86 (1995) 405
West, R.H., see Smith, G.C. 90 (1995) 357
Wetzel, P., see Hong, S. 90 (1995) 65
White, J.M., see Asami, S. 82/83 (1994) 359
Wieldraaijer, W., see Van Hardeveld, R.M. 84 (1995) 339
Wijekoon, W.M.K.P., E.W. Koenig, W.M. Hetherington III and W.R. Salzman, Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface 81 (1994) 347
Winkler, A., see Karstens, H. 86 (1995) 521
Wise, M.L., see Okada, L.A. 82/83 (1994) 410
Wise, M.L., see George, S.M. 82/83 (1994) 460
Wissenbach, K., see Kreutz, E.W. 86 (1995) 310
Wolff-Rottke, B., see Ihlemann, J. 86 (1995) 228
Wolff-Rottke, B., see Ihlemann, J. 86 (1995) 245
Wolfram, Z., see Duś, R. 90 (1995) 277
Wollenberger, H., see Al-Kassab, T. 87/88 (1995) 329
Wolter, J.H., see Hopkins, J. 84 (1995) 299
Wong, P.C., Y.S. Li and K.A.R. Mitchell, Investigations of the interface between magnesium and polyethyleneterephthalate by X-ray photoelectron spectroscopy 84 (1995) 245
Wong, P.C., Y.S. Li, M.Y. Zhou and K.A.R. Mitchell, XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film 89 (1995) 255
Wong, P.C., see Li, Y.S. 89 (1995) 263
Woods, R., see Buckley, A.N. 84 (1995) 223
Wu, C.Z., see Wu, J.D. 90 (1995) 81
Wu, J., S. Li, G. Li, C. Li and Q. Xin, FT-IR investigation of methane adsorption on silica 81 (1994) 37
Wu, J.D., C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li, Synthesis of molybdenum nitride γ-Mo_2N by multipulse laser irradiation of molybdenum in nitrogen 90 (1995) 81
Wu, L.H., see Wu, J.D. 90 (1995) 81
Wu, N.J., see Zomorrodian, A. 90 (1995) 343
Wu, S. and D. Haneman, Cadmium selenide–amorphous hydrogenated silicon heterostructures 89 (1995) 289
Wysocki, T., see Bryl, R. 87/88 (1995) 69

Xiao, D., see Yang, X.-M. 90 (1995) 175
Xiao, X.R., Y. Lin, Y. Yang, X.G. Chen and J.K. You, Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes 90 (1995) 321
Xie, L., see Jiang, S. 84 (1995) 373
Xie, R., see Canter, K.F. 85 (1995) 339
Xin, Q., see Wu, J. 81 (1994) 37

Xin, X.Q., see Ye, X.R. 89 (1995) 151
Xu, J., L.D. Hulett, Jr., T.A. Lewis and N.H. Tolk, Light emission from polymers under positron and electron bombardment 85 (1995) 49
Xu, J., see Ling, C.C. 85 (1995) 305
Xu, J., see Hulett, Jr., L.D. 85 (1995) 334
Xue, G., see Ji, G. 81 (1994) 63
Xue, G., see Guo, S. 84 (1995) 351
Xue, G., J. Ding and P. Cheng, Growth of a surface film on copper from benzotriazole solutions 89 (1995) 77
Xue, Q., T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai, MBE-STM study of the Ga-rich 4×2 phase of the GaAs(001) surface 87/88 (1995) 364
Xue, Q.K., see Hashizume, T. 87/88 (1995) 373

Yago, H., T. Nomura and K. Ishikawa, Strain relaxation in GaAs islands on GaP(001) 84 (1995) 119
Yakubtsov, O.A., see Dmitruk, N.L. 90 (1995) 489
Yamada, M., see Ide, Y. 82/83 (1994) 310
Yamada, M., see Sasaki, M. 82/83 (1994) 387
Yamaguchi, H., Y. Homma and Y. Horikoshi, In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy 82/83 (1994) 223
Yamaguchi, M., see Shirai, Y. 85 (1995) 138
Yamaguchi, S., see Kawasuso, A. 85 (1995) 280
Yamaguchi, Y., see Nagasawa, H. 82/83 (1994) 405
Yamamoto, M., see Otake, S. 82/83 (1994) 263
Yamamoto, M., K. Nishikawa and T. Nishiuchi, Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy 87/88 (1995) 291
Yamamoto, R., see Oshima, N. 85 (1995) 329
Yamamoto, T., see Nunogaki, M. 85 (1995) 132
Yamamoto, Y., see Ohnishi, H. 82/83 (1994) 444
Yamamoto, Y., see Itoh, Y. 85 (1995) 165
Yamano, H., see Vetrivel, R. 82/83 (1994) 516
Yamashita, M., see Suda, Y. 82/83 (1994) 332
Yamauchi, R., see Vetrivel, R. 82/83 (1994) 516
Yamauchi, R., see Kubo, M. 82/83 (1994) 559
Yamauchi, R., see Kubo, M. 89 (1995) 131
Yamazaki, T., see Suzuki, R. 85 (1995) 87
Yan, P. and S.-Z. Yang, Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature 90 (1995) 149
Yanagisawa, Y., Oxygen exchange between adsorbed NO and MgO surfaces 89 (1995) 251
Yanchenko, A.M., see Fedotov, A.K. 84 (1995) 379
Yang, G., J.H. Kim, S. Yang and A.H. Weiss, Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES) 85 (1995) 77
Yang, S., see Yang, G. 85 (1995) 77
Yang, S., see Weiss, A.H. 85 (1995) 82
Yang, S.-J., see Li, C. 81 (1994) 465
Yang, S.-Z., see Yan, P. 90 (1995) 149
Yang, W.Y., see Zhang, X.Q. 84 (1995) 267
Yang, X.-M., D. Xiao, Z.-H. Lu and Y. Wei, Structural investigation of Langmuir–Blodgett monolayers of L-α-dipalmitoylphosphatidylcholine by atomic force microscopy 90 (1995) 175
Yang, Y., see Xiao, X.R. 90 (1995) 321
Yang, Z.S., see Wang, X.K. 89 (1995) 297
Yao, J.N., see Loo, B.H. 81 (1994) 175
Yao, T., see Uesugi, K. 82/83 (1994) 367
Yao, T., see Takiguchi, T. 82/83 (1994) 428
Yasuda, T., see Hata, K. 87/88 (1995) 117
Yates, Jr., J.T., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke, Activation of the Ga–CH_3 bond using atomic hydrogen – a possible route to III–V semiconductor films with low carbon levels 82/83 (1994) 180
Ye, X.R., H.W. Hou, X.Q. Xin and C.F. Hammer, M–S (M = Mo, W) cluster compound films on copper surfaces 89 (1995) 151
Yelon, A., see Meunier, M. 86 (1995) 475
Yen, J.C., see Keller, B.P. 82/83 (1994) 126
Yen, R.-B., see Li, C. 81 (1994) 465
Yeom, H.W., see Sasaki, M. 82/83 (1994) 387
Yokoyama, H., M. Tanimoto, M. Shinohara and N. Inoue, Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy 82/83 (1994) 158
Yokoyama, N., see Sakuma, Y. 82/83 (1994) 46
Yokoyama, N., see Sakuma, Y. 82/83 (1994) 239
Yokoyama, S., see Keil, M. 90 (1995) 377
Yom, S.S., see Kim, T.W. 90 (1995) 75
Yonezawa, Y., see Masuda, A. 81 (1994) 277
Yoon, Y.S., see Kim, T.W. 90 (1995) 75
York, T.H., see Tyrrell, G.C. 86 (1995) 50
Yoshida, I., H. Furukawa, T. Hirosawa and M. Nakao, Fabrication of CuO_2-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy 82/83 (1994) 501
Yoshida, S. and M. Sasaki, Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE 82/83 (1994) 28
Yoshida, S., see Sasaki, M. 82/83 (1994) 269
Yoshida, S. and H. Ishida, An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection–absorption spectroscopy 89 (1995) 39
Yoshikawa, A., M. Kobayashi and S. Tokita, Surface reaction mechanism in

MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method 82/83 (1994) 316
Yoshimura, M., see Uesugi, K. 82/83 (1994) 367
Yoshimura, M., see Takiguchi, T. 82/83 (1994) 428
Yoshino, J., see Kano, N. 82/83 (1994) 132
You, J.K., see Xiao, X.R. 90 (1995) 321
You, X.Z., see Zhang, X.Q. 84 (1995) 267
Yu, H., M.G. Huber and F.W. Froben, Laser ablation of refractory material, cluster formation and deposition 86 (1995) 74
Yu, W., see Sullivan, J.L. 90 (1995) 309
Yu, Z., see Wang, J. 84 (1995) 383
Yurov, V., see Sakurai, T. 87/88 (1995) 405
Yusifov, F.K., see Tontegode, A.Ya. 90 (1995) 185

Zemek, J., see D'Anna, E. 86 (1995) 170
Zhang, J.-Y., see Esrom, H. 86 (1995) 202
Zhang, L.P., see Wang, P.W. 84 (1995) 75
Zhang, L.P., see Wang, P.W. 90 (1995) 413
Zhang, R., see Gu, S. 81 (1994) 431
Zhang, X.Q., W.Y. Yang, X.Z. You and Y. Wei, Preparation and characterization of self-assembly organic multilayer films on silica surface 84 (1995) 267
Zhao, G., see Wang, J. 84 (1995) 383
Zhao, R., see Holt, S.A. 84 (1995) 125
Zhao, X., see Jiang, S. 84 (1995) 373
Zhdanov, V.P. and P.R. Norton, Nucleation during molecular beam epitaxy 81 (1994) 109
Zhdanov, V.P., see Kasza, R.V. 84 (1994) 97
Zheng, Y., see Gu, S. 81 (1994) 431
Zherikhin, A.N., see Sobol, E.N. 90 (1995) 235
Zhirnov, V.V., see Givargizov, E.I. 87/88 (1995) 24
Zhong, P., see Gu, S. 81 (1994) 431
Zhou, H.Q., see Weiss, A.H. 85 (1995) 82
Zhou, J.M., see Xue, Q. 87/88 (1995) 364
Zhou, M.Y., see Wong, P.C. 89 (1995) 255
Zhu, Y., see Canter, K.F. 85 (1995) 339
Zielasek, V., A. Büssenschütt and M. Henzler, Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum 90 (1995) 117
Zimmermann, U., see Shi, M. 85 (1995) 143
Zomorrodian, A., A. Mesarwi, N.J. Wu and A. Ignatiev, XPS oxygen line broadening in lead zirconium titanate and related materials 90 (1995) 343
Zotov, A.V., see Khramtsova, E.A. 82/83 (1994) 576
Zou, H., G.M. Hood, R.J. Schultz and J.A. Roy, Thermal etching of α-Zr single-crystal surfaces 90 (1995) 59
Zurita, L., see Durán, J.D.G. 81 (1994) 1

ELSEVIER

Applied Surface Science MI 81–90 (1995) 33–115

applied surface science

Subject index to volumes 81–90

Ablation

The laser ablation threshold of $YBa_2Cu_3O_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13

Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18

Pulsed laser ablation of copper, R. Jordan, D. Cole, J.G. Lunney, K. Mackay and D. Givord 86 (1995) 24

Why are high-T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm^2?, R.W. Dreyfus 86 (1995) 29

Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35

Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40

Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45

Characterisation of ionic species generated during ablation of $Bi_2Sr_2Ca_2Cu_3O_{10}$ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50

Laser wavelength dependence of $YBa_2Cu_3O_y$ laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehé 86 (1995) 59

Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64

Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68

Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74

Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79

Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86

Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90

Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95

Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99

Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107

Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114

Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122

SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
Pulsed laser deposition and nanometer scale characterization of $YBa_2Cu_3O_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
Pulsed laser deposition of $NbTe_x$ thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170
$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
Optodynamic aspect of a pulsed laser ablation process, R. Hrovatin and J. Možina 86 (1995) 213
Atypical characteristics of KrF excimer laser ablation of indium–tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228
Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239
Structuring of polyimide–metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
Combination of excimer laser micromachining and replication processes suited for large scale production, J. Arnold, U. Dasbach, W. Ehrfeld, K. Hesch and H. Löwe 86 (1995) 251
Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaan and M. Prasad 86 (1995) 548
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
Macro-particle ejection by laser ablation of high-temperature superconductors, E.N. Sobol, M.S. Kitai, S.M. Gol'berg and A.N. Zherikhin 90 (1995) 235
Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Alkali halides

Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declemy and Ph. Goudeau 81 (1994) 119
Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117

Alkali metals

The adsorption of sodium dodecyl sulphate on fluorite and its surface free energy, B. Jańczuk, M.L. González-Martín and J.M. Bruque 81 (1994) 95

Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
XPS investigation of lithium borate glass and the $Li/LiBO_2$ interface, D.A. Hensley and S.H. Garofalini 81 (1994) 331
LiBr on Si(111): an X-ray standing wave measurement, Th. Gog, G.C. Follis and S.M. Durbin 81 (1994) 485
Adsorption and desorption of H_2O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
Evidence for infrared absorption enhancement of species at the lithium metal/electrolytic solution interface, Y. Suzuki, K. Sagisaka and A. Hatta 84 (1995) 1
Theoretical study of the positron surface state at an alkali-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler and A.H. Weiss 85 (1995) 22
Study of positron surface states on the alkali-metal-covered transition-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss 85 (1995) 26
Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
A FEM study of liquid lithium on a ⟨011⟩-oriented tungsten tip, K. Hata, M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita 87/88 (1995) 117
Scanning tunneling microscopy study of the (3 × 1) reconstruction induced by Li adsorption on the Si(111) surface, R.Z. Bakhtizin, C. Park, T. Hashizume and T. Sakurai 87/88 (1995) 347
A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}Cs^+$ beam, H. Tomizuka and A. Ayame 89 (1995) 281
Influence of surface charge on thermal positive ion emission from potassium bromide, M.F. Butman, J. Nakamura, S. Kamidoi and H. Kawano 89 (1995) 323
Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
An XPS study of the optimum loading of barium on high-silica MFI zeolite, M.H. Mohamed, M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui 90 (1995) 409
SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy 90 (1995) 447

Alloys

Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143
Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
Matrix factors affecting quantitative analysis of AES for binary alloys, H. Bubert and R.P.H. Garten 81 (1994) 203
Surface enrichment of niobium on Inconel 718 (100) single crystals, D.J. Dwyer, X.J. Pang, M. Gao and R.P. Wei 81 (1994) 229
The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
Thermodynamics and kinetics of solidification of Si–As solutions, R. Reitano 86 (1995) 323
Atom probe studies of nanostructured alloys, K. Hono and T. Sakurai 87/88 (1995) 166
APFIM investigations on ordered γ-TiAl using single-layer detection method, J.

Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179
Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
Characterization of neutron-irradiated Fe–Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy, C. Schmuck, P. Auger, F. Danoix and D. Blavette 87/88 (1995) 228
An APFIM/TEM investigation of the discontinuous precipitation in a Ni–In alloy, G.P. Geber 87/88 (1995) 234
Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
Effect of low-energy (20–40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin 87/88 (1995) 257
APFIM study of the compositional inhomogeneity of sputtered Co–Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambreland, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi 87/88 (1995) 291
A study of the effect of ageing temperature on phase separation in Fe–45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
Comparison of low temperature decomposition in Fe–Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1
Ultraviolet inverse photoemission study of the oxidation of YFe_2, P. Vavassori, L. Callegaro and E. Puppin 89 (1995) 93
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and coadsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
Erratum to "Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
Surface segregation and core-level shift of a Pd–Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515

Aluminium

Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
Evaluation of matrix effects in SIMS quantification of $Al_xGa_{1-x}As/GaAs$ heterostructures: a SNMS approach, A. Torrisi, A. Scandurra and A. Licciardello 81 (1994) 259
Comment on 'Influence of surface composition on initial hydration of aluminium in boiling water' by A. Strålin and T. Hjertberg, B.R. Strohmeier 81 (1994) 273
Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V.

Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
Flow modulation epitaxy of $Ga_xIn_{1-x}As$/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $Al_xGa_{1-x}As$ on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208
Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$ and AsH_3, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
Atomic-scale modification of the $AlCl_3$-adsorbed Si(111)-7 × 7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
An FT-IR investigation of parabactin adsorbed onto aluminum, D.C. Hansen, E. McCafferty, C.W. Lins and J.J. Fitzpatrick 84 (1995) 85
AFM investigations of the initial stages of prepolymer film growth on aluminium, T. Gesang, R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann 84 (1995) 273
A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter 84 (1995) 299
Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
Energy loss measurements for 20 keV positrons in Al thin films, G.R. Massoumi, W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson 85 (1995) 39
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325
Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
UV light irradiation effects on nucleation during chemical vapor deposition of Al films, M. Hanabusa and A. Komatsu 86 (1995) 428
Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488
Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy, C. Schmuck, P. Auger, F. Danoix and D. Blavette 87/88 (1995) 228
X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on

Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin 89 (1995) 401
On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman 90 (1995) 95
Erratum to "Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107

Aluminium oxide

Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda 82/83 (1994) 481
Electrical properties of $Si–Al_2O_3$ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the $CO + H_2$ reaction over lanthanide-modified Rh/Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391
Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter 86 (1995) 368
XPS studies of the effect of Mn on Pd/Al_2O_3, P.C. L'Argentière, M.G. Cañón and N.S. Fígoli 89 (1995) 63
A study of the composition distribution at the Ti/Al_2O_3 interface using the MCs^+-SIMS technique, X. Chen and Y. Wang 89 (1995) 169
Interfacial reaction of NiO with Al_2O_3-$(11\bar{2}0)$ and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339

Ammonia

SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem 81 (1994) 127
Chemical reactivity of the $Si(111)(\sqrt{3} \times \sqrt{3})R30°$-B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima 82/83 (1994) 434
Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297

Annealing

Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnarends and H. Schut 85 (1995) 271
An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique , A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino 85 (1995) 280
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
UV photo-annealing of thin sol–gel films, R.E. Van de Leest 86 (1995) 278
Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics, J. Flicstein, Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe 86 (1995) 286
Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii 86 (1995) 299
Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas 90 (1995) 455

Antimony

Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy,

H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
Surface segregation of Sb in doped TiO_2 rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdell 90 (1995) 289
A photoemission study of electron states in Sb-ion implanted TiO_2(110), A.E. Taverner, A. Gulino, R.G. Egdell and T.J. Tate 90 (1995) 383

Argon

Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
Threshold behavior of ionization and excitation cross sections of He and Ar by positron impact, O. Sueoka, B. Jin and A. Hamada 85 (1995) 59

Arsenic

A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
Variable-energy positron beam study of arsenic diffusion in poly-silicon, D.W. Lawther, R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver 85 (1995) 265
Thermodynamics and kinetics of solidification of Si–As solutions, R. Reitano 86 (1995) 323

Atomic force microscopy

Growth of excimer-laser-induced dendritic surface structures on polyethyleneterephthalate, J. Heitz, E. Arenholz, D. Bäuerle and K. Schilcher 81 (1994) 103
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
Atomic force microscopic study of directional $SrSO_4$(001) surface and its etching property, A. Seo and H. Shindo 82/83 (1994) 475
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553

Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration, S.A. Holt, R. Zhao and S. Myhra 84 (1995) 125
Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
AFM investigations of the initial stages of prepolymer film growth on aluminium, T. Gesang, R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann 84 (1995) 273
Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
Pulsed laser deposition and nanometer scale characterization of $YBa_2Cu_3O_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
Laser chemical vapour deposition for microelectronics, G. Auvert 86 (1995) 466
VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
Laser chemical etching of Cu_2O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
Thickness determination of uniform overlayers on rough substrates by angle-dependent XPS, P.L.J. Gunter and J.W. Niemantsverdriet 89 (1995) 69
Atomic force microscopy determination of the topography of fly-ash particles, C.M. Demanet 89 (1995) 97
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155
Structural investigation of Langmuir–Blodgett monolayers of L-α-dipalmitoylphosphatidylcholine by atomic force microscopy, X.-M. Yang, D. Xiao, Z.-H. Lu and Y. Wei 90 (1995) 175
AFM and XPS characterization of the Si(111) surface after thermal treatment, B. Lamontagne, D. Guay, D. Roy, R. Sporken and R. Caudano 90 (1995) 481

Atomic probe analysis

Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37
Atom probe studies of nanostructured alloys, K. Hono and T. Sakurai 87/88 (1995) 166
APFIM investigations on ordered γ-TiAl using single-layer detection method, J. Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179
The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels, R.C. Thomson and M.K. Miller 87/88 (1995) 185
Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz 87/88 (1995) 194
Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
Atom probe field ion microscopy of type 308 CRE stainless steel welds, S.S. Babu, S.A. David, J.M. Vitek and M.K. Miller 87/88 (1995) 207
Characterization of neutron-irradiated Fe–Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
Nucleation and growth of θ' precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy, C. Schmuck, P. Auger, F. Danoix and D. Blavette 87/88 (1995) 228
Atom probe analysis of interfacial segregation, M.K. Miller and G.D.W. Smith 87/88 (1995) 243

Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
APFIM study of the compositional inhomogeneity of sputtered Co–Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
A general protocol for the reconstruction of 3D atom probe data, P. Bas, A. Bostel, B. Deconihout and D. Blavette 87/88 (1995) 298
A method for reconstructing and locating atoms on the crystal lattice in three-dimensional atom probe data, P.P. Camus, D.J. Larson and T.F. Kelly 87/88 (1995) 305
A study of the effect of ageing temperature on phase separation in Fe–45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
Comparison of low temperature decomposition in Fe–Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
FIM/AP analysis of Cu–Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329
Improvements in the transmission of voltage evaporation pulses in the atom probe, S.J. Sijbrandij, A. Cerezo and G.D.W. Smith 87/88 (1995) 414
Performance of the multiple events position sensitive detector used in the tomographic atom probe, B. Deconihout, A. Bostel, M. Bouet, J.M. Sarrau, P. Bas and D. Blavette 87/88 (1995) 428
Microfabrication of extraction electrodes for local-electrode atom probes, S.S. Bajikar, T.F. Kelly, C.-M. Teng and P.P. Camus 87/88 (1995) 438
Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly 87/88 (1995) 446
The performance of the IMR three-dimensional atom probe, K. Hono, R. Okano, T. Saeda and T. Sakurai 87/88 (1995) 453
On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman 90 (1995) 95

Auger electron spectroscopy

An AES study of intrinsic and ion-induced structure in the SiO_2–Si system, B. Lang, B. Sefsaf and G. Allan 81 (1994) 17
The smoothing properties of some new shapes for transmission functions in Fourier space. A real case study on exemplary noisy Auger spectra, R. Siuda 81 (1994) 27
Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
Electron-beam-induced oxidation of CdS, V.B. Mityukhlyaev 81 (1994) 137
Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143
Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161
Matrix factors affecting quantitative analysis of AES for binary alloys, H. Bubert and R.P.H. Garten 81 (1994) 203
Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
Modified relative sensitivity factors for Auger spectra, F. Pavlyak 81 (1994) 351
Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G.

Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
Activation of the Ga–CH_3 bond using atomic hydrogen – a possible route to III–V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
Self-limiting adsorption of thermally cracked $SiCl_2H_2$ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants, J.A. Schreifels, N.H. Turner and R.E. Morris 84 (1995) 23
Adsorption and co-adsorption of boron and oxygen on ordered α-SiC surfaces, V.M. Bermudez 84 (1995) 45
Initial oxidation kinetics of Fe–Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
AES and XPS study of thin RF-sputtered Ta_2O_5 layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
Multi-spectral scanning Auger microscopy of tribological surfaces, I.R. Barkshire, M. Prutton and G.C. Smith 84 (1995) 331
Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss 85 (1995) 77
Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
M–S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
Quantitative correction of backscattering in Auger electron spectroscopy of thin films, G. Lévêque and J. Bonnet 89 (1995) 211
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
Synthesis of molybdenum nitride γ-Mo_2N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bear-

ing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
Determining hybridization differences for amorphous carbon from the XPS C 1s envelope, S.T. Jackson and R.G. Nuzzo 90 (1995) 195
XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
Morphology, atomic composition and photoelectric properties of the microrelief InP–electrolyte interface, N.L. Dmitruk, E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets 90 (1995) 489

Barium

Modelling of barium transport in dispenser cathodes, A. Sil and D.S. Venkateswarlu 81 (1994) 469
Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75

Beryllium

Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211

Biological materials

An FT-IR investigation of parabactin adsorbed onto aluminum, D.C. Hansen, E. McCafferty, C.W. Lins and J.J. Fitzpatrick 84 (1995) 85

Bismuth

Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration, S.A. Holt, R. Zhao and S. Myhra 84 (1995) 125

Borides

Chemical etching of (100) and (110) faces of flux-grown $LaBO_3$ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65

Boron

Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
Adsorption and co-adsorption of boron and oxygen on ordered α-SiC surfaces, V.M. Bermudez 84 (1995) 45
Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413

Boron nitride

Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149

Cadmium

Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
Photo-assisted growth and characterization of $Zn_xCd_{1-x}S$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442

Cadmium selenide

Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
Cadmium selenide–amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes, X.R. Xiao, Y. Lin, Y. Yang, X.G. Chen and J.K. You 90 (1995) 321

Cadmium sulphide

Surface thermodynamic properties of cadmium sulfide, J.D.G. Durán, L. Zurita, M.C. Guindo, A.V. Delgado and F. González-Caballero 81 (1994) 1
Electron-beam-induced oxidation of CdS, V.B. Mityukhlyaev 81 (1994) 137

Cadmium telluride

A positron annihilation study of the formation of defect layers in cadmium mercury telluride, A. Towner, P.C. Rice-Evans and N. Shaw 85 (1995) 315
Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan 89 (1995) 159

Calcium

A study of $CaO–SO_2$ interaction, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 409
A study of $CaO–SO_2$ interaction in the presence of O_2, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
A new parameter to characterize limestones as SO_2 sorbents, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 89 (1995) 197

Carbides

Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
Structuring of polyimide–metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz 87/88 (1995) 194

Carbon

Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74
Laser diagnostics of C_{60} and C_{70} films by broadband surface acoustic wave spectroscopy, A.A. Kolomenskii, M. Szabadi and P. Hess 86 (1995) 591
Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study, M. Devel, C. Girard, C. Joachim and O.J.F. Martin 87/88 (1995) 390
Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guczi 90 (1995) 165
Determining hybridization differences for amorphous carbon from the XPS C 1s envelope, S.T. Jackson and R.G. Nuzzo 90 (1995) 195
Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271

Carbon dioxide

Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
Surface interaction between H_2 and CO_2 over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah 90 (1995) 393

Carbon monoxide

Adsorption of CO on Mg-promoted Co-(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289

CO adsorption on clean and atomic-layer-Cu-covered ZnO($10\bar{1}0$) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the CO + H_2 reaction over lanthanide-modified Rh/Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391
Investigation of adsorption and coadsorption of O_2 and CO on Rh by O_2^+ field ion and Li^+ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block 87/88 (1995) 159
Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and coadsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137

Catalysis

Identification of active species and theoretical classification of simple catalyst oxides using surface redox couples, Y.P. Arnaud and H. Bertrais 81 (1994) 69
The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
In-situ FTIR investigation of coke formation on USY zeolite, C. Li, Y.-W. Chen, S.-J. Yang and R.-B. Yen 81 (1994) 465
Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
Deposition of inorganic salts from solution on flat substrates by spin-coating: theory, quantification and application to model catalysts, R.M. Van Hardeveld, P.L.J. Gunter, L.J. Van IJzendoorn, W. Wieldraaijer, E.W. Kuipers and J.W. Niemantsverdriet 84 (1995) 339
The distribution of activation energy for hydrogen desorption over silica-supported nickel catalysts determined from temperature-programmed desorption spectra, M. Arai, Y. Nishiyama, T. Masuda and K. Hashimoto 89 (1995) 11
Preparation of a model Ziegler–Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297

Ceramics

Laser–surface processing of metals and ceramics for industrial applications, H.W. Bergmann, K. Schutte, E. Schubert and A. Emmel 86 (1995) 259

Chemical vapour deposition

Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
Characterization of adsorption in flow type atomic layer epitaxy reactor, J. Aarik and H. Siimon 81 (1994) 281
Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by

metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$ and AsH_3, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer expitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
Sub-atomic-layer epitaxy of Si using Si_2H_6, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
Self-limiting adsorption of thermally cracked $SiCl_2H_2$ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
Mechanisms of SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2, H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
Isothermal H_2 desorption kinetics from Si(100)2 × 1: dependence on disilane

and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
$NbCl_5$ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics, J. Flicstein, Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe 86 (1995) 286
Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
UV light irradiation effects on nucleation during chemical vapor deposition of Al films, M. Hanabusa and A. Komatsu 86 (1995) 428
Photoassisted growth of II–VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
Photo-assisted growth and characterization of $Zn_xCd_{1-x}S$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
Laser chemical vapour deposition for microelectronics, G. Auvert 86 (1995) 466
Laser processing of tungsten from WF_6 and SiH_4, M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
Laser-induced etching and deposition of tungsten in WF_6–H_2 atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488
The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500
Excimer laser-induced deposition of copper from Cu(hfac)(TMVS), R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
Germanium-containing coatings by IR laser-induced decomposition of ethoxy(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530
P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
Erratum to "Characterization of adsorption in flow type atomic layer epitaxy reactor" [Appl. Surf. Sci. 81 (1994) 281], J. Aarik and H. Siimon 90 (1995) 109

Chromium

The partitioning of substitutional solute elements during the tempering of marten-

site in Cr and Mo containing steels, R.C. Thomson and M.K. Miller 87/88 (1995) 185
Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
APFIM study of the compositional inhomogeneity of sputtered Co–Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
A study of the effect of ageing temperature on phase separation in Fe–45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
Comparison of low temperature decomposition in Fe–Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271
Peak fitting of the chromium 2p XPS spectrum, A.M. Salvi, J.E. Castle, J.F. Watts and E. Desimoni 90 (1995) 333
Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas 90 (1995) 455

Clusters

Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559

Cobalt

Adsorption of CO on Mg-promoted Co(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289
Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
APFIM study of the compositional inhomogeneity of sputtered Co–Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
Etching of $CoSi_2$ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}$ $Co_2Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297

Computer simulations

Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543
Surface barrier sensitivity of positronium formation at surfaces, A. Ishii and T. Aisaka 85 (1995) 33
Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh 85 (1995) 187
VEPFIT applied to depth profiling problems, A. van Veen, H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. IJpma 85 (1995) 216
Extension of the PC version of VEPFIT with input and output routines running under Windows, H. Schut and A. van Veen 85 (1995) 225
Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto 89 (1995) 131
Preferential sputtering of argon ion bombarded Ni_3Al and $TaSi_2$, S. Hofmann and M.G. Stepanova 90 (1995) 227

Copper

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
Effects of atomic hydrogen on Cu(II)bishexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
The electrochemical faceting of copper in 85% aqueous o-phosphoric acid by using a potential reversal technique, A. Hernández Creus, R.M. Souto, S. González, M.M. Laz, R.C. Salvarezza and A.J. Arvia 81 (1994) 387

CO adsorption on clean and atomic-layer-Cu-covered ZnO(10$\bar{1}$0) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry, D.L. Cocke, G.K. Chuah, N. Kruse and J.H. Block 84 (1995) 153
High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation, Ch. Grégoire, J.-J. Pireaux, A. Cros and R. Caudano 84 (1995) 163
Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
Study of positron surface states on the alkali-metal-covered transition-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss 85 (1995) 26
Work function and epithermal positron emission from copper, N. Overton, A.P. Knights, A. Goodyear and P.G. Coleman 85 (1995) 54
Pulsed laser ablation of copper, R. Jordan, D. Cole, J.G. Lunney, K. Mackay and D. Givord 86 (1995) 24
Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
Excimer laser-induced deposition of copper from Cu(hfac)(TMVS), R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
Laser chemical etching of Cu_2O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambreland, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
FIM/AP analysis of Cu–Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329
Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai 87/88 (1995) 380
MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly 87/88 (1995) 446
An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection–absorption spectroscopy, S. Yoshida and H. Ishida 89 (1995) 39
Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
M–S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann 89 (1995) 383
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and coadsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
Erratum to "Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271

Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277

Depth profiling

Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants, J.A. Schreifels, N.H. Turner and R.E. Morris 84 (1995) 23
Defect profiling in multilayered systems using mean depth scaling, G.C. Aers, P.A. Marshall, T.C. Leung and R.D. Goldberg 85 (1995) 196
Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles, V.J. Ghosh, B. Nielsen, K.G. Lynn and D.O. Welch 85 (1995) 210
VEPFIT applied to depth profiling problems, A. van Veen, H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. IJpma 85 (1995) 216
Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito 85 (1995) 229
Surface segregation of Sb in doped TiO_2 rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdell 90 (1995) 289

Deuterium

Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1, M. Suemitsu, H. Nakazawa and N. Miyamoto 82/83 (1994) 449

Diamond

Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov 87/88 (1995) 24

Dielectric constant

Measurement of oxide thickness using a variable-energy positron beam, T.C. Leung, P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz 85 (1995) 292

Diffusion

Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama 85 (1995) 259
Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai 87/88 (1995) 380

Doping effects

Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M.

Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413

Elastic recoil detection

Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417

Electrical properties

Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells, H. Kobayashi, F. Mizuno and Y. Nakato 81 (1994) 399
Ideal static induction transistor implemented with molecular layer epitaxy, P. Płotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
Flow modulation epitaxy of $Ga_xIn_{1-x}As$/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
Electrical properties of Si–Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
Laser-induced formation of porous silicon, V. Baranauskas, G.P. Thim and A. Peled 86 (1995) 398
Electrochemical and photoelectrochemical modification and characterisation of thin passive films, O. Blum and U. König 86 (1995) 417
VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
Capacitance–voltage characteristics of Schottky barrier diode in the presence of deep-level impurities and series resistance, P. Chattopadhyay and S. Sanyal 89 (1995) 205
Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
Cadmium selenide–amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
Influence of surface charge on thermal positive ion emission from potassium bromide, M.F. Butman, J. Nakamura, S. Kamidoi and H. Kawano 89 (1995) 323
Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis 90 (1995) 39
Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
Charge transfer processes in a-WO_3/Si heterostructure during electro- and photochromism, E.A. Tutov and A.A. Baev 90 (1995) 303
Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes, X.R. Xiao, Y. Lin, Y. Yang, X.G. Chen and J.K. You 90 (1995) 321
Morphology, atomic composition and photoelectric properties of the microrelief InP–electrolyte interface, N.L. Dmitruk, E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets 90 (1995) 489
Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Electromigration

Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237

Electron bombardment

Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310

Electron diffraction

Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161

Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309

Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14

Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28

Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136

Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141

Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276

Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290

Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298

Sub-atomic-layer epitaxy of Si using Si_2H_6, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332

Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380

Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387

Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394

Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487

Fabrication of CuO_2-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao 82/83 (1994) 501

A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter 84 (1995) 299

Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107

Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338

GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447

Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530

Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov 87/88 (1995) 24

Structure of the MBE-grown GaAs(001)-(2 × 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai 87/88 (1995) 373

Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113

Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner 90 (1995) 65

Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129

In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297

Electron emission

Secondary electron emission from Ag(100) stimulated by positron and electron impact, A.P. Knights and P.G. Coleman 85 (1995) 43

Electron energy loss spectroscopy

The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265

Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309

Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435

Chemical reactivity of the Si(111)$(\sqrt{3} \times \sqrt{3})$R30°-B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima 82/83 (1994) 434

Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569

High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation, Ch. Grégoire, J.-J. Pireaux, A. Cros and R. Caudano 84 (1995) 163

A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227

The (0001)-surface of 6H-SiC: morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175

Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117

Electron microscopy

Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183

Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309

The electrochemical faceting of copper in 85% aqueous o-phosphoric acid by using a potential reversal technique, A. Hernández Creus, R.M. Souto, S. González, M.M. Laz, R.C. Salvarezza and A.J. Arvia 81 (1994) 387

Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64

Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70

Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122

Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136

Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141

In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223

Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359

Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380

Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394

$NbCl_5$ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468

Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494

Chemical etching of (100) and (110) faces of flux-grown $LaBO_3$ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65

Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325

Multi-spectral scanning Auger microscopy of tribological surfaces, I.R. Barkshire, M. Prutton and G.C. Smith 84 (1995) 331

Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383

Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413

Coupling optics for a combined electron positron scanning microscope, L.J. Seijbel, R.F.J. Neelissen, P. Kruit, A. van Veen and H. Schut 85 (1995) 92

Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen) , K. Kajiyama 85 (1995) 259

Contrast in positron reemission microscopy due to positron trapping by dislocations, K.F. Canter, G. Amarendra, D. Vasumathi, S.A. Wesley, R. Xie, A.P. Mills, Jr., R.L. Sabatini and Y. Zhu 85 (1995) 339

Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1

Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45

Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74

Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99

Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107

Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122

SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128

SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134

Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149

Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154

$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175

Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190

Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208

Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228

Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239

Tailoring of surface properties by removal and deposition with laser radiation, E.W. Kreutz, H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging 86 (1995) 266

Microstructure, chemical composition and properties of the surface layer of M2 steel after laser melting under different conditions, J. Kusiński 86 (1995) 317

Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338

Formation of poly-$Si_{1-x}Ge_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346

Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation, A.V. Demchuk and V.A. Labunov 86 (1995) 353

Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422
GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
Laser chemical vapour deposition for microelectronics, G. Auvert 86 (1995) 466
Laser processing of tungsten from WF_6 and SiH_4, M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
Laser-induced etching and deposition of tungsten in WF_6–H_2 atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
Kinetic model for scanning laser-induced deposition from the liquid phase, Zs. Geretovszky, L. Kelemen, K. Bali and T. Szörényi 86 (1995) 494
Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530
Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov 87/88 (1995) 24
Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
Characterization of neutron-irradiated Fe–Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
An APFIM/TEM investigation of the discontinuous precipitation in a Ni–In alloy, G.P. Geber 87/88 (1995) 234
Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambreland, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
Microfabrication of extraction electrodes for local-electrode atom probes, S.S. Bajikar, T.F. Kelly, C.-M. Teng and P.P. Camus 87/88 (1995) 438
Etching of $CoSi_2$ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229
Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
Interfacial reaction of NiO with Al_2O_3 $(11\bar{2}0)$ and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
Thermal etching of α-Zr single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy 90 (1995) 59
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75

Synthesis of molybdenum nitride γ-Mo_2N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
Erratum to "Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM / TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
Morphology, atomic composition and photoelectric properties of the microrelief InP–electrolyte interface, N.L. Dmitruk, E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets 90 (1995) 489
Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Electron spin resonance

Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294

Ellipsometry

Photoreflectance of strained $Si_{1-x}Ge_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda 82/83 (1994) 481
Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185
Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii 86 (1995) 299
Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyaev and A.S. Medvedev 89 (1995) 49
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
An ellipsometric procedure for the characterization of very thin surface films on absorbing substrates, T. Easwarakhanthan, S. Ravelet and P. Renard 90 (1995) 251

Epitaxy

Nucleation during molecular beam epitaxy, V.P. Zhdanov and P.R. Norton 81 (1994) 109
Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
Characterization of adsorption in flow type atomic layer epitaxy reactor, J. Aarik and H. Siimon 81 (1994) 281
Photoreflectance of strained $Si_{1-x}Ge_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
Atomic layer epitaxy of device quality Al-GaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
Selective MLE growth of GaAs and surface treatment for ideal static induction tran-

sistor (ISIT) application, Y. Oyama, P. Płotka and J. Nishizawa 82/83 (1994) 41
Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
Ideal static induction transistor implemented with molecular layer epitaxy, P. Płotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
Flow modulation epitaxy of $Ga_xIn_{1-x}As$/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$ and AsH_3, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer expitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290

Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
Sub-atomic-layer epitaxy of Si using Si_2H_6, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
Self-limiting adsorption of thermally cracked $SiCl_2H_2$ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
Mechanisms of SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2, H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
$NbCl_5$ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
Fabrication of CuO_2-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao 82/83 (1994) 501
Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
Electrical properties of Si–Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
Strain relaxation in GaAs islands on GaP(001), H. Yago, T. Nomura and K. Ishikawa 84 (1995) 119
A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter 84 (1995) 299
Application of time-dependent diffusion models to the study of real solids, D.T. Britton and J. Störmer 85 (1995) 1
Positron annihilation studies of defects in molecular beam epitaxy grown III–V layers, M.T. Umlor, P. Asoka-Kumar, D.J. Keeble, P.W. Cooke and K.G. Lynn 85 (1995) 295
Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
Photoassisted growth of II–VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
Photo-assisted growth and characterization of $Zn_xCd_{1-x}S$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
GaAs growth by photon-assisted metalorganic molecular beam epitaxy using

ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
In-situ laser reflectometry of the epitaxial growth of thin semiconductor films, T. Farrell and J.V. Armstrong 86 (1995) 582
MBE-STM study of the Ga-rich 4 × 2 phase of the GaAs(001) surface, Q. Xue, T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai 87/88 (1995) 364
Structure of the MBE-grown GaAs(001)-(2 × 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai 87/88 (1995) 373
Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann 89 (1995) 383
Erratum to "Characterization of adsorption in flow type atomic layer epitaxy reactor" [Appl. Surf. Sci. 81 (1994) 281], J. Aarik and H. Siimon 90 (1995) 109
Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
Atomic hydrogen-assisted ALE of germanium, S. Sugahara, M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura 90 (1995) 349
Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (*h*11)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Erbium

Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95

Etching

Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
Chemical etching of (100) and (110) faces of flux-grown $LaBO_3$ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65
Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422
Laser-induced etching and deposition of tungsten in WF_6–H_2 atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
Laser chemical etching of Cu_2O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaan and M. Prasad 86 (1995) 548
Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559
Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577

Etching of $CoSi_2$ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl_2 environment, P. Tejedor and P.S. Domínguez 89 (1995) 271
Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis 90 (1995) 39
Thermal etching of α-Zr single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy 90 (1995) 59
A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309

Evaporation

Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan 89 (1995) 159
Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
Cadmium selenide–amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
Interfacial reaction of NiO with Al_2O_3 $(11\bar{2}0)$ and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
The influence of the substrate material on the growth of V_2O_5 flash-evaporated films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov 90 (1995) 389

Field desorption

Investigation of adsorption and coadsorption of O_2 and CO on Rh by O_2^+ field ion and Li^+ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block 87/88 (1995) 159

Field effect

Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst 87/88 (1995) 45
Field-induced redistribution and diffusion of water on a Pt field emitter, R. Bryl, T. Wysocki and R. Błaszczyszyn 87/88 (1995) 69
Microstructured liquid metal ion and electron sources (MILMIS/MILMES), J. Mitterauer 87/88 (1995) 79
Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces, G.L. Kellogg 87/88 (1995) 353
Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study, M. Devel, C. Girard, C. Joachim and O.J.F. Martin 87/88 (1995) 390

Field electron microscopy

Surface structure dependence of O_2–W adsorption system, M. Sato 82/83 (1994) 532

Field emission

Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov 87/88 (1995) 24
A quantitative estimation of the sensitivity of field-emission pressure-gauge, T. Iwata and K.-S. Chang 87/88 (1995) 31
Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst 87/88 (1995) 45

Electron field emission (FE) from quantum size systems, L.G. Il'chenko, Yu.V. Kryuchenko and V.G. Litovchenko 87/88 (1995) 53
Modeling of the field emitter triode (FET) as a displacement/pressure sensor, D. Nicolaescu 87/88 (1995) 61
Microstructured liquid metal ion and electron sources (MILMIS/MILMES), J. Mitterauer 87/88 (1995) 79
Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151

Field emission microscopy

Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37
Development of a FEM, FIM-AP system for studying gridded vacuum microelectronic devices, M. Huang, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 421

Field evaporation

Field evaporation theory: a review of basic ideas, R.G. Forbes 87/88 (1995) 1
Field evaporation of gold by scanning tunneling microscopy, W. Mizutani, A. Ohi, M. Motomatsu and H. Tokumoto 87/88 (1995) 398

Field ion microscopy

Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst 87/88 (1995) 45
A FEM study of liquid lithium on a ⟨011⟩-oriented tungsten tip, K. Hata, M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita 87/88 (1995) 117
Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt, C. Voss and N. Kruse 87/88 (1995) 127
Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
FIM phenomena observed with benzene as image gas, B. Schulze, A. Theiss, U. Schmidt and F.W. Röllgen 87/88 (1995) 140
Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röllgen 87/88 (1995) 146
Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
APFIM investigations on ordered γ-TiAl using single-layer detection method, J. Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179
Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz 87/88 (1995) 194
Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
Atom probe field ion microscopy of type 308 CRE stainless steel welds, S.S. Babu, S.A. David, J.M. Vitek and M.K. Miller 87/88 (1995) 207
Characterization of neutron-irradiated Fe–Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
An APFIM/TEM investigation of the discontinuous precipitation in a Ni–In alloy, G.P. Geber 87/88 (1995) 234
Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
Effect of low-energy (20–40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin 87/88 (1995) 257
APFIM study of the compositional inhomogeneity of sputtered Co–Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambreland, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284

Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi 87/88 (1995) 291
FIM/AP analysis of Cu–Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329
Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces, G.L. Kellogg 87/88 (1995) 353
Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
Development of a FEM, FIM-AP system for studying gridded vacuum microelectronic devices, M. Huang, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 421
On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman 90 (1995) 95
Erratum to "Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107

Gallium

Activation of the $Ga–CH_3$ bond using atomic hydrogen – a possible route to III–V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276

Gallium arsenide

A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
Evaluation of matrix effects in SIMS quantification of $Al_xGa_{1-x}As/GaAs$ heterostructures: a SNMS approach, A. Torrisi, A. Scandurra and A. Licciardello 81 (1994) 259
Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
Ideal static induction transistor implemented with molecular layer epitaxy, P. Płotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
Flow modulation epitaxy of $Ga_xIn_{1-x}As/AlAs$ heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136

Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $Al_xGa_{1-x}As$ on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208
Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$ and AsH_3, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer expitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290
Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
Strain relaxation in GaAs islands on GaP(001), H. Yago, T. Nomura and K. Ishikawa 84 (1995) 119
Reactivity of III–V and II–VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter 84 (1995) 299
Defects and material processing in compound semiconductors, K. Wada 85 (1995) 246
Defect analysis using 2D-ACAR: GaAs as a test case, A.A. Manuel, R. Ambigapathy, K. Saarinen, P. Hautojärvi and C. Corbel 85 (1995) 301
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
Defects and arsenic distribution in low-temperature-grown GaAs, N. Hozhabri, A.R. Koymen, S.C. Sharma and K. Alavi 85 (1995) 311
Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N.

Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577
MBE-STM study of the Ga-rich 4 × 2 phase of the GaAs(001) surface, Q. Xue, T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai 87/88 (1995) 364
Structure of the MBE-grown GaAs(001)-(2 × 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai 87/88 (1995) 373
Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl_2 environment, P. Tejedor and P.S. Domínguez 89 (1995) 271
Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis 90 (1995) 39
A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309
Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (*h*11)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437

Gallium phosphide

Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
Strain relaxation in GaAs islands on GaP(001), H. Yago, T. Nomura and K. Ishikawa 84 (1995) 119
Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453

Germanium

Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
Photoreflectance of strained $Si_{1-x}Ge_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
Formation of poly-$Si_{1-x}Ge_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530

Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
Atomic hydrogen-assisted ALE of germanium, S. Sugahara, M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura 90 (1995) 349

Glass

XPS investigation of lithium borate glass and the Li/$LiBO_2$ interface, D.A. Hensley and S.H. Garofalini 81 (1994) 331
Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387

Gold

Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declemy and Ph. Goudeau 81 (1994) 119
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss 85 (1995) 77
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
Characterization of neutron-irradiated Fe–Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambreland, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
Field evaporation of gold by scanning tunneling microscopy, W. Mizutani, A. Ohi, M. Motomatsu and H. Tokumoto 87/88 (1995) 398
Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto 89 (1995) 131
Preparation of a model Ziegler–Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187

Graphite

Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers, M. Sreemany and T.B. Ghosh 90 (1995) 241

Hafnium

Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto 85 (1995) 329

Halides

LiBr on Si(111): an X-ray standing wave measurement, Th. Gog, G.C. Follis and S.M. Durbin 81 (1994) 485

Halogenides

Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$ and AsH_3, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228

Atomic-scale modification of the $AlCl_3$-adsorbed Si(111)-7×7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
$NbCl_5$ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
Preparation of a model Ziegler–Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
Influence of surface charge on thermal positive ion emission from potassium bromide, M.F. Butman, J. Nakamura, S. Kamidoi and H. Kawano 89 (1995) 323
Silicon surface cleaning using XeF_2 gas treatment, V.S. Aliev, M.R. Baklanov and V.I. Bukhtiyarov 90 (1995) 191

Halogens

The adsorption of sodium dodecyl sulphate on fluorite and its surface free energy, B. Jańczuk, M.L. González-Martín and J.M. Bruque 81 (1994) 95
Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577

Helium

Threshold behavior of ionization and excitation cross sections of He and Ar by positron impact, O. Sueoka, B. Jin and A. Hamada 85 (1995) 59
Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnarends and H. Schut 85 (1995) 271

Hydrides

Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$ and AsH_3, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo 89 (1995) 21

Hydrocarbons

A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
Chemisorption of poly(methylhydrogensiloxane) on oxide surfaces: a quantitative investigation using static SIMS, K. Reihs, R. Aguiar Colom, S. Gleditzsch, M. Deimel, B. Hagenhoff and A. Benninghoven 84 (1995) 107
FIM phenomena observed with benzene as image gas, B. Schulze, A. Theiss, U. Schmidt and F.W. Röllgen 87/88 (1995) 140
Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röllgen 87/88 (1995) 146
Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T.

Hashizume, H.W. Pickering and T. Sakurai 87/88 (1995) 380
An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection–absorption spectroscopy, S. Yoshida and H. Ishida 89 (1995) 39
Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137

Hydrogen

Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
Comment on 'Influence of surface composition on initial hydration of aluminium in boiling water' by A. Strålin and T. Hjertberg, B.R. Strohmeier 81 (1994) 273
The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
Activation of the Ga–CH_3 bond using atomic hydrogen – a possible route to III–V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
Isothermal H_2 desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
Reactivity of III–V and II–VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the CO + H_2 reaction over lanthanide-modified Rh/Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391
Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnarends and H. Schut 85 (1995) 271
VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt, C. Voss and N. Kruse 87/88 (1995) 127
Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
The distribution of activation energy for hydrogen desorption over silica-supported nickel catalysts determined from temperature-programmed desorption spectra, M. Arai, Y. Nishiyama, T. Masuda and K. Hashimoto 89 (1995) 11
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
Cadmium selenide–amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis 90 (1995) 39
Hydrogen adsorption induced phase transitions on Si(100)-c(8 × 8): temperature dependence studied by LEED, X. Hu and Z. Lin 90 (1995) 111
The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J.

Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
Atomic hydrogen-assisted ALE of germanium, S. Sugahara, M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura 90 (1995) 349
Surface interaction between H_2 and CO_2 over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah 90 (1995) 393

Indium

Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
Atypical characteristics of KrF excimer laser ablation of indium–tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
An APFIM/TEM investigation of the discontinuous precipitation in a Ni–In alloy, G.P. Geber 87/88 (1995) 234

Indium antimonide

Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136

Indium arsenide

Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223

Indium phosphide

Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells, H. Kobayashi, F. Mizuno and Y. Nakato 81 (1994) 399
Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
Flow modulation epitaxy of $Ga_xIn_{1-x}As$/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
Application of time-dependent diffusion models to the study of real solids, D.T. Britton and J. Störmer 85 (1995) 1
Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaan and M. Prasad 86 (1995) 548
Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
Interfacial reaction of Ag with the InP (100)4 × 2 surface – a photoemission study, H. Engelhard, F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann 90 (1995) 89
Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (*h*11)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
Morphology, atomic composition and photoelectric properties of the microrelief InP–electrolyte interface, N.L. Dmitruk,

E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets 90 (1995) 489

Infrared spectroscopy

FT-IR investigation of methane adsorption on silica, J. Wu, S. Li, G. Li, C. Li and Q. Xin 81 (1994) 37

Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83

Combined use of XPS, IR and EDAX techniques for the characterization of ZrO_2–SiO_2 powders prepared by a sol–gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325

In-situ FTIR investigation of coke formation on USY zeolite, C. Li, Y.-W. Chen, S.-J. Yang and R.-B. Yen 81 (1994) 465

Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171

Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460

Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548

Evidence for infrared absorption enhancement of species at the lithium metal/electrolytic solution interface, Y. Suzuki, K. Sagisaka and A. Hatta 84 (1995) 1

An FT-IR investigation of parabactin adsorbed onto aluminum, D.C. Hansen, E. McCafferty, C.W. Lins and J.J. Fitzpatrick 84 (1995) 85

A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145

A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227

In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the CO + H_2 reaction over lanthanide-modified Rh/Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391

Using the Lambert–Beer law for thickness evaluation of photoconductor coatings for recording holograms, A. Larena, G. Pinto and F. Millán 84 (1995) 407

Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1

Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170

UV photo-annealing of thin sol–gel films, R.E. Van de Leest 86 (1995) 278

Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294

Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii 86 (1995) 299

An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection–absorption spectroscopy, S. Yoshida and H. Ishida 89 (1995) 39

Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyaev and A.S. Medvedev 89 (1995) 49

Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77

M–S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151

The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori 89 (1995) 411

IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO_2 film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu 90 (1995) 29

Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149

A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid–base alternating Langmuir–Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown 90 (1995) 205

Surface interaction between H_2 and CO_2 over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah 90 (1995) 393

Interfaces

Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183

Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435

Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115

Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359

Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537

An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179

Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351

Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305

Atom probe analysis of interfacial segregation, M.K. Miller and G.D.W. Smith 87/88 (1995) 243

X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57

A study of the composition distribution at the Ti/Al_2O_3 interface using the MCs^+-SIMS technique, X. Chen and Y. Wang 89 (1995) 169

Ion bombardment

Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422

Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565

Initial oxidation kinetics of Fe–Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91

A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203

Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287

Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107

Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii 86 (1995) 299

Preferential sputtering of argon ion bombarded Ni_3Al and $TaSi_2$, S. Hofmann and M.G. Stepanova 90 (1995) 227

A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309

Ion implantation

Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama 85 (1995) 259

Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnarends and H. Schut 85 (1995) 271

Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364

Effect of low-energy (20–40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin 87/88 (1995) 257

A photoemission study of electron states in Sb-ion implanted TiO_2(110), A.E. Taverner, A. Gulino, R.G. Egdell and T.J. Tate 90 (1995) 383

Range profiles of 6–10 MeV ^{15}N ions implanted in silicon, T. Ahlgren, K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen 90 (1995) 419

Ion scattering

The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
$NbCl_5$ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
Structural study of $SrTiO_3$(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548
Deposition of inorganic salts from solution on flat substrates by spin-coating: theory, quantification and application to model catalysts, R.M. Van Hardeveld, P.L.J. Gunter, L.J. Van IJzendoorn, W. Wieldraaijer, E.W. Kuipers and J.W. Niemantsverdriet 84 (1995) 339
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama 85 (1995) 259
The laser ablation threshold of $YBa_2Cu_3O_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
Etching of $CoSi_2$ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
Interfacial reaction of NiO with Al_2O_3 ($11\bar{2}0$) and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and coadsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
Recovery and recrystallization of $SrTiO_3$ (100) surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita 90 (1995) 123
XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309

Iron

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
Initial oxidation kinetics of Fe–Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309

Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37
Characterization of neutron-irradiated Fe–Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
A study of the effect of ageing temperature on phase separation in Fe–45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
Comparison of low temperature decomposition in Fe–Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
Ultraviolet inverse photoemission study of the oxidation of YFe_2, P. Vavassori, L. Callegaro and E. Puppin 89 (1995) 93
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner 90 (1995) 65
Topological study of crack growth on iron crystal, M. Pingo, J. Vošta, J. Pancíř and I. Haslingerová 90 (1995) 373

Krypton

Installation of a Kr moderator in the high-brightness beam at Brandeis, D. Vasumathi, G. Amarendra, K.F. Canter and A.P. Mills, Jr. 85 (1995) 154

Langmuir–Blodgett structures

Structural investigation of Langmuir–Blodgett monolayers of L-α-dipalmitoylphosphatidylcholine by atomic force microscopy, X.-M. Yang, D. Xiao, Z.-H. Lu and Y. Wei 90 (1995) 175
A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid–base alternating Langmuir–Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown 90 (1995) 205

Lanthanides

Chemical etching of (100) and (110) faces of flux-grown $LaBO_3$ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65

Laser processing

Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
Growth of excimer-laser-induced dendritic surface structures on polyethyleneterephthalate, J. Heitz, E. Arenholz, D. Bäuerle and K. Schilcher 81 (1994) 103
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
Square-shaped temperature distribution induced by a Gaussian-shaped laser beam, Y.-F. Lu 81 (1994) 357
Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
Laser-induced decomposition of dimethyl cadmium on a quartz substrate, S.-P. Lee and M.C. Lin 84 (1995) 31
Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1
Overheated metastable states in polymer sublimation by laser radiation, V.I. Mazhukin, I. Smurov, C. Surry and G. Flamant 86 (1995) 7
The laser ablation threshold of $YBa_2Cu_3O_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
Pulsed laser ablation of copper, R. Jordan, D. Cole, J.G. Lunney, K. Mackay and D. Givord 86 (1995) 24

Why are high-T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm^2?, R.W. Dreyfus 86 (1995) 29

Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35

Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40

Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45

Characterisation of ionic species generated during ablation of $Bi_2Sr_2Ca_2Cu_3O_{10}$ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50

Laser wavelength dependence of $YBa_2Cu_3O_y$ laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehé 86 (1995) 59

Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64

Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68

Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74

Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79

Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86

Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90

Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95

Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99

Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114

Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122

SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128

SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134

Pulsed laser deposition and nanometer scale characterization of $YBa_2Cu_3O_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140

Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144

Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149

Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154

Pulsed laser deposition of $NbTe_x$ thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160

Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165

Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170

$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175

Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180

Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
Metal pattern deposition by laser-induced forward transfer, Z. Kántor, Z. Tóth and T. Szörényi 86 (1995) 196
New approach of a laser-induced forward transfer for deposition of patterned thin metal films, H. Esrom, J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza 86 (1995) 202
Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
Optodynamic aspect of a pulsed laser ablation process, R. Hrovatin and J. Možina 86 (1995) 213
Atypical characteristics of KrF excimer laser ablation of indium–tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228
Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239
Structuring of polyimide–metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
Combination of excimer laser micromachining and replication processes suited for large scale production, J. Arnold, U. Dasbach, W. Ehrfeld, K. Hesch and H. Löwe 86 (1995) 251
Laser–surface processing of metals and ceramics for industrial applications, H.W. Bergmann, K. Schutte, E. Schubert and A. Emmel 86 (1995) 259
Tailoring of surface properties by removal and deposition with laser radiation, E.W. Kreutz, H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging 86 (1995) 266
Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
Influence of temperature gradient to solidification velocity ratio on the structure transformation in pulsed- and CW-laser surface treatment, N.A. Berjeza, S.P. Velikevitch, V.I. Mazhukin, I. Smurov and G. Flamant 86 (1995) 303
Rapid prototyping with CO_2 laser radiation, E.W. Kreutz, G. Backes, A. Gasser and K. Wissenbach 86 (1995) 310
Microstructure, chemical composition and properties of the surface layer of M2 steel after laser melting under different conditions, J. Kusiński 86 (1995) 317
Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
Formation of poly-$Si_{1-x}Ge_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation, A.V. Demchuk and V.A. Labunov 86 (1995) 353
Theoretical and experimental studies of a-Si:H recrystallization by XeCl excimer laser irradiation, R. Černý, V. Vydra, P. Přikryl, I. Ulrych, J. Kočka, K.M.A. El-Kader, Z. Chvoj and V. Cháb 86 (1995) 359
Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter 86 (1995) 368
Formation of Ti^{3+} ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton 86 (1995) 382
Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
Laser-induced formation of porous silicon, V. Baranauskas, G.P. Thim and A. Peled 86 (1995) 398
Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
Thin films of polymer blends: surface treatment and theoretical modeling, P.

Viville, O. Thoelen, S. Beauvois, R. Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude 86 (1995) 411
Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422
Laser direct writing and instabilities: a one-dimensional approach, N. Arnold, P.B. Kargl and D. Bäuerle 86 (1995) 457
Laser chemical vapour deposition for microelectronics, G. Auvert 86 (1995) 466
Laser processing of tungsten from WF_6 and SiH_4, M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
Laser-induced etching and deposition of tungsten in WF_6–H_2 atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488
Kinetic model for scanning laser-induced deposition from the liquid phase, Zs. Geretovszky, L. Kelemen, K. Bali and T. Szörényi 86 (1995) 494
The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500
Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
Excimer laser-induced deposition of copper from Cu(hfac)(TMVS), R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530
Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538
Laser chemical etching of Cu_2O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaan and M. Prasad 86 (1995) 548
Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559
Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577
Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl_2 environment, P. Tejedor and P.S. Domínguez 89 (1995) 271
Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
Synthesis of molybdenum nitride γ-Mo_2N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
Laser-induced temperature rise in Gaussian-shaped holes, Y.F. Lu, T.E. Loh, H.G. Soh and T.S. Low 90 (1995) 217
Melting and diffusion under nanosecond laser pulse, W. Szyszko 90 (1995) 325

Lead

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
Surface analysis of commercial lead/acid battery grids, R. De Marco and J. Liesegang 84 (1995) 237
Time of flight mass spectrometry and covariance mapping technique investiga-

tion of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35
Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1
XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343

Low energy electron diffraction

Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
Structural study of $SrTiO_3$(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
Adsorption and co-adsorption of boron and oxygen on ordered α-SiC surfaces, V.M. Bermudez 84 (1995) 45
Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
The (0001)-surface of 6H-SiC: morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
Hydrogen adsorption induced phase transitions on Si(100)-c(8 × 8): temperature dependence studied by LEED, X. Hu and Z. Lin 90 (1995) 111

Luminescence

Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
Flow modulation epitaxy of $Ga_xIn_{1-x}As$/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
Electrical properties of Si–Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (*h*11)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437

Magnesium

Adsorption of CO on Mg-promoted Co(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289
Investigations of the interface between magnesium and polyethyleneterephthalate by

X-ray photoelectron spectroscopy, P.C. Wong, Y.S. Li and K.A.R. Mitchell 84 (1995) 245
Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
Preparation of a model Ziegler–Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187

Magnesium oxide

Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161
Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559
Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto 89 (1995) 131
Oxygen exchange between adsorbed NO and MgO surfaces, Y. Yanagisawa 89 (1995) 251

Magnetic properties

Atom probe studies of nanostructured alloys, K. Hono and T. Sakurai 87/88 (1995) 166

Manganese

Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
XPS studies of the effect of Mn on Pd/Al_2O_3, P.C. L'Argentière, M.G. Cañón and N.S. Fígoli 89 (1995) 63

Mass spectroscopy

Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
Activation of the Ga–CH_3 bond using atomic hydrogen – a possible route to III–V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry, D.L. Cocke, G.K. Chuah, N. Kruse and J.H. Block 84 (1995) 153
Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35
Characterisation of ionic species generated during ablation of $Bi_2Sr_2Ca_2Cu_3O_{10}$ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
Surface reactions on palladium hydride in vacuum, air and water studied in situ

with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo 89 (1995) 21
The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Mercury telluride

A positron annihilation study of the formation of defect layers in cadmium mercury telluride, A. Towner, P.C. Rice-Evans and N. Shaw 85 (1995) 315

Metals

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559
Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351
Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79
Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
Metal pattern deposition by laser-induced forward transfer, Z. Kántor, Z. Tóth and T. Szörényi 86 (1995) 196
New approach of a laser-induced forward transfer for deposition of patterned thin metal films, H. Esrom, J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza 86 (1995) 202
Structuring of polyimide–metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
Laser–surface processing of metals and ceramics for industrial applications, H.W. Bergmann, K. Schutte, E. Schubert and A. Emmel 86 (1995) 259
Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces, G.L. Kellogg 87/88 (1995) 353

Methane

FT-IR investigation of methane adsorption on silica, J. Wu, S. Li, G. Li, C. Li and Q. Xin 81 (1994) 37
Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211

Methanol

Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface, W.M.K.P. Wijekoon, E.W. Koenig, W.M. Hetherington III and W.R. Salzman 81 (1994) 347

Mica

An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155

Molecular dynamics

Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E.

Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543
Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559

Molybdenum

A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500
The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels, R.C. Thomson and M.K. Miller 87/88 (1995) 185
Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi 87/88 (1995) 291
Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121
M–S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
Synthesis of molybdenum nitride γ-Mo_2N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81

Monte Carlo simulations

A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $Al_xGa_{1-x}As$ on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208
Development of a new Monte Carlo simulation system on positron behavior in matter, S. Okada and H. Kaneko 85 (1995) 149
Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh 85 (1995) 187

Mössbauer spectroscopy

Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90

Multilayers

Preparation and characterization of self-assembly organic multilayer films on silica surface, X.Q. Zhang, W.Y. Yang, X.Z. You and Y. Wei 84 (1995) 267
Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh 85 (1995) 187
Defect profiling in multilayered systems using mean depth scaling, G.C. Aers, P.A. Marshall, T.C. Leung and R.D. Goldberg 85 (1995) 196
Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles, V.J. Ghosh, B. Nielsen, K.G. Lynn and D.O. Welch 85 (1995) 210
Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto 85 (1995) 329
Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79
Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
FIM/AP analysis of Cu–Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329

Nickel

Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
Initial oxidation kinetics of Fe–Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
A comparative study of the interaction of oxygen with clusters and single-crystal

surfaces of nickel, C.N.R. Rao, V. Vijayakrishnan, G.U. Kulkarni and M.K. Rajumon 84 (1995) 285
Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto 85 (1995) 329
Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
An APFIM/TEM investigation of the discontinuous precipitation in a Ni–In alloy, G.P. Geber 87/88 (1995) 234
Structure and chemistry of grain boundaries in Ni–16Cr–9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi 87/88 (1995) 291
A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
Interfacial reaction of NiO with Al_2O_3 $(11\bar{2}0)$ and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
Observation of field-induced fragmentation of nickel clusters using Scanning Tunneling Microscopy, M.V.H. Rao, V. Srinivas, V.V. Rao, B.K. Mathur and K.L. Chopra 89 (1995) 417
Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman 90 (1995) 95

Niobium

Surface enrichment of niobium on Inconel 718 (100) single crystals, D.J. Dwyer, X.J. Pang, M. Gao and R.P. Wei 81 (1994) 229
Surface fractal dimension of sintered porous solid niobium, L.I. Skatkov, V.V. Konotop, P.G. Cheremskoy, V.P. Gomozov and B.I. Bayrachny 81 (1994) 427
$NbCl_5$ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
Pulsed laser deposition of $NbTe_x$ thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160

Niobium oxide

Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144

Nitric oxide

Ultrathin SiO_2 films on Si formed by N_2O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt, C. Voss and N. Kruse 87/88 (1995) 127
Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
Oxygen exchange between adsorbed NO and MgO surfaces, Y. Yanagisawa 89 (1995) 251
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and coadsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15

Nitrides

Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55

Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28

Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373

Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325

Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68

Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121

Synthesis of molybdenum nitride γ-Mo_2N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81

Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas 90 (1995) 455

Nitrogen

SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem 81 (1994) 127

A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203

Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357

The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori 89 (1995) 411

Range profiles of 6–10 MeV ^{15}N ions implanted in silicon, T. Ahlgren, K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen 90 (1995) 419

Noble gases

Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401

Nuclear magnetic resonance

Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83

A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145

Nuclear reaction analysis

XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261

Nucleation

Nucleation and island growth during water adsorption at sub-monolayer coverages, R.V. Kasza, K. Griffiths, V.P. Zhdanov and P.R. Norton 84 (1994) 97

Optical properties

A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175

Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76

Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109

Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using $GaCl_3$, $AlCl_3$

and AsH_3, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
Preparation and characterization of self-assembly organic multilayer films on silica surface, X.Q. Zhang, W.Y. Yang, X.Z. You and Y. Wei 84 (1995) 267
Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1
Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114
Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122
Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
Oligonucleotide hybridization observed by surface plasmon optical techniques, D. Piscevic, R. Lawall, M. Veith, M. Liley, Y. Okahata and W. Knoll 90 (1995) 425

Organic substances

Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
Preparation and characterization of self-assembly organic multilayer films on silica surface, X.Q. Zhang, W.Y. Yang, X.Z. You and Y. Wei 84 (1995) 267
Structural investigation of Langmuir–Blodgett monolayers of L-α-dipalmitoylphosphatidylcholine by atomic force microscopy, X.-M. Yang, D. Xiao, Z.-H. Lu and Y. Wei 90 (1995) 175
XPS investigation of electron beam effects on a trimethylsilane dosed Si(100) surface, P.W. Wang, S. Bater, L.P. Zhang, M. Ascherl and J.H. Craig, Jr. 90 (1995) 413

Organometallic vapour deposition

Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548
Electrical properties of Si–Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583

Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
Synthesis of conducting oxides by ML-ALE, V.E. Drozd and V.B. Aleskovski 82/83 (1994) 591
Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75

Oxidation

Electron-beam-induced oxidation of CdS, V.B. Mityukhlyaev 81 (1994) 137
The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
Initial oxidation kinetics of Fe–Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry, D.L. Cocke, G.K. Chuah, N. Kruse and J.H. Block 84 (1995) 153
APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
Ultraviolet inverse photoemission study of the oxidation of YFe_2, P. Vavassori, L. Callegaro and E. Puppin 89 (1995) 93
Enhanced silicon oxidation in O_2 and O_2:F_2, G.F. Cerofolini, G. La Bruna and L. Meda 89 (1995) 361
A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin 89 (1995) 401

Oxides

Identification of active species and theoretical classification of simple catalyst oxides using surface redox couples, Y.P. Arnaud and H. Bertrais 81 (1994) 69
A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
A study of $CaO–SO_2$ interaction, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 409
A study of $CaO–SO_2$ interaction in the presence of O_2, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
Structural study of $SrTiO_3$(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
Synthesis of conducting oxides by ML-ALE, V.E. Drozd and V.B. Aleskovski 82/83 (1994) 591
Chemisorption of poly(methylhydrogensiloxane) on oxide surfaces: a quantitative investigation using static SIMS, K. Reihs, R. Aguiar Colom, S. Gleditzsch, M. Deimel, B. Hagenhoff and A. Benninghoven 84 (1995) 107
AES and XPS study of thin RF-sputtered Ta_2O_5 layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R.

Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35
Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114
The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500
Laser chemical etching of Cu_2O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
A new parameter to characterize limestones as SO_2 sorbents, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 89 (1995) 197
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
Interfacial reaction of NiO with Al_2O_3 $(11\bar{2}0)$ and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
Recovery and recrystallization of $SrTiO_3$(100) surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita 90 (1995) 123
XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy 90 (1995) 447
Characterization of RuO_2 thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong 90 (1995) 497

Oxygen

Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
A study of CaO–SO_2 interaction in the presence of O_2, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
Surface structure dependence of O_2–W adsorption system, M. Sato 82/83 (1994) 532
Adsorption and co-adsorption of boron and oxygen on ordered α-SiC surfaces, V.M. Bermudez 84 (1995) 45
A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
A comparative study of the interaction of oxygen with clusters and single-crystal surfaces of nickel, C.N.R. Rao, V. Vijayakrishnan, G.U. Kulkarni and M.K. Rajumon 84 (1995) 285
Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss 85 (1995) 77
The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500
Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
Investigation of adsorption and coadsorption of O_2 and CO on Rh by O_2^+ field ion and Li^+ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block 87/88 (1995) 159

Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375
The reactivity of O_2/H_2, O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343

Palladium

Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
FIM/AP analysis of Cu–Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329
Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo 89 (1995) 21
XPS studies of the effect of Mn on Pd/Al_2O_3, P.C. L'Argentière, M.G. Cañón and N.S. Fígoli 89 (1995) 63
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
Surface segregation and core-level shift of a Pd–Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515

Phase transitions

In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223
Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
Effect of low-energy (20–40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin 87/88 (1995) 257
Hydrogen adsorption induced phase transitions on Si(100)-c(8 × 8): temperature dependence studied by LEED, X. Hu and Z. Lin 90 (1995) 111

Phosphorus

The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383

Photochemistry

Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
Laser-induced decomposition of dimethyl cadmium on a quartz substrate, S.-P. Lee and M.C. Lin 84 (1995) 31
Tailoring of surface properties by removal and deposition with laser radiation, E.W. Kreutz, H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging 86 (1995) 266
Aggregation kinetics of photo-excited colloid solutions observed by dynamic photon correlation spectroscopy (PCS), N. Borochov and A. Peled 86 (1995) 533
IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO_2 film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu 90 (1995) 29

Photoelectron spectroscopy

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11

Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
Surface enrichment of niobium on Inconel 718 (100) single crystals, D.J. Dwyer, X.J. Pang, M. Gao and R.P. Wei 81 (1994) 229
Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
Ultrathin SiO_2 films on Si formed by N_2O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
Adsorption of CO on Mg-promoted Co(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289
XPS study of an intumescent coating. Application to the ammonium polyphosphate/pentaerythritol fire-retardant system, S. Bourbigot, M. Le Bras, L. Gengembre and R. Delobel 81 (1994) 299
Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
Combined use of XPS, IR and EDAX techniques for the characterization of ZrO_2–SiO_2 powders prepared by a sol–gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325
XPS investigation of lithium borate glass and the Li/$LiBO_2$ interface, D.A. Hensley and S.H. Garofalini 81 (1994) 331
The effect of cyclic oxidation–reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
On the XPS peak shape analysis, M. Sreemany and T.B. Ghosh 81 (1994) 365
Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans 81 (1994) 449
Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587

A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants, J.A. Schreifels, N.H. Turner and R.E. Morris 84 (1995) 23
Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145
An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
Reactivity of III–V and II–VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
AES and XPS study of thin RF-sputtered Ta_2O_5 layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
Surface analysis of commercial lead/acid battery grids, R. De Marco and J. Liesegang 84 (1995) 237
Investigations of the interface between magnesium and polyethyleneterephthalate by X-ray photoelectron spectroscopy, P.C. Wong, Y.S. Li and K.A.R. Mitchell 84 (1995) 245
A comparative study of the interaction of oxygen with clusters and single-crystal surfaces of nickel, C.N.R. Rao, V. Vijayakrishnan, G.U. Kulkarni and M.K. Rajumon 84 (1995) 285
Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
Defects and arsenic distribution in low-temperature-grown GaAs, N. Hozhabri, A.R. Koymen, S.C. Sharma and K. Alavi 85 (1995) 311
Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
Formation of Ti^{3+} ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton 86 (1995) 382
Excimer laser-induced deposition of copper from Cu(hfac)(TMVS), R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538
Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577
APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyaev and A.S. Medvedev 89 (1995) 49
X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57
XPS studies of the effect of Mn on Pd/Al_2O_3, P.C. L'Argentière, M.G. Cañón and N.S. Fígoli 89 (1995) 63
Thickness determination of uniform overlayers on rough substrates by angle-dependent XPS, P.L.J. Gunter and J.W. Niemantsverdriet 89 (1995) 69
Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment, P. Gröning, O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlapbach 89 (1995) 83
Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
Elemental binding energies for X-ray photoelectron spectroscopy, C.J. Powell 89 (1995) 141
M–S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229
XPS investigations of the interactions of hydrogen with thin films of zirconium

oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}Cs^+$ beam, H. Tomizuka and A. Ayame 89 (1995) 281
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375
Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann 89 (1995) 383
Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin 89 (1995) 401
Reactivity assay of surface carboxyl chain-ends of poly(ethylene terephthalate) (PET) film and track-etched microporous membranes using fluorine labelled- and/or ^{3}H-labelled derivatization reagents: tandem analysis by X-ray photoelectron spectroscopy (XPS) and liquid scintillation counting (LSC), M. Deldime, J.-L. Dewez, Y.-J. Schneider and J. Marchand-Brynaert 90 (1995) 1
Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner 90 (1995) 65
Interfacial reaction of Ag with the InP (100)4 × 2 surface – a photoemission study, H. Engelhard, F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann 90 (1995) 89
Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129
Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155
Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guczi 90 (1995) 165
Determining hybridization differences for amorphous carbon from the XPS C 1s envelope, S.T. Jackson and R.G. Nuzzo 90 (1995) 195
Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers, M. Sreemany and T.B. Ghosh 90 (1995) 241
XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271
Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy, S. Kennou, S. Ladas, E.C. Paloura and J.A. Kalomiros 90 (1995) 283
Surface segregation of Sb in doped TiO_2 rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdell 90 (1995) 289
In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309

Peak fitting of the chromium 2p XPS spectrum, A.M. Salvi, J.E. Castle, J.F. Watts and E. Desimoni 90 (1995) 333
XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343
Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces, M. Keil, J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw 90 (1995) 377
A photoemission study of electron states in Sb-ion implanted TiO_2(110), A.E. Taverner, A. Gulino, R.G. Egdell and T.J. Tate 90 (1995) 383
An XPS study of the optimum loading of barium on high-silica MFI zeolite, M.H. Mohamed, M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui 90 (1995) 409
XPS investigation of electron beam effects on a trimethylsilane dosed Si(100) surface, P.W. Wang, S. Bater, L.P. Zhang, M. Ascherl and J.H. Craig, Jr. 90 (1995) 413
AFM and XPS characterization of the Si(111) surface after thermal treatment, B. Lamontagne, D. Guay, D. Roy, R. Sporken and R. Caudano 90 (1995) 481
Surface segregation and core-level shift of a Pd–Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515

Photoemission

Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
Ultraviolet inverse photoemission study of the oxidation of YFe_2, P. Vavassori, L. Callegaro and E. Puppin 89 (1995) 93
Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guczi 90 (1995) 165

Photon emission

Light emission from polymers under positron and electron bombardment, J. Xu, L.D. Hulett, Jr., T.A. Lewis and N.H. Tolk 85 (1995) 49

Plasma processing

Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
Ultrathin SiO_2 films on Si formed by N_2O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357
Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyaev and A.S. Medvedev 89 (1995) 49
Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment, P. Gröning, O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlapbach 89 (1995) 83
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
Cadmium selenide–amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori 89 (1995) 411
Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155
In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297

Platinum

Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells, H. Kobayashi, F. Mizuno and Y. Nakato 81 (1994) 399

Field-induced redistribution and diffusion of water on a Pt field emitter, R. Bryl, T. Wysocki and R. Błaszczyszyn 87/88 (1995) 69
Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt, C. Voss and N. Kruse 87/88 (1995) 127
Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guczi 90 (1995) 165
Surface interaction between H_2 and CO_2 over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah 90 (1995) 393

Polymers

Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
Growth of excimer-laser-induced dendritic surface structures on polyethyleneterephthalate, J. Heitz, E. Arenholz, D. Bäuerle and K. Schilcher 81 (1994) 103
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
XPS study of an intumescent coating. Application to the ammonium polyphosphate/pentaerythritol fire-retardant system, S. Bourbigot, M. Le Bras, L. Gengembre and R. Delobel 81 (1994) 299
Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation, Ch. Grégoire, J.-J. Pireaux, A. Cros and R. Caudano 84 (1995) 163
A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227
Investigations of the interface between magnesium and polyethyleneterephthalate by X-ray photoelectron spectroscopy, P.C. Wong, Y.S. Li and K.A.R. Mitchell 84 (1995) 245
Sample charging during static SIMS studies of polymers, G.J. Leggett and J.C. Vickerman 84 (1995) 253
AFM investigations of the initial stages of prepolymer film growth on aluminium, T. Gesang, R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann 84 (1995) 273
Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351
Using the Lambert–Beer law for thickness evaluation of photoconductor coatings for recording holograms, A. Larena, G. Pinto and F. Millán 84 (1995) 407
Light emission from polymers under positron and electron bombardment, J. Xu, L.D. Hulett, Jr., T.A. Lewis and N.H. Tolk 85 (1995) 49
Assay of weathering effects on protective polymer coatings using positron annihilation spectroscopy, L.D. Hulett, Jr., S. Wallace, J. Xu, B. Nielsen, Cs. Szeles, K.G. Lynn, J. Pfau and A. Schaub 85 (1995) 334
Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1
Overheated metastable states in polymer sublimation by laser radiation, V.I. Mazhukin, I. Smurov, C. Surry and G. Flamant 86 (1995) 7
Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239
Structuring of polyimide–metal carbide layer systems by excimer laser ablation,

J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
Thin films of polymer blends: surface treatment and theoretical modeling, P. Viville, O. Thoelen, S. Beauvois, R. Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude 86 (1995) 411
Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röllgen 87/88 (1995) 146
An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection–absorption spectroscopy, S. Yoshida and H. Ishida 89 (1995) 39
Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment, P. Gröning, O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlapbach 89 (1995) 83
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
Characterization of triplex RNA poly[rU]·poly[rA]·poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy, Y. Fang, C. Bai, T. Wang and Y.-Q. Tang 89 (1995) 331
Reactivity assay of surface carboxyl chain-ends of poly(ethylene terephthalate) (PET) film and track-etched microporous membranes using fluorine labelled- and/or ^{3}H-labelled derivatization reagents: tandem analysis by X-ray photoelectron spectroscopy (XPS) and liquid scintillation counting (LSC), M. Deldime, J.-L. Dewez, Y.-J. Schneider and J. Marchand-Brynaert 90 (1995) 1
Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces, M. Keil, J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw 90 (1995) 377

Positron beams

Positron diffusion in solids and in liquid metals, A. Seeger 85 (1995) 8
Design and simulation of the PSI electrostatic positron beam, D. Gerola, W.B. Waeber and M. Shi 85 (1995) 106
A gated positron beam incorporating a scattering cell and novel ion extractor, J. Moxom, G. Laricchia and M. Charlton 85 (1995) 118
Production of an intense slow positron beam by using an electron LINAC and its applications, I. Kanazawa, Y. Ito, M. Hirose, H. Abe, O. Sueoka, S. Takamura, A. Ichimiya, Y. Murata, F. Komori, K. Fukutani, S. Okada and T. Hattori 85 (1995) 124
A several tens-keV monoenergetic positron surface analyzer with ^{22}Na and electrostatic fields, M. Nunogaki, T. Yamamoto, Y. Honda and T. Okada 85 (1995) 132
Construction and performance of a slow positron beam guided by an increasing magnetic field, Y. Shirai, H. Miura and M. Yamaguchi 85 (1995) 138
Magnetic positron optics, D.T. Britton, K. Uhlmann and G. Kögel 85 (1995) 158

Positron diffraction

Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions , M. Kato and A. Ishii 85 (1995) 69

Positron microscopy

Development of a reflection geometry positron reemission microscope, A. Goodyear and P.G. Coleman 85 (1995) 98

Positron scattering

Total cross-section measurements for positrons and electrons colliding with

molecules: CCl_4, A. Hamada and O. Sueoka 85 (1995) 64
Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions , M. Kato and A. Ishii 85 (1995) 69
Development of a new Monte Carlo simulation system on positron behavior in matter, S. Okada and H. Kaneko 85 (1995) 149

Positron spectroscopy

Application of time-dependent diffusion models to the study of real solids, D.T. Britton and J. Störmer 85 (1995) 1
Annihilation of incompletely thermalized positronium studied by age–momentum correlation, H. Stoll, M. Koch, U. Lauff, K. Maier, J. Major, H. Schneider, A. Seeger and A. Siegle 85 (1995) 17
Theoretical study of the positron surface state at an alkali-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler and A.H. Weiss 85 (1995) 22
Study of positron surface states on the alkali-metal-covered transition-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss 85 (1995) 26
Energy loss measurements for 20 keV positrons in Al thin films, G.R. Massoumi, W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson 85 (1995) 39
Work function and epithermal positron emission from copper, N. Overton, A.P. Knights, A. Goodyear and P.G. Coleman 85 (1995) 54
Method for the measurement of positron affinities and positron work functions suitable for both positive and negative work function materials, A.H. Weiss, S. Yang, H.Q. Zhou, E. Jung, A.R. Koymen, S. Naidu, G. Brauer and M.J. Puska 85 (1995) 82
Generation of an intense pulsed positron beam for positron lifetime and TOF experiments, R. Suzuki, T. Mikado, M. Chiwaki, H. Ohgaki and T. Yamazaki 85 (1995) 87
Production of an intense slow positron beam using a compact cyclotron, M. Hirose, M. Washio and K. Takahashi 85 (1995) 111
Slow positron beam extraction from high magnetic fields, M. Shi, D. Gerola, W.B. Waeber and U. Zimmermann 85 (1995) 143
Installation of a Kr moderator in the high-brightness beam at Brandeis, D. Vasumathi, G. Amarendra, K.F. Canter and A.P. Mills, Jr. 85 (1995) 154
Slow positron production using the RIKEN AVF cyclotron, Y. Itoh, K.H. Lee, T. Nakajyo, A. Goto, N. Nakanishi, M. Kase, I. Kanazawa, Y. Yamamoto, N. Oshima and Y. Ito 85 (1995) 165
Positron Doppler broadening measurements with a LINAC-based slow positron beam, D. Segers, J. Paridaens, T. Van Hoecke, C. Dauwe, L. Dorikens-Vanpraet, C. Quaeyhaegens and L.M. Stals 85 (1995) 172
An overview of the slow-positron beam facility at the photon factory, KEK, T. Kurihara, A. Shirakawa, A. Enomoto, T. Shidara, H. Kobayashi and K. Nakahara 85 (1995) 178
Deconvolution of Doppler-broadened positron annihilation lineshapes by the generalised least-squares method, B.K. Panda, S. Fleischer, C.C. Ling, C.D. Beling, S. Fung and S. Panda 85 (1995) 182
Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh 85 (1995) 187
Defect profiling in multilayered systems using mean depth scaling, G.C. Aers, P.A. Marshall, T.C. Leung and R.D. Goldberg 85 (1995) 196
Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles, V.J. Ghosh, B. Nielsen, K.G. Lynn and D.O. Welch 85 (1995) 210
VEPFIT applied to depth profiling problems, A. van Veen, H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. IJpma 85 (1995) 216
Extension of the PC version of VEPFIT with input and output routines running under Windows, H. Schut and A. van Veen 85 (1995) 225
Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito 85 (1995) 229
Defects in Czochralski-grown silicon crystals investigated by positron annihilation, A. Ikari 85 (1995) 253
Variable-energy positron beam study of arsenic diffusion in poly-silicon, D.W. Lawther, R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver 85 (1995) 265
Slow positron implantation spectroscopy of edge-defined film-fed growth silicon, P.G. Coleman, E. Bloss, S. Setzler, S. LaShell, G. Davies and W.D. Sawyer 85 (1995) 276
An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime tech-

nique , A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino 85 (1995) 280
Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287
Measurement of oxide thickness using a variable-energy positron beam, T.C. Leung, P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz 85 (1995) 292
Positron annihilation studies of defects in molecular beam epitaxy grown III–V layers, M.T. Umlor, P. Asoka-Kumar, D.J. Keeble, P.W. Cooke and K.G. Lynn 85 (1995) 295
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
Defects and arsenic distribution in low-temperature-grown GaAs, N. Hozhabri, A.R. Koymen, S.C. Sharma and K. Alavi 85 (1995) 311
A positron annihilation study of the formation of defect layers in cadmium mercury telluride, A. Towner, P.C. Rice-Evans and N. Shaw 85 (1995) 315
Positron beam spectroscopy for the assessment of the structure and defect density of titanium nitride, P.C. Rice-Evans, A.S. Saleh and S.J. Bull 85 (1995) 320
Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325
Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto 85 (1995) 329
Assay of weathering effects on protective polymer coatings using positron annihilation spectroscopy, L.D. Hulett, Jr., S. Wallace, J. Xu, B. Nielsen, Cs. Szeles, K.G. Lynn, J. Pfau and A. Schaub 85 (1995) 334
Contrast in positron reemission microscopy due to positron trapping by dislocations, K.F. Canter, G. Amarendra, D. Vasumathi, S.A. Wesley, R. Xie, A.P. Mills, Jr., R.L. Sabatini and Y. Zhu 85 (1995) 339

Quantum effects

Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
Electron field emission (FE) from quantum size systems, L.G. Il'chenko, Yu.V. Kryuchenko and V.G. Litovchenko 87/88 (1995) 53

Quartz

Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387

Radiation damage

Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito 85 (1995) 229
An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique , A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino 85 (1995) 280
Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287
Characterization of neutron-irradiated Fe–Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis 90 (1995) 39

Raman scattering

A Raman microprobe study of the electrochromic and photochromic thin films

of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface, W.M.K.P. Wijekoon, E.W. Koenig, W.M. Hetherington III and W.R. Salzman 81 (1994) 347
Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351
Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
Formation of poly-$Si_{1-x}Ge_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
Characterization of triplex RNA poly[rU]·poly[rA]·poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy, Y. Fang, C. Bai, T. Wang and Y.-Q. Tang 89 (1995) 331
The influence of the substrate material on the growth of V_2O_5 flash-evaporated films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov 90 (1995) 389
Characterization of RuO_2 thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong 90 (1995) 497

Rhenium

Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185

Rhodium

Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the CO + H_2 reaction over lanthanide-modified Rh/Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391
Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
Investigation of adsorption and coadsorption of O_2 and CO on Rh by O_2^+ field ion and Li^+ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block 87/88 (1995) 159
Surface segregation and core-level shift of a Pd–Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515

Ruthenium

Characterization of RuO_2 thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong 90 (1995) 497

Scanning tunneling microscopy

STM-stimulated modification of solids: a quantum chemical study, V.S. Gurin and A.B. Kovrikov 81 (1994) 43
Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
Atomic-scale modification of the $AlCl_3$-adsorbed Si(111)-7 × 7 surface, T.

Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
Scanning tunneling microscope observations of Si(111)3 × 1-Ag and 6 × 1-Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444
Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
Reply to the "Comment of A.N. Buckley and R. Woods on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart", J. Ralston 84 (1995) 225
Pulsed laser deposition and nanometer scale characterization of $YBa_2Cu_3O_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter 86 (1995) 368
Scanning tunneling microscopy study of the (3 × 1) reconstruction induced by Li adsorption on the Si(111) surface, R.Z. Bakhtizin, C. Park, T. Hashizume and T. Sakurai 87/88 (1995) 347
MBE-STM study of the Ga-rich 4 × 2 phase of the GaAs(001) surface, Q. Xue, T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai 87/88 (1995) 364
Simulations of rectification in a laser-illuminated scanning tunneling microscope, M.J. Hagmann 87/88 (1995) 368
Structure of the MBE-grown GaAs(001)-(2 × 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai 87/88 (1995) 373
Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai 87/88 (1995) 380
MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study, M. Devel, C. Girard, C. Joachim and O.J.F. Martin 87/88 (1995) 390
Field evaporation of gold by scanning tunneling microscopy, W. Mizutani, A. Ohi, M. Motomatsu and H. Tokumoto 87/88 (1995) 398
Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
The (0001)-surface of 6H-SiC: morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175
Characterization of triplex RNA poly[rU]·poly[rA]·poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy, Y. Fang, C. Bai, T. Wang and Y.-Q. Tang 89 (1995) 331
Observation of field-induced fragmentation of nickel clusters using Scanning Tunneling Microscopy, M.V.H. Rao, V. Srinivas, V.V. Rao, B.K. Mathur and K.L. Chopra 89 (1995) 417
In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces, M. Keil, J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw 90 (1995) 377

Schottky barrier

Are modulations of the Schottky surface barrier the only explanation for the gas-sensing effects in sintered SnO_2?, R. Ionescu, C. Moise and A. Vancu 84 (1995) 291
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
Capacitance–voltage characteristics of Schottky barrier diode in the presence of deep-level impurities and series resistance, P. Chattopadhyay and S. Sanyal 89 (1995) 205

Secondary ion mass spectrometry

SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem 81 (1994) 127
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
Evaluation of matrix effects in SIMS quantification of $Al_xGa_{1-x}As/GaAs$ heterostructures: a SNMS approach, A.

Torrisi, A. Scandurra and A. Licciardello 81 (1994) 259
Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans 81 (1994) 449
Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
Chemisorption of poly(methylhydrogensiloxane) on oxide surfaces: a quantitative investigation using static SIMS, K. Reihs, R. Aguiar Colom, S. Gleditzsch, M. Deimel, B. Hagenhoff and A. Benninghoven 84 (1995) 107
A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227
Sample charging during static SIMS studies of polymers, G.J. Leggett and J.C. Vickerman 84 (1995) 253
Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413
Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1
A study of the composition distribution at the Ti/Al_2O_3 interface using the MCs^+-SIMS technique, X. Chen and Y. Wang 89 (1995) 169
A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}Cs^+$ beam, H. Tomizuka and A. Ayame 89 (1995) 281
A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid–base alternating Langmuir–Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown 90 (1995) 205
In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy 90 (1995) 447
Determination of the spatial distribution of trace elements in stainless steel by imaging microprobe secondary ion mass spectrometry, G.N. Salaita 90 (1995) 465

Selenium

Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316

Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Semiconductors

Activation of the Ga–CH_3 bond using atomic hydrogen – a possible route to III–V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
Reactivity of III–V and II–VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
Photoassisted growth of II–VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
In-situ laser reflectometry of the epitaxial growth of thin semiconductor films, T. Farrell and J.V. Armstrong 86 (1995) 582
Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12

Silane

Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
Isothermal H_2 desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145

Silicides

Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
Etching of $CoSi_2$ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner 90 (1995) 65

Silicon

An AES study of intrinsic and ion-induced structure in the SiO_2–Si system, B. Lang, B. Sefsaf and G. Allan 81 (1994) 17
Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans 81 (1994) 449
Photoreflectance of strained $Si_{1-x}Ge_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by

metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
Sub-atomic-layer epitaxy of Si using Si_2H_6, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
Self-limiting adsorption of thermally cracked $SiCl_2H_2$ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
Boron δ-doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
Isothermal H_2 desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
Atomic-scale modification of the $AlCl_3$-adsorbed Si(111)-7 × 7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
Chemical reactivity of the Si(111)$(\sqrt{3} \times \sqrt{3})$R30°-B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima 82/83 (1994) 434
Adsorption and desorption of H_2O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
Scanning tunneling microscope observations of Si(111)3 × 1-Ag and 6 × 1-Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444
Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1, M. Suemitsu, H. Nakazawa and N. Miyamoto 82/83 (1994) 449
Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
Electrical properties of Si–Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145
An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
Laser-induced selective deposition of Ni–P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383

Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413

Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss 85 (1995) 77

Covalency, elasticity and electron correlation in Si vacancies, A. Oshiyama, M. Saito and O. Sugino 85 (1995) 239

Defects in Czochralski-grown silicon crystals investigated by positron annihilation, A. Ikari 85 (1995) 253

Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen) , K. Kajiyama 85 (1995) 259

Variable-energy positron beam study of arsenic diffusion in poly-silicon, D.W. Lawther, R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver 85 (1995) 265

Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnarends and H. Schut 85 (1995) 271

Slow positron implantation spectroscopy of edge-defined film-fed growth silicon, P.G. Coleman, E. Bloss, S. Setzler, S. LaShell, G. Davies and W.D. Sawyer 85 (1995) 276

An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique , A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino 85 (1995) 280

Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287

Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95

$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175

Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208

Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics, J. Flicstein, Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe 86 (1995) 286

Thermodynamics and kinetics of solidification of Si–As solutions, R. Reitano 86 (1995) 323

Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338

Formation of poly-$Si_{1-x}Ge_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346

Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation, A.V. Demchuk and V.A. Labunov 86 (1995) 353

Theoretical and experimental studies of a-Si:H recrystallization by XeCl excimer laser irradiation, R. Černý, V. Vydra, P. Pfikryl, I. Ulrych, J. Kočka, K.M.A. El-Kader, Z. Chvoj and V. Cháb 86 (1995) 359

Laser-induced formation of porous silicon, V. Baranauskas, G.P. Thim and A. Peled 86 (1995) 398

Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422

Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453

Laser processing of tungsten from WF_6 and SiH_4, M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475

Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488

Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514

VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521

Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559

Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564

Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568

P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhirnov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov 87/88 (1995) 24
Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
Scanning tunneling microscopy study of the (3 × 1) reconstruction induced by Li adsorption on the Si(111) surface, R.Z. Bakhtizin, C. Park, T. Hashizume and T. Sakurai 87/88 (1995) 347
Thermal desorption spectroscopy study of chemically etched porous silicon, N. Hadj Zoubir and M. Vergnat 89 (1995) 35
X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57
A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}Cs^+$ beam, H. Tomizuka and A. Ayame 89 (1995) 281
Cadmium selenide–amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
Chemistry at silicon crystalline surfaces, G.F. Cerofolini and L. Meda 89 (1995) 351
Enhanced silicon oxidation in O_2 and O_2:F_2, G.F. Cerofolini, G. La Bruna and L. Meda 89 (1995) 361
Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner 90 (1995) 65
Hydrogen adsorption induced phase transitions on Si(100)-c(8 × 8): temperature dependence studied by LEED, X. Hu and Z. Lin 90 (1995) 111
Silicon surface cleaning using XeF_2 gas treatment, V.S. Aliev, M.R. Baklanov and V.I. Bukhtiyarov 90 (1995) 191
In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
Charge transfer processes in a-WO_3/Si heterostructure during electro- and photochromism, E.A. Tutov and A.A. Baev 90 (1995) 303
XPS investigation of electron beam effects on a trimethylsilane dosed Si(100) surface, P.W. Wang, S. Bater, L.P. Zhang, M. Ascherl and J.H. Craig, Jr. 90 (1995) 413
Range profiles of 6–10 MeV ^{15}N ions implanted in silicon, T. Ahlgren, K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen 90 (1995) 419
SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy 90 (1995) 447
AFM and XPS characterization of the Si(111) surface after thermal treatment, B. Lamontagne, D. Guay, D. Roy, R. Sporken and R. Caudano 90 (1995) 481

Silicon carbide

Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
Mechanisms of SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2, H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
Adsorption and co-adsorption of boron and oxygen on ordered α-SiC surfaces, V.M. Bermudez 84 (1995) 45
The (0001)-surface of 6H-SiC: morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175
Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy, S. Kennou, S. Ladas, E.C. Paloura and J.A. Kalomiros 90 (1995) 283

Silicon nitride

A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G.

Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170

Silicon oxide

An AES study of intrinsic and ion-induced structure in the SiO_2–Si system, B. Lang, B. Sefsaf and G. Allan 81 (1994) 17

FT-IR investigation of methane adsorption on silica, J. Wu, S. Li, G. Li, C. Li and Q. Xin 81 (1994) 37

SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem 81 (1994) 127

Ultrathin SiO_2 films on Si formed by N_2O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277

Combined use of XPS, IR and EDAX techniques for the characterization of ZrO_2–SiO_2 powders prepared by a sol–gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325

Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460

An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179

Measurement of oxide thickness using a variable-energy positron beam, T.C. Leung, P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz 85 (1995) 292

SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128

Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294

Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii 86 (1995) 299

Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387

Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyaev and A.S. Medvedev 89 (1995) 49

A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}Cs^+$ beam, H. Tomizuka and A. Ayame 89 (1995) 281

IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO_2 film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu 90 (1995) 29

Silver

Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151

Scanning tunneling microscope observations of Si(111)3 × 1-Ag and 6 × 1-Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444

Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325

Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347

Secondary electron emission from Ag(100) stimulated by positron and electron impact, A.P. Knights and P.G. Coleman 85 (1995) 43

Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405

Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113

The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229

Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375

Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann 89 (1995) 383

Interfacial reaction of Ag with the InP (100)4 × 2 surface – a photoemission study, H. Engelhard, F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann 90 (1995) 89

Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers, M. Sreemany and T.B. Ghosh 90 (1995) 241
Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271

Sputter deposition

Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declemy and Ph. Goudeau 81 (1994) 119
Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565
AES and XPS study of thin RF-sputtered Ta_2O_5 layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185

Sputtering

Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly 87/88 (1995) 446
Preferential sputtering of argon ion bombarded Ni_3Al and $TaSi_2$, S. Hofmann and M.G. Stepanova 90 (1995) 227

Steel

Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito 85 (1995) 229
Microstructure, chemical composition and properties of the surface layer of M2 steel after laser melting under different conditions, J. Kusiński 86 (1995) 317
The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels, R.C. Thomson and M.K. Miller 87/88 (1995) 185
Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz 87/88 (1995) 194
Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
Atom probe field ion microscopy of type 308 CRE stainless steel welds, S.S. Babu, S.A. David, J.M. Vitek and M.K. Miller 87/88 (1995) 207
Comparison of low temperature decomposition in Fe–Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly 87/88 (1995) 446
Determination of the spatial distribution of trace elements in stainless steel by imaging microprobe secondary ion mass spectrometry, G.N. Salaita 90 (1995) 465

Strontium

Atomic force microscopic study of directional $SrSO_4$(001) surface and its etching property, A. Seo and H. Shindo 82/83 (1994) 475
Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
Structural study of $SrTiO_3$(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
Recovery and recrystallization of $SrTiO_3$ (100) surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita 90 (1995) 123

Sulphides

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
The effect of growth parameters on the deposition of CaS thin films by atomic

layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325
Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538

Sulphur

Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143
A study of CaO–SO_2 interaction, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 409
Atomic force microscopic study of directional $SrSO_4(001)$ surface and its etching property, A. Seo and H. Shindo 82/83 (1994) 475
Photo-assisted growth and characterization of $Zn_xCd_{1-x}S$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442

Sulphur dioxide

A study of CaO–SO_2 interaction in the presence of O_2, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
A new parameter to characterize limestones as SO_2 sorbents, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 89 (1995) 197

Superconductors

Pulsed laser deposition and nanometer scale characterization of $YBa_2Cu_3O_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140

Superconductivity

Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
Fabrication of CuO_2-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao 82/83 (1994) 501
Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration, S.A. Holt, R. Zhao and S. Myhra 84 (1995) 125
The laser ablation threshold of $YBa_2Cu_3O_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
Why are high-T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm^2?, R.W. Dreyfus 86 (1995) 29
Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
Characterisation of ionic species generated during ablation of $Bi_2Sr_2Ca_2Cu_3O_{10}$ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
Laser wavelength dependence of $YBa_2Cu_3O_y$ laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehé 86 (1995) 59
SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
Macro-particle ejection by laser ablation of high-temperature superconductors, E.N. Sobol, M.S. Kitai, S.M. Gol'berg and A.N. Zherikhin 90 (1995) 235

Superlattices

Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H.

Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
Fabrication of CuO_2-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao 82/83 (1994) 501

Surface composition

Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171

Surface diffusion

Modelling of barium transport in dispenser cathodes, A. Sil and D.S. Venkateswarlu 81 (1994) 469
Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141

Surface plasmons

Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions , M. Kato and A. Ishii 85 (1995) 69
Oligonucleotide hybridization observed by surface plasmon optical techniques, D. Piscevic, R. Lawall, M. Veith, M. Liley, Y. Okahata and W. Knoll 90 (1995) 425

Surface segregation

Surface segregation study of Ib–VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
Surface segregation and core-level shift of a Pd–Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515

Surface structure

Thermal etching of α-Zr single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy 90 (1995) 59

Tantalum

AES and XPS study of thin RF-sputtered Ta_2O_5 layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin 89 (1995) 401

Tellurium

Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
Pulsed laser deposition of $NbTe_x$ thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364

Thermal desorption

A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
Adsorption of CO on Mg-promoted Co-(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289
A study of $CaO–SO_2$ interaction in the presence of O_2, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
A study of $CaO–SO_2$ interaction in the presence of O_2, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
Activation of the $Ga–CH_3$ bond using atomic hydrogen – a possible route to III–V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner,

S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
CO adsorption on clean and atomic-layer-Cu-covered ZnO($10\bar{1}0$) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
Self-limiting adsorption of thermally cracked $SiCl_2H_2$ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
Adaptive temperature program ALE of $Si_{1-x}Ge_x$/Si heterostructures from Si_2H_6/Ge_2H_6, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
Isothermal H_2 desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
Adsorption and desorption of H_2O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1, M. Suemitsu, H. Nakazawa and N. Miyamoto 82/83 (1994) 449
Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
UV photo-annealing of thin sol–gel films, R.E. Van de Leest 86 (1995) 278
Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559
The distribution of activation energy for hydrogen desorption over silica-supported nickel catalysts determined from temperature-programmed desorption spectra, M. Arai, Y. Nishiyama, T. Masuda and K. Hashimoto 89 (1995) 11
Thermal desorption spectroscopy study of chemically etched porous silicon, N. Hadj Zoubir and M. Vergnat 89 (1995) 35
Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121
Oxygen exchange between adsorbed NO and MgO surfaces, Y. Yanagisawa 89 (1995) 251
Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO_2 film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu 90 (1995) 29
Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297

Thin films

Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declemy and Ph. Goudeau 81 (1994) 119
A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
Ultrathin SiO_2 films on Si formed by N_2O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377

Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda 82/83 (1994) 481
Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565
Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
AES and XPS study of thin RF-sputtered Ta_2O_5 layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325
Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
Using the Lambert–Beer law for thickness evaluation of photoconductor coatings for recording holograms, A. Larena, G. Pinto and F. Millán 84 (1995) 407
Energy loss measurements for 20 keV positrons in Al thin films, G.R. Massoumi, W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson 85 (1995) 39
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325
The laser ablation threshold of $YBa_2Cu_3O_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
Why are high-T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm^2?, R.W. Dreyfus 86 (1995) 29
Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
Characterisation of ionic species generated during ablation of $Bi_2Sr_2Ca_2Cu_3O_{10}$ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
Laser wavelength dependence of $YBa_2Cu_3O_y$ laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehé 86 (1995) 59
Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79
Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99
Influence of ion bombardment on the refractive index of laser pulse deposited oxide

films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114
Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122
SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
Pulsed laser deposition and nanometer scale characterization of $YBa_2Cu_3O_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
Pulsed laser deposition of $NbTe_x$ thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
$Si_{1-x}Ge_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185
Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
Metal pattern deposition by laser-induced forward transfer, Z. Kántor, Z. Tóth and T. Szörényi 86 (1995) 196
New approach of a laser-induced forward transfer for deposition of patterned thin metal films, H. Esrom, J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza 86 (1995) 202
Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
Atypical characteristics of KrF excimer laser ablation of indium–tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228
UV photo-annealing of thin sol–gel films, R.E. Van de Leest 86 (1995) 278
Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
Diffusion and reactions in thin films, A.L. Greer 86 (1995) 329
Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
Formation of poly-$Si_{1-x}Ge_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
Thin films of polymer blends: surface treatment and theoretical modeling, P. Viville, O. Thoelen, S. Beauvois, R.

Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude 86 (1995) 411
Electrochemical and photoelectrochemical modification and characterisation of thin passive films, O. Blum and U. König 86 (1995) 417
UV light irradiation effects on nucleation during chemical vapor deposition of Al films, M. Hanabusa and A. Komatsu 86 (1995) 428
Photoassisted growth of II–VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
Laser processing of tungsten from WF_6 and SiH_4, M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
Excimer laser-induced deposition of copper from Cu(hfac)(TMVS), R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
Laser chemical etching of Cu_2O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
In-situ laser reflectometry of the epitaxial growth of thin semiconductor films, T. Farrell and J.V. Armstrong 86 (1995) 582
Laser diagnostics of C_{60} and C_{70} films by broadband surface acoustic wave spectroscopy, A.A. Kolomenskii, M. Szabadi and P. Hess 86 (1995) 591
16 MB DRAM trench depth characterization using dome scatterometry, Z.R. Hatab, S.L. Prins, S.S.H. Naqvi and J.R. McNeil 86 (1995) 597
P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
Electron field emission (FE) from quantum size systems, L.G. Il'chenko, Yu.V. Kryuchenko and V.G. Litovchenko 87/88 (1995) 53
Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röllgen 87/88 (1995) 146
APFIM study of the compositional inhomogeneity of sputtered Co–Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyaev and A.S. Medvedev 89 (1995) 49
Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121
Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan 89 (1995) 159
Preparation of a model Ziegler–Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
Quantitative correction of backscattering in Auger electron spectroscopy of thin films, G. Lévêque and J. Bonnet 89 (1995) 211
Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
Cadmium selenide–amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
Interfacial reaction of NiO with $Al_2O_3(11\bar{2}0)$ and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339

Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375
Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile–butadiene–styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129
Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
An ellipsometric procedure for the characterization of very thin surface films on absorbing substrates, T. Easwarakhanthan, S. Ravelet and P. Renard 90 (1995) 251
Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy, S. Kennou, S. Ladas, E.C. Paloura and J.A. Kalomiros 90 (1995) 283
Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes, X.R. Xiao, Y. Lin, Y. Yang, X.G. Chen and J.K. You 90 (1995) 321
The influence of the substrate material on the growth of V_2O_5 flash-evaporated films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov 90 (1995) 389
Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas 90 (1995) 455
Characterization of RuO_2 thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong 90 (1995) 497
Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Time of flight techniques

Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227
Composition of sputtered material from Cu–Ni alloy during Xe^+ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
Total cross-section measurements for positrons and electrons colliding with molecules: CCl_4, A. Hamada and O. Sueoka 85 (1995) 64
Generation of an intense pulsed positron beam for positron lifetime and TOF experiments, R. Suzuki, T. Mikado, M. Chiwaki, H. Ohgaki and T. Yamazaki 85 (1995) 87
Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35
Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
The performance of the IMR three-dimensional atom probe, K. Hono, R. Okano, T. Saeda and T. Sakurai 87/88 (1995) 453
A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid–base alternating Langmuir–Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown 90 (1995) 205

Tin

Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223

SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1

Erratum to "Nucleation and growth of θ′ precipitation in Sn-modified Al–Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107

Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Tin oxide

Are modulations of the Schottky surface barrier the only explanation for the gas-sensing effects in sintered SnO_2?, R. Ionescu, C. Moise and A. Vancu 84 (1995) 291

Atypical characteristics of KrF excimer laser ablation of indium–tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219

Titanium

Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143

Structural study of $SrTiO_3$(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528

Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357

Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373

Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35

Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74

Electrochemical and photoelectrochemical modification and characterisation of thin passive films, O. Blum and U. König 86 (1995) 417

APFIM investigations on ordered γ-TiAl using single-layer detection method, J. Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179

A study of the composition distribution at the Ti/Al_2O_3 interface using the MCs^+-SIMS technique, X. Chen and Y. Wang 89 (1995) 169

Preparation of a model Ziegler–Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187

Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75

Recovery and recrystallization of $SrTiO_3$(100) surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita 90 (1995) 123

Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129

Titanium carbide

In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185

Titanium dioxide

A photoemission study of electron states in Sb-ion implanted TiO_2(110), A.E. Taverner, A. Gulino, R.G. Egdell and T.J. Tate 90 (1995) 383

Titanium nitride

Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237

Oxidation of TiN thin films in an ion-beam-assisted deposition process, H.

Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565
Positron beam spectroscopy for the assessment of the structure and defect density of titanium nitride, P.C. Rice-Evans, A.S. Saleh and S.J. Bull 85 (1995) 320
In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185
Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129

Titanium oxide

Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122
Formation of Ti^{3+} ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton 86 (1995) 382
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori 89 (1995) 411
Surface segregation of Sb in doped TiO_2 rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdell 90 (1995) 289
XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343

Transition metals

A simple approach to the calculation of surface defect energies in transition metals, M.C. Desjonquères, D. Spanjaard, B. Piveteau and S. Papadia 87/88 (1995) 337
Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guczi 90 (1995) 165

Tribology

Multi-spectral scanning Auger microscopy of tribological surfaces, I.R. Barkshire, M. Prutton and G.C. Smith 84 (1995) 331

Tungsten

A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
Surface structure dependence of O_2–W adsorption system, M. Sato 82/83 (1994) 532
Laser processing of tungsten from WF_6 and SiH_4, M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
Laser-induced etching and deposition of tungsten in WF_6–H_2 atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37
Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst 87/88 (1995) 45
A FEM study of liquid lithium on a ⟨011⟩-oriented tungsten tip, K. Hata, M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita 87/88 (1995) 117
M–S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
Charge transfer processes in a-WO_3/Si heterostructure during electro- and photochromism, E.A. Tutov and A.A. Baev 90 (1995) 303

Tunneling

Electron tunneling in double-barrier diode, Liu Yunpeng and Luo Enze 87/88 (1995) 75

Vanadium

Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375

Vanadium oxide

The influence of the substrate material on the growth of V_2O_5 flash-evaporated

films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov 90 (1995) 389

Water

Electron-beam-induced oxidation of CdS, V.B. Mityukhlyaev 81 (1994) 137
The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans 81 (1994) 449
Adsorption and desorption of H_2O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
Nucleation and island growth during water adsorption at sub-monolayer coverages, R.V. Kasza, K. Griffiths, V.P. Zhdanov and P.R. Norton 84 (1994) 97
Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
Field-induced redistribution and diffusion of water on a Pt field emitter, R. Bryl, T. Wysocki and R. Błaszczyszyn 87/88 (1995) 69
Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo 89 (1995) 21

Work function

Work function and epithermal positron emission from copper, N. Overton, A.P. Knights, A. Goodyear and P.G. Coleman 85 (1995) 54
Method for the measurement of positron affinities and positron work functions suitable for both positive and negative work function materials, A.H. Weiss, S. Yang, H.Q. Zhou, E. Jung, A.R. Koymen, S. Naidu, G. Brauer and M.J. Puska 85 (1995) 82
Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37

Xenon

Silicon surface cleaning using XeF_2 gas treatment, V.S. Aliev, M.R. Baklanov and V.I. Bukhtiyarov 90 (1995) 191

X-ray diffraction

Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declemy and Ph. Goudeau 81 (1994) 119
Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Braul, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
A study of $CaO–SO_2$ interaction in the presence of O_2, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Suemune 82/83 (1994) 149
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
Fabrication of CuO_2-plane-based high-temperature superconducting thin films by

atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao 82/83 (1994) 501
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
Surface analysis of commercial lead/acid battery grids, R. De Marco and J. Liesegang 84 (1995) 237
Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325
Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
The laser ablation threshold of $YBa_2Cu_3O_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99
Structural properties of $LiNbO_3$ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
Pulsed laser deposition of $NbTe_x$ thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170
Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
Morphology of $Si_{1-x}Ge_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter 86 (1995) 368
Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan 89 (1995) 159
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
Interfacial reaction of NiO with $Al_2O_3(11\bar{2}0)$ and polycrystalline α-Al_2O_3, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
Synthesis of molybdenum nitride γ-Mo_2N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (*h*11)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
Characterization of the plasma plume and of thin film epitaxially produced during

laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

X-ray fluorescence

Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553

X-ray scattering

Surface fractal dimension of sintered porous solid niobium, L.I. Skatkov, V.V. Konotop, P.G. Cheremskoy, V.P. Gomozov and B.I. Bayrachny 81 (1994) 427
An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179

X-ray spectroscopy

Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
Combined use of XPS, IR and EDAX techniques for the characterization of ZrO_2–SiO_2 powders prepared by a sol–gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325
$NbCl_5$ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
Formation of Ti^{3+} ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton 86 (1995) 382
Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500

X-ray standing wave

LiBr on Si(111): an X-ray standing wave measurement, Th. Gog, G.C. Follis and S.M. Durbin 81 (1994) 485

Yttrium

Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
Ultraviolet inverse photoemission study of the oxidation of YFe_2, P. Vavassori, L. Callegaro and E. Puppin 89 (1995) 93
The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229

Zeolites

In-situ FTIR investigation of coke formation on USY zeolite, C. Li, Y.-W. Chen, S.-J. Yang and R.-B. Yen 81 (1994) 465
Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543
An XPS study of the optimum loading of barium on high-silica MFI zeolite, M.H. Mohamed, M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui 90 (1995) 409

Zinc

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of

zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
Photo-assisted growth and characterization of $Zn_xCd_{1-x}S$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538

Zinc oxide

Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface, W.M.K.P. Wijekoon, E.W. Koenig, W.M. Hetherington III and W.R. Salzman 81 (1994) 347
Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
CO adsorption on clean and atomic-layer-Cu-covered ZnO($10\bar{1}0$) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99

Zirconium

Combined use of XPS, IR and EDAX techniques for the characterization of ZrO_2–SiO_2 powders prepared by a sol–gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325
Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $Pb(Ti_{0.48}Zr_{0.52})O_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35
The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2$-$Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
Thermal etching of α-Zr single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy 90 (1995) 59
XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343

ELSEVIER

Applied Surface Science MI 81–90 (1995) 116–118

applied surface science

List of terms used in the subject index

Ablation
Alkali halides
Alkali metals
Alloys
Aluminium
Aluminium oxide
Ammonia
Annealing
Antimony
Argon
Arsenic
Atomic force microscopy
Atomic probe analysis
Auger electron spectroscopy

Barium
Beryllium
Biological materials
Bismuth
Borides
Boron
Boron nitride

Cadmium
Cadmium selenide
Cadmium sulphide
Cadmium telluride
Calcium
Carbides
Carbon
Carbon dioxide
Carbon monoxide
Catalysis
Ceramics
Chemical vapour deposition
Chromium
Clusters
Cobalt
Computer simulations
Copper

Depth profiling
Deuterium
Diamond
Dielectric constant
Diffusion
Doping effects

Elastic recoil detection
Electrical properties
Electromigration
Electron bombardment
Electron diffraction
Electron emission
Electron energy loss spectroscopy
Electron microscopy
Electron spin resonance
Ellipsometry
Epitaxy
Erbium
Etching
Evaporation

Field desorption
Field effect
Field electron microscopy
Field emission
Field emission microscopy
Field evaporation
Field ion microscopy

Gallium
Gallium arsenide
Gallium phosphide
Germanium
Glass

Gold
Graphite

Hafnium
Halides
Halogenides
Halogens
Helium
Hydrides
Hydrocarbons
Hydrogen

Indium
Indium antimonide
Indium arsenide
Indium phosphide
Infrared spectroscopy
Interfaces
Ion bombardment
Ion implantation
Ion scattering
Iron

Krypton

Langmuir–Blodgett structures
Lanthanides
Laser processing
Lead
Low energy electron diffraction
Luminescence

Magnesium
Magnesium oxide
Magnetic properties
Manganese
Mass spectroscopy
Mercury telluride
Metals
Methane
Methanol
Mica
Molecular dynamics
Molybdenum
Monte Carlo simulations
Mössbauer spectroscopy
Multilayers

Nickel
Niobium
Niobium oxide
Nitric oxide
Nitrides
Nitrogen
Noble gases
Nuclear magnetic resonance
Nuclear reaction analysis
Nucleation

Optical properties
Organic substances
Organometallic vapour deposition
Oxidation
Oxides
Oxygen

Palladium
Phase transitions
Phosphorus
Photochemistry
Photoelectron spectroscopy
Photoemission
Photon emission
Plasma processing
Platinum
Polymers
Positron beams
Positron diffraction
Positron microscopy
Positron scattering
Positron spectroscopy

Quantum effects
Quartz

Radiation damage
Raman scattering
Rhenium
Rhodium
Ruthenium

Scanning tunneling microscopy
Schottky barrier
Secondary ion mass spectrometry
Selenium
Semiconductors
Silane
Silicides
Silicon

Silicon carbide
Silicon nitride
Silicon oxide
Silver
Sputter deposition
Sputtering
Steel
Strontium
Sulphides
Sulphur
Sulphur dioxide
Superconductors
Superconductivity
Superlattices
Surface composition
Surface diffusion
Surface plasmons
Surface segregation
Surface structure

Tantalum
Tellurium
Thermal desorption
Thin films
Time of flight techniques
Tin
Tin oxide
Titanium
Titanium carbide
Titanium dioxide
Titanium nitride
Titanium oxide
Transition metals
Tribology
Tungsten
Tunneling

Vanadium
Vanadium oxide

Water
Work function

Xenon
X-ray diffraction
X-ray fluorescence
X-ray scattering
X-ray spectroscopy
X-ray standing wave

Yttrium

Zeolites
Zinc
Zinc oxide
Zirconium

INSTRUCTIONS FOR AUTHORS

Submission: Contributions must be written in English and should have an abstract. They should be submitted to one of the Editors in triplicate with one set of *original drawings* (no larger than ca. 20×30 cm) of the figures and two sets of duplicate copies. Micrographs should *always* be submitted in triplicate. The Publisher prefers to have an ELECTRONIC FILE of the final text on a $3^1/_2$" or $5^1/_4$" diskette. Both double density and high density diskettes are acceptable. There is little restriction on the word processor used. The name and version of the word-processing program, type of computer and format of the files should be clearly indicated. It is the responsibility of the author to ensure that the version on disk exactly matches the paper copies. For editorial addresses, see inside front cover.

Rapid publication: Short papers, for which rapid publication is appropriate, may be submitted as a "Letter to the Editor". The manuscripts should not exceed 1000 words in length, contain a modest number of illustrations and a short abstract.

Copyright transfer: The submission of a paper will be taken to imply that the author has satisfied himself that no copyright will thereby be infringed. Upon acceptance of an article by this journal the author(s) will be asked to transfer copyright of the article to the Publisher. This transfer will ensure the widest possible dissemination of information.

Preparation of manuscripts

(1) *Manuscripts* should be typed throughout with double line spacing and wide margins on numbered pages.

(2) *Title page(s)* should contain, in addition to the article title, author(s)' names and affiliations, the text of related footnotes and the text of the abstract. Indicate which author will act as contact author and *provide E-mail No., FAX No. and telephone No.*, if available.

(3) *Tables* should be typed on separate sheets at the end of the manuscript. In addition to its serial number, each table should have a sufficiently detailed heading or caption to explain the data displayed in it.

(4) *Figures* should be numbered and their captions listed together at the end of the manuscript.

(5) *References* in the text to other publications should be numbered consecutively within square brackets, for example: "Hoekje and Hoflund [1] have shown ..." and listed together at the end of the text, for example:

[1] S.J. Hoekje and G.B. Hoflund, Appl. Surf. Sci. 47 (1991) 43.
[2] A. Roth, Vacuum Technology, 3rd ed. (North-Holland, Amsterdam, 1990).
[3] V. Celli, in: Dynamical Properties of Solids, Vol. 6, Eds. G.K. Horton and A.A. Maradudin (North-Holland, Amsterdam, 1990) p. 337.

References to unpublished or not readily accessible reports should be avoided. In the case of multiple authorship all authors should be listed in the references provided they number less than ten. Only in the case of more than ten authors is the first author et al. acceptable.

(6) *Formulae* in the manuscript should be typed with particular consideration given to characters that may be misinterpreted, e.g.

I (cap.), l (el), 1 (one), ′ (prime)	c, C; k, K, κ (kappa); p, P, ρ (rho)
o (lower case), O (cap.), 0 (zero), ° (deg)	u, v (lower case), ν (nu), V (cap.)
× (times), x (lower case), X (cap.)	Σ (sigma), Σ (sum), Π (pi), Π (product); etc.

If necessary, unusual symbols should be explained in pencil in the margin.

(7) *Vectors* should be indicated by a wavy underlining, and will be printed in bold-face italics.

Preparation of figures

The publisher requires a set of good quality drawings and photographs to produce the printed line figures and half-tone plates in the journal. Photographic copies ("glossy prints") of drawings are also acceptable for the line figures if they have been sharply focused and evenly exposed. **As a rule, Xerox copies cannot be accepted.** Original drawings and photographs will be returned after publication of the paper.

(1) *Line figures*: The drawings or glossy prints supplied for the line figures should be 1.5–3 times larger than the printed size of the figures and should contain all the required, carefully applied lettering.
Figures are preferably reduced to a single column width (7.6 cm) unless their complexity, large width-to-height ratio, or need to display special detail makes a larger format necessary (max. printed width ~ 20 cm). Inappropriately sized lettering on a figure may prevent its reduction to the size optimum for its information content. The lettering used on a drawing should be chosen so that after reduction, the height of numbers and (capital) letters falls within the range 1.2–2.4 mm. Care should be exercised in choosing the pen width of machine-plotted graphs. Frequently lines in these figures are too fine compared to the area of the figure.
Shaded areas in line figures should be shown by means of cross-hatching (or a matrix of dots) rather than a continuous grey "wash". Cross-hatching, after reduction, of density less than ~ 25 lines/cm is satisfactory.

(2) *Half-tone plates*: The photographs supplied for reproduction should be unmounted unless they form part of a composite figure and they should have a somewhat greater contrast than is desired in the printed figure. It is important that the photographs supplied are not already screened (overprinted with the point-matrix used by printers) or moiré patterns will form when they are screened for a second time. When necessary, the top side of a photograph should be marked on the back. A reduction factor should be recommended for a photo when it is not obvious what detail in the photo is of interest.

(3) *Colour plates*: Illustrations can be printed in colour when they are judged by the Editor to be essential to the presentation. The Publisher and the Author will each bear part of the extra costs involved. Further information concerning colour illustrations and the costs to the author can be obtained from the Publisher.

IMPORTANT: When page proofs of the accepted manuscript are made and sent out to authors, this is in order to check that no undetected errors have arisen in the typesetting (or file conversion) process. At the proof stage only printer's errors may be corrected. No changes in, or additions to, the edited manuscript will be accepted.

Offprints: 50 offprints of the article will be supplied free of charge. Additional offprints may be ordered from the publisher. An order form will be sent to contributors together with the proofs. There is **no** page charge.

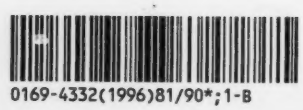
applied surface science

Abstracted/indexed in: Aluminium Industry Abstracts; Chemical Abstracts; Current Contents: Physical, Chemical and Earth Sciences; EI Compendex Plus; Engineering Index; INSPEC; Metals Abstracts

MASTER INDEX

Volumes 81–90

Author index	1
Subject index	33
List of terms used in the subject index	116



0169-4332(1996)81/90*;1-B